### LTC4283



## Negative Voltage Hot Swap Controller with **Energy Monitor**

### **FEATURES**

- Allows Safe Insertion into Live –48V Backplanes
- **Protects MOSFET with SOA Timer**
- Programmable 15mV to 30mV Current Limit Sense Voltage with 2% Accuracy and Adjustable Foldback
- 8-Bit to 16-Bit Gear-Shift ADC with 0.5% Accuracy
- Monitors Voltages, Currents, Power and Energy
- Nonvolatile Configuration and Fault Recording
- Floating Topology for Rugged High Voltage Operation
- Selectable Inrush Control: dV/dt or Current Limit
- I<sup>2</sup>C/SMBus or Single-Wire Broadcast Interfaces
- Min/Max ADC Measurement Logging with Alerts
- Reboots on I<sup>2</sup>C Command with Programmable Delay
- Adjustable Input UV/OV Thresholds and Hysteresis
- 38-Pin 5mm × 7mm QFN Package

### **APPLICATIONS**

- Telecom Infrastructure
- -48V Distributed Power Systems
- Servers and Data Centers
- **Power Monitors**

## DESCRIPTION

The LTC<sup>®</sup>4283 negative voltage hot swap controller drives an external N-channel MOSFET to allow a board to be safely inserted and removed from a live backplane. The device features programmable current limit with foldback and independently adjustable inrush current to optimize the MOSFET safe operating area (SOA). The SOA timer limits MOSFET temperature rise for reliable protection against overstresses.

An I<sup>2</sup>C interface and onboard gear-shift ADC allow monitoring of board current, voltage, power, energy, and fault status. An available single-wire broadcast mode simplifies the interface by eliminating two isolators. The included EEPROM provides black-box capturing and nonvolatile configuration of fault behavior.

Additional features respond to input UV/OV, interrupt the host when a fault has occurred, notify when output power is good, detect insertion of a board, turn off the MOSFET if an external supply monitor fails to indicate power good within a timeout period, and auto-reboot after a programmable delay following a host commanded turn-off.

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### TYPICAL APPLICATION

RTN UV = 38.6V1k. 1W. ×4 **≤**200k LTC4283 Startup Behavior ₹ 0 1uF UV RELEASE AT 43.1V IN SERIES OV = 71.9V  $V_{\text{EE}}$ VEE RTN OV RELEASE AT 70.7V CONTAC (SHORT PIN) ξ 5 11k BOUNCE 487 -48V INPUT INTVCC RTNS n Vz VIN VFF 50V/DIV UVH SC UVL SDA VIDAD 14.3k SDAO RAMP V<sub>OUT</sub> 50V/DIV AI FRT# 0V LTC4283 18.2k 500uF TMR ADIN V<sub>GATE</sub> 10V/DIV 128ms DEBOUNCE EN# ADIO **≨**1.13M 4.7nF Vee PGIO ξ 10k IINRUSH 5A/DIV 68nF SENSE<sup>-</sup> SENSE<sup>+</sup> GATE DRAIN DRMS 470Ω V<sub>FE</sub> Vee 25ms/DIV **≤** 100k 100nF **>** 200k VEE [Ŧ] -48\ νοιιτ INPUT PSMN4R8-100BSE ×2  $0.5 m\Omega$ 4283 TA01:

-48V/600W Hot Swap Controller with Telemetry



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### **ABSOLUTE MAXIMUM RATINGS**

#### (Notes 1 and 2)

| Supply Voltage:                                      |
|--|
| V <sub>IN</sub> –0.3V to 12.5V                       |
| INTV <sub>CC</sub> –0.3V to 5.5V                     |
| Input Voltages                                       |
| V <sub>7</sub> (Note 3)–0.3V to 16                   |
| DRAIN (Note 4)                                       |
| EN# (Note 5)   |
| UVL. UVH   |
| ADIN1-4, ADR0, ADR1, DRNS, OV, RTNS,                 |
| SCL. SDAI. SENSE <sup>+</sup> . SENSE <sup>-</sup> . |
| VOUTTH, WP–0.3V to INTVcc + 0.3V                     |
| Output Voltages                                      |
| GATE. PGI01-40.3V to VIN + 0.3V                      |
| VREF   |
| ADI01-4. RAMP. TMR0.3V to INTVcc + 0.3V              |
| ALERT#. SDA0   |
| Input Currents:                                      |
| V7   |
| DRAIN  |
| FN# 5m/  |
| Operating Ambient Temperature Range                  |
| LTC4283C   |
| -40°C to 85°C  |
| LTC4283H40°C to 125°C                                |
| Storage Temperature Range–65°C to 150°C              |

### PIN CONFIGURATION



### **ORDER INFORMATION**

| TUBE            | TAPE AND REEL     | PART MARKING* | PACKAGE DESCRIPTION             | TEMPERATURE RANGE |
|-----------------|-------------------|---------------|---------------------------------|-------------------|
| LTC4283CUHF#PBF | LTC4283CUHF#TRPBF | 4283          | 38-Lead (5mm × 7mm) Plastic QFN | 0°C to 70°C       |
| LTC4283IUHF#PBF | LTC4283IUHF#TRPBF | 4283          | 38-Lead (5mm × 7mm) Plastic QFN | -40°C to 85°C     |
| LTC4283HUHF#PBF | LTC4283HUHF#TRPBF | 4283          | 38-Lead (5mm × 7mm) Plastic QFN | -40°C to 125°C    |

Contact the factory for parts specified with wider operating temperature ranges. \*The temperature grade is identified by a label on the shipping container. Tape and reel specifications. Some packages are available in 500 unit reels through designated sales channels with #TRMPBF suffix.

Rev. 0

|                         | · · · · · · · · · · · · · · · · · · ·   |   |   |                       |                       |                       |       |
|-------------------------|---|---|---|-----------------------|-----------------------|-----------------------|-------|
| SYMBOL                  | PARAMETER   | CONDITIONS  |   | MIN                   | ТҮР                   | MAX                   | UNITS |
| Power Supply            | 1   |   |   |                       |                       |                       |       |
| VIN                     | Shunt Regulated Voltage at V <sub>IN</sub>                                      | $I_{IN} + I_{VZ} = 4mA$   |   | 10.8                  | 11.5                  | 12                    | V     |
| $\Delta V_{IN}$         | Load Regulation at V <sub>IN</sub>  | $I_{IN} + I_{VZ} = 4mA$ to 35mA   |   |                       | 250                   | 500                   | mV    |
| I <sub>IN</sub>         | V <sub>IN</sub> Supply Current  | V <sub>IN</sub> = 10.5V   |   |                       | 2.5                   | 4                     | mA    |
| V <sub>IN(UVLO)</sub>   | V <sub>IN</sub> Undervoltage Lockout Threshold                                  | V <sub>IN</sub> Rising  |   | 7.5                   | 8.1                   | 8.6                   | V     |
| $\Delta V_{IN(UVLO)}$   | V <sub>IN</sub> Undervoltage Lockout Hysteresis                                 |   |   | 0.4                   | 0.5                   | 0.6                   | V     |
| I <sub>VZ</sub>         | V <sub>Z</sub> Input Current  | $V_{IN} = 10.5V, V_Z = 15V$   |   |                       |                       | 20                    | μA    |
| INTV <sub>CC</sub>      | Internal 5V LDO Voltage   | $I_{LOAD}$ = 1mA to 30mA, $I_{IN}$ + $I_{VZ}$ = 35mA                                  |   | 4.75                  | 5.05                  | 5.35                  | V     |
| V <sub>CC(UVLO)</sub>   | INTV <sub>CC</sub> Undervoltage Lockout Threshold                               | INTV <sub>CC</sub> Rising   |   | 3.65                  | 4                     | 4.3                   | V     |
| $\Delta V_{CC(UVLO)}$   | INTV <sub>CC</sub> Undervoltage Lockout Hysteresis                              |   |   | 0.12                  | 0.2                   | 0.3                   | V     |
| Gate Drive              |   |   |   |                       |                       |                       |       |
| V <sub>GATE</sub>       | Gate Drive Voltage for GATE   |   |   | V <sub>IN</sub> – 0.3 | V <sub>IN</sub>       | V <sub>IN</sub> + 0.3 | V     |
| V <sub>GATE(TH)</sub>   | Gate High Threshold for Asserting Power Good                                    | GATE Rising   | • | V <sub>IN</sub> – 2.1 | V <sub>IN</sub> – 1.8 | V <sub>IN</sub> – 1.5 | V     |
| V <sub>GATE(HYST)</sub> | Gate High Hysteresis  |   |   | 0.3                   | 0.7                   | 1.1                   | V     |
| I <sub>GATE(UP)</sub>   | GATE Pull-Up Current  | $V_{GATE} = 4V$   |   | -80                   | -100                  | -150                  | μA    |
| IGATE(DN)               | GATE Fast Pull-Down Current   | $\Delta V_{SENSE} = V_{ILIM(FAST)} + 10mV, V_{GATE} = 7V$                             |   | 1                     | 2.3                   | 4                     | A     |
|                         | GATE Current Limit Pull-Down Current  | $\Delta V_{SENSE} = V_{ILIM} + 5mV, V_{GATE} = 7V$                                    | • | 25                    | 50                    | 100                   | mA    |
|                         | GATE Turn Off Pull-Down Current   | TMR, OV, EN# = High, UVL = Low,<br>V <sub>GATE</sub> = 7V                             | • | 8                     | 18                    | 40                    | mA    |
| On/Off Timing           | ]   |   |   |                       |                       |                       | ·     |
| t <sub>PHL(SENSE)</sub> | ∆V <sub>SENSE</sub> High to GATE Low Propagation Delay                          | ILIM = 0000b, $\Delta V_{SENSE}$ Steps from 0mV to 100mV, $V_{GATE} < 3V$ , GATE Open | • |                       | 60                    | 150                   | ns    |
| t <sub>PHL(GATE)</sub>  | GATE Turn Off Propagation Delay   | TMR, OV, EN# = High, UVL = Low, $V_{GATE} < 3V$ , GATE Open                           | • |                       | 0.5                   | 1                     | μs    |
| t <sub>DL(DB)</sub>     | Debounce Delay, Auto-Retry Delay<br>Following Undervoltage or PGI Fault         |   | • | 115                   | 128                   | 141                   | ms    |
| t <sub>DL(PG)</sub>     | Power Good Delay  |   |   | 230                   | 256                   | 282                   | ms    |
| t <sub>DL(PGIWD)</sub>  | Power Good Input Watchdog Timer   |   | • | 461                   | 512                   | 563                   | ms    |
| t <sub>DL(RTRY)</sub>   | Auto-Retry Delay Following Overcurrent,<br>FET Bad or External Fault (Table 11) | COOLING_DL = 000b - 111b  | • |                       |                       | ±10                   | %     |
| t <sub>DL(RTCRST)</sub> | Auto-Retry Counter Reset Delay  | OC_RETRY, FET_BAD_RETRY = 01b, 10b  |   | 14.8                  | 16.4                  | 18                    | S     |
| t <sub>DL(FETBAD)</sub> | FET Bad Fault Timer Delay (Table 11)  | FTBD_DL = 00b - 11b   | • |                       |                       | ±10                   | %     |
| t <sub>DL(RBT)</sub>    | Auto-Reboot Delay (Table 23)  | After RBT_EN Bit is Set Via I <sup>2</sup> C Interface,<br>RBT_DL = 000b – 111b       | • |                       |                       | ±10                   | %     |
| dV/dt Control           | ·   | ·   |   |                       |                       |                       | ·     |
| I <sub>RAMP</sub>       | RAMP Output Current   | Startup Only, dV/dt Control Enabled   |   | -2.25                 | -2.5                  | -2.75                 | μA    |
| IRAMP(DN)               | RAMP Discharge Current  | V <sub>RAMP</sub> = 1.2V  |   | 1                     | 4                     | 10                    | mA    |
|                         |   |   |   |                       |                       |                       |       |

| STRIBUL         PARAMIC LEY         CURUITURS         ININ         ININ         ININ         MAA         UNITS           Drain Monitor         Drain Monitor         0         2         2.05         2.1         V           VD_PG(TH)         DRAIN Input Threshold for Power Good         DRAIN Raing, Vorman Comment         20         mV           VD_FE(TM)         DRAIN Input Threshold for FET Bad Timer         DRAIN Raing, Vorman Comment         0         ±10         mV           VD_FE(TM)         DRAIN Input Threshold for FET Bad Timer         DRAIN Raing, Vorman Comment         0         ±10         mV           VD_FE(TM)         DRAIN Input Threshold for FET Bad Timer         DRAIN Raing, Vorman Comment         0         ±10         mV           VD_EARIN         DRAIN Input Threshold for FET Bad Timer         Vorman Comment         Vorman Comment         0         ±10         mV           Current Limit Voltage DAC Zero-Scale         ILLM = 0000b, C-Grade (Note 6)         14.7         15         15.3         mV           Current Limit Voltage DAC INL         ILLM = 0111b, L-H-Grade         2.9         30         3.0         mV           Current Limit Voltage DAC INL         RTNS = 1.8V, DRNS = 0.1.8V         FB = 01b         4.5         50         55         % <tr< th=""><th></th><th></th><th></th><th></th><th></th><th>RAINI</th><th></th><th>BRAV</th><th></th></tr<>  |                                 |   |  |          |   | RAINI        |          | BRAV         |          |
|--|---------------------------------|---|--|----------|---|--------------|----------|--------------|----------|
| Drain Monitor         Open(Th)         OPAIN Input Threshold for Power Good         DRAIN Input Threshold for FP Bad Timer         OPAIN Input Threshold for FF Bad Timer         OPAIN Input Threshold for Fower Good         I/// Compt Threshold for Fower Good <t< th=""><th>STIMBUL</th><th>PARAMETER</th><th>CONDITIONS</th><th></th><th></th><th>MIN</th><th>ITP</th><th>MAX</th><th>UNIIS</th></t<>   | STIMBUL                         | PARAMETER   | CONDITIONS   |          |   | MIN          | ITP      | MAX          | UNIIS    |
| Op.Reg(ms)         DRAIN input Threshold for Power Good         OPAIN Failing         ●         2         2.05         2.1         V           VD_REG(MS)         DRAIN Input Threshold for FET Bad Timer<br>and TMR Pul-Up Current (2014b 11)         DRAIN Input Threshold for FET Bad Timer<br>and TMR Pul-Up Current (2014b 11)         Image 200mV         0         ±10         mV           VD_REG(MS)         DRAIN Input Stresshold for FET Bad Timer<br>and TMR Pul-Up Current (2014b 11)         VD_RAIN = 200mV         0         ±10         mV           VD_REITHS         DRAIN Input Stresshold for FET Bad Timer<br>and TMR Pul-Up Current Limit Voltage DAC Zero-Scale         ILIM = 0000b, C-Grade (Note 6)         14.7         15         15.3         mV           Current Limit Voltage DAC Ful-Scale         ILIM = 1011D, C-Grade (Note 6)         29.4         30.3         30.6         mV           Current Limit Voltage DAC INL         Current Limit Foldback Factor at Startup         RTNS = 1.8V, DRNS = 0.1.8V         FB = 01b         455         50         55         %           Current Limit Foldback Factor in Normal<br>Operation         RTNS = DRNS = 1.8V         FB = 11b         6         10         16         %           VILIMARTIN         Fast Pul-Down Sense Threshold Voltage         ILIM = 0000b         -0         -2         20         30         40         mV   | Drain Monitor                   | -   | [  |          |   |              |          |              |          |
| MD_DEGUNST)<br>DRAIN Input Hysteresis for Power Good<br>and TMR Pull-Up Current (Table 11)<br>and TMR Pull-Up Current (Table 11)<br>MVD_FET(HYST)<br>DRAIN Input Theodoff or FET Bard Immer<br>and TMR Pull-Up Current<br>DRAIN Input Theodoff or FET Bard Immer<br>Add TMR Pull-Up Current<br>DRAIN Input Theodoff or FET Bard Immer<br>MUMAN         DRAIN Input Hysteresis with VD_FET(H)<br>VDRAIN = 2V         Immer<br>MUMAN         Immer<br>MUM   | V <sub>D,PG(TH)</sub>           | DRAIN Input Threshold for Power Good  | DRAIN Falling  |          |   | 2            | 2.05     | 2.1          | V        |
| DFAIN Input Threshold for FET Bad Timer         DRAIN Rainel, Vorter (Tabia 11)         Paint Reline, Vorter (Tabia 11)         Paint  | $\Delta V_{D,PG(HYST)}$         | DRAIN Input Hysteresis for Power Good   |  |          |   |              | 20       |              | mV       |
| MVD_FEI(HYST)         DRAIN Input Hysteresis with VD_FEI(TH)         10         mV           Uprant         DRAIN Input Current         VD_RAIN = 200mV         ●         0         ±0.1         µA           Current Limit         VDRAIN = 2V         ●         0         ±1         µA           Current Limit Voltage DAC Zero-Scale         ILIM = 0000b, C-Grade (Note 6)         14.7         15         15.5         mV           Current Limit Voltage DAC Full-Scale         ILIM = 1000b, L, H-Grade (Note 6)         14.7         15         15.5         mV           Current Limit Voltage DAC Full-Scale         ILIM = 1000b, L, H-Grade (Note 6)         14.5         15.5         mV           Current Limit Voltage DAC INL         RTNS = 1.8V, DRNS = 0, 1.8V         FB = 10b         45         50         55         %           Current Limit Foldback Factor at Startup         RTNS = 1.8V, DRNS = 1.8V         FB = 10b         16         20         24         %           GenomMaL         Current Limit Foldback Factor in Normal Deration         RTNS = DRNS = 1.8V         FB = 10b         45         50         55         %           VILIM(FAST)         Fast Pull-Down Sense Threshold Voltage         ILIM = 0000b         41         µA           Senset         Senset = samV         6 <td>V<sub>D,FET(TH)</sub></td> <td>DRAIN Input Threshold for FET Bad Timer<br/>and TMR Pull-Up Current (Table 11)</td> <td>DRAIN Rising, V<sub>DTH</sub> = 00b - 1<sup>-</sup></td> <td>1b</td> <td>•</td> <td></td> <td></td> <td>±10</td> <td>%</td>  | V <sub>D,FET(TH)</sub>          | DRAIN Input Threshold for FET Bad Timer<br>and TMR Pull-Up Current (Table 11) | DRAIN Rising, V <sub>DTH</sub> = 00b - 1 <sup>-</sup>                                  | 1b       | • |              |          | ±10          | %        |
| DRAIN         DRAIN Input Current         VDRAIN = 200mV         0         ±0.1         µA           VILIM         Current Limit Voltage DAC Zero-Scale         ILIM = 0000b, C-Grade (Note 6)         14.7         15         15.3         mV           Current Limit Voltage DAC Full-Scale         ILIM = 0000b, C-Grade (Note 6)         14.7         15         15.3         mV           Current Limit Voltage DAC Full-Scale         ILIM = 1111b, C-Frade (Note 6)         24.9         30         30.6         mV           Current Limit Voltage DAC Full-Scale         ILIM = 1111b, C-Frade (Note 6)         29         30         31         mV           Gramma Contract Limit Foldback Factor at Startup         RTNS = 1.8V, DRNS = 0, 1.8V         FB = 01b         45         50         55         %           Current Limit Foldback Factor in Normal Operation         RTNS = 1.8V, DRNS = 1.8V         FB = 01b         6         16         20         24         %           Operation         Destation         RTNS = Sense 1.8V         FB = 01b         6         16         20         6         %           VILIM(FAST)         Fast Pull-Down Sense Threshold Voltage         ILIM = 0000b         15         20         6         %           VILIM(FAST)         Senset Input Current         SEnset = 28mV<  | $\Delta V_{D,FET(HYST)}$        | DRAIN Input Hysteresis with V <sub>D,FET(TH)</sub>                            |  |          |   |              | 10       |              | mV       |
| Understand         Version         Pit M   | IDRAIN                          | DRAIN Input Current   | V <sub>DRAIN</sub> = 200mV   |          |   |              | 0        | ±0.1         | μA       |
|  |                                 |   | V <sub>DRAIN</sub> = 2 V   |          |   |              | 0        | ±1           | μA       |
| VILIM         Current Limit Voltage DAC Zero-Scale         ILIM = 0000b, C-Grade (Note 6)<br>ILIM = 1111b, C-Grade (Note 6)         14.7         15         15.5         mV           Current Limit Voltage DAC Full-Scale         ILIM = 1111b, C-Grade (Note 6)<br>ILIM = 1111b, L-H-Grade         29.4         30         30.6         mV           Current Limit Voltage DAC INL         EB = 01b         44.5         50         55         %           Current Limit Foldback Factor at Startup         RTNS = 1.8V, DRNS = 0, 1.8V         FB = 01b         445         50         55         %           CRNDMAL         Qurrent Limit Foldback Factor in Normal         RTNS = 1.8V, DRNS = 0, 1.8V         FB = 01b         445         50         55         %           CRNDMAL         Qurrent Limit Foldback Factor in Normal         RTNS = DRNS = 1.8V         FB = 01b         45         50         55         %           VILIM(FAST)         Fast Pull-Down Sense Threshold Voltage         ILIM = 0000b         15         20         30         40         mV           ISENSE*         SENSE Input Current         SENSE* SE* SENS* a 3mV         0         14.7         14.7         14.7         14.7         14.7         14.7         13         %         14.7         14.7         15         15.5         mV         16  | <b>Current Limit</b>            |   |  |          |   |              |          |              |          |
| Current Limit Voltage DAC Full-Scale         ILIM = 1111b, C-Grade (Note 6)         29         30         30.6         mV           Current Limit Voltage DAC INL          0         ±50         µV           Current Limit Voltage DAC INL          0         ±50         µV           Current Limit Foldback Factor at Startup<br>Operation         RTNS = 1.8V, DRNS = 0, 1.8V         FB = 01b         455         50         55         %           CMORMAL         Current Limit Foldback Factor in Normal<br>Operation         RTNS = DRNS = 1.8V         FB = 01b         455         50         555         %           CMORMAL         Current Limit Foldback Factor in Normal         RTNS = DRNS = 1.8V         FB = 01b         455         50         555         %           CMORMAL         Qurrent Limit Foldback Factor in Normal         RTNS = DRNS = 1.8V         FB = 01b         455         50         55         %           VILIM(FAST)         Fast Pull-Down Sense Threshold Voltage         ILIM = 0000b         15         20         30         40         mV           VILIM(FAST)         Fast Pull-Down Sense Threshold Voltage         ILIM = 1111b         477         60         70         mV           Velsex*         SENSE* Input Current         SENSE* SENSE* SENSE* 2         3  | V <sub>ILIM</sub>               | Current Limit Voltage DAC Zero-Scale  | ILIM = 0000b, C-Grade (Note 6<br>ILIM = 0000b, I-, H-Grade                             | 5)       | • | 14.7<br>14.5 | 15<br>15 | 15.3<br>15.5 | mV<br>mV |
| Current Limit Voltage DAC INL         •         0         ±50         µV $\alpha_{STARTUP}$ Current Limit Foldback Factor at Startup         RTNS = 1.8V, DRNS = 0, 1.8V         FB = 01b         •         45         50         55         % $\alpha_{NORMAL}$ Current Limit Foldback Factor in Normal<br>Operation         RTNS = DRNS = 1.8V         FB = 01b         •         45         50         55         % $PB = 01b$ •         45         50         55         %         FB = 10b         •         16         20         24         % $\alpha_{NORMAL}$ Current Limit Foldback Factor in Normal<br>Operation         RTNS = DRNS = 1.8V         FB = 01b         •         45         50         55         % $FB = 10b$ •         15         20         26         %         %         FB = 10b         •         16         20         30         40         mV $ILIM = 100b$ 0         ±1         MA         M  |                                 | Current Limit Voltage DAC Full-Scale  | ILIM = 1111b, C-Grade (Note 6)<br>ILIM = 1111b, I-, H-Grade                            |          | • | 29.4<br>29   | 30<br>30 | 30.6<br>31   | mV<br>mV |
| $ \frac{\alpha_{STARTUP}}{\alpha_{STARTUP}} \left\{ \begin{array}{c} Current Limit Foldback Factor at Startup} \\ \alpha_{NORMAL} \\ \alpha_{ORMAL} \\ \frac{Current Limit Foldback Factor in Normal}{Operation} \\ \end{array} \right  \left\{ \begin{array}{c} RTNS = 1.8V, DRNS = 0, 1.8V \\ \hline FB = 10b \\ PR = 11b \\ PR = 10b \\ PR = 11b \\ PR = 10b \\ PR = 11b \\ PR = 10b \\ $   |                                 | Current Limit Voltage DAC INL   |  |          | • |              | 0        | ±50          | μV       |
| $ \begin{array}{ c c c c c c c c c c c c c c c c c c c$  | α <sub>STARTUP</sub>            | Current Limit Foldback Factor at Startup                                      | RTNS = 1.8V, DRNS = 0, 1.8V  | FB = 01b |   | 45           | 50       | 55           | %        |
| $ \begin{array}{ c c c c c c c c c c c c c c c c c c c$  |                                 |   |  | FB = 10b |   | 16           | 20       | 24           | %        |
| $ \begin{array}{ccrc} c_{NORMAL} \\ c_{NORM$   |                                 |   |  | FB = 11b |   | 7            | 10       | 13           | %        |
| $ \begin{array}{ c c c c c c c c c c c c c c c c c c c$  | anormal                         | Current Limit Foldback Factor in Normal                                       | RTNS = DRNS = 1.8V   | FB = 01b |   | 45           | 50       | 55           | %        |
| $ \begin{array}{ c c c c c c c c c c c c c c c c c c c$  |                                 | Operation   |  | FB = 10b |   | 15           | 20       | 26           | %        |
| VILLM(FAST)         Fast Pull-Down Sense Threshold Voltage         ILIM = 0000b         ILIM = 0000b         ILIM = 0000b         ILIM = 1111b         ILIM = 1000b  |                                 |   |  | FB = 11b |   | 6            | 10       | 16           | %        |
| ILIM = 1111b         ●         47         60         70         mV           ISENSE <sup>+</sup> SENSE <sup>+</sup> Input Current         SENSE <sup>+</sup> = 33mV         ●         0         ±1         µA           ISENSE <sup>-</sup> SENSE <sup>-</sup> Input Current         SENSE <sup>-</sup> = SENSE <sup>+</sup> = 0         ●         -8         -17         -35         µA           TMR Pin Function         TMR Pull-Up Current in Current Limit<br>Onset<br>Startup in Foldback         DRNS = 0V, TMR = 1V         ●         -1.5         -2         -2.5         µA           DRNS = 0V, TMR = 1V         ●         -1.5         -2         -2.5         µA           DRNS = 0V, TMR = 1V         ●         -1.5         -2         -2.5         µA           DRNS = 1.8V, TMR = 1V         ●         -1.92         -202         -212         µA           FB = 01b         ●         -39         -42         -45         µA           FB = 10b         ●         -39         -42         -45         µA           FB = 10b         ●         -39         -42         -45         µA           TMR (DN)         TMR Pull-Down Current         DRNS = 1.8V, TMR = 1V         ●         -192         -202         -212         µA           TMR(DN)   | V <sub>ILIM(FAST)</sub>         | Fast Pull-Down Sense Threshold Voltage  | ILIM = 0000b   |          |   | 20           | 30       | 40           | mV       |
| $ \begin{array}{c c c c c c c c c c c c c c c c c c c $  |                                 |   | ILIM = 1111b   |          |   | 47           | 60       | 70           | mV       |
| Isense <sup></sup> SENSe <sup></sup> Input Current         SENSe <sup></sup> = SENSe <sup>+</sup> = 0        8         -17         -35         µA           TMR Pin Function         ITMR Pull-Up Current in Current Limit<br>Onset<br>Startup in Foldback         Immediate Current Immediate Current Limit<br>Onset         Immediate Current Immediate Current Limit<br>Onset         Immediate Current Immediate Current Limit<br>ONS = 1.8V, TMR = 1V         Immediate Current Immediate Current Immediate Current Immediate Current Immediate Current         Immediate Current Immediate Current         Immediate Current Immediate Current Immediate Current Immediate Current         Immediate Current Immediate Current Immediate Current Immediate Current         Immediate Current Immediate Current Immediate Current Immediate Current Immediate Current Immediate Current Immediate Current Immediate Current Immediate Current Immediate Current Immediate Current Immediate Current Immediate Current Immediate Current Immediate Current Immediate Current Immediate Current Immediate Current Immediate Immediate Current Immediate Immediate Current Immediate Immediate Immediate Current Immediate   | I <sub>SENSE</sub> +            | SENSE <sup>+</sup> Input Current  | SENSE <sup>+</sup> = 33mV  |          |   |              | 0        | ±1           | μA       |
| TMR Pin Function           ITMR (UP)         TMR Pull-Up Current in Current Limit<br>Onset<br>Startup in Foldback         DRNS = 0V, TMR = 1V         Image: Control Disabled,<br>DRNS = 1.8V, TMR = 1V         FB = 00b         Image: Control Disabled,<br>FB = 01b         FB = 00b         Image: Control Disabled,<br>FB = 01b         FB = 00b         Image: Control Disabled,<br>FB = 01b         FB = 01b         Image: Control Disabled,<br>FB = 01b         FB = 01b         Image: Control Disabled,<br>FB = 01b         FB = 01b         Image: Control Disabled,<br>FB = 11b         Image: Cont   | I <sub>SENSE</sub> <sup>-</sup> | SENSE <sup>-</sup> Input Current  | $SENSE^{-} = SENSE^{+} = 0$  |          |   | -8           | -17      | -35          | μA       |
| $ \begin{array}{ c c c c c c c c c c c c c c c c c c c$  | TMR Pin Fund                    | tion  | ·  |          |   |              |          |              |          |
| $\begin{array}{ c c c c c c c c c c c c c c c c c c c$   | I <sub>TMR(UP)</sub>            | TMR Pull-Up Current in Current Limit  |  |          |   |              |          |              |          |
| $ \begin{array}{ c c c c c c c c c c c c c c c c c c c$  |                                 | Onset   | DRNS = 0V, TMR = 1V  |          |   | -1.5         | -2       | -2.5         | μΑ       |
| $ \begin{array}{ c c c c c c c c c c c c c c c c c c c$  |                                 | Startup in Foldback   | dV/dt Control Disabled,  | FB = 00b |   | -192         | -202     | -212         | μA       |
| $\frac{FB = 10b}{FB = 11b} \bullet \frac{-39}{-20} -\frac{42}{-24} \mu A$ $\frac{FB = 10b}{FB = 11b} \bullet \frac{-20}{-20} -\frac{22}{-24} \mu A$ $\frac{FB = 10b}{FB = 11b} \bullet \frac{-20}{-20} -\frac{22}{-24} \mu A$ $\frac{FB = 10b}{FB = 11b} \bullet \frac{-20}{-20} -\frac{212}{-212} \mu A$ $\frac{FB = 10b}{FB = 11b} \bullet \frac{-20}{-20} -\frac{212}{-212} \mu A$ $\frac{FB = 10b}{FB = 11b} \bullet \frac{-20}{-20} -\frac{212}{-212} \mu A$ $\frac{FB = 10b}{FB = 11b} \bullet \frac{-20}{-20} -\frac{212}{-212} \mu A$ $\frac{FB = 10b}{FB = 11b} \bullet \frac{-20}{-20} -\frac{212}{-212} \mu A$ $\frac{FB = 10b}{FB = 11b} \bullet \frac{-20}{-20} -\frac{212}{-212} \mu A$ $\frac{FB = 10b}{FB = 11b} \bullet \frac{-20}{-20} -\frac{212}{-212} \mu A$ $\frac{FB = 10b}{FB = 11b} \bullet \frac{-20}{-20} -\frac{212}{-212} \mu A$ $\frac{FB = 10b}{FB = 10} \bullet \frac{-192}{-202} -\frac{202}{-212} \mu A$ $\frac{FB = 10b}{FB = 10} \bullet \frac{-192}{-202} -\frac{202}{-212} \mu A$ $\frac{FB = 10b}{FB = 10} \bullet \frac{-192}{-202} -\frac{202}{-212} \mu A$ $\frac{FB = 10b}{FB = 10} \bullet \frac{-192}{-202} -\frac{202}{-212} \mu A$ $\frac{FB = 10b}{FB = 10} \bullet \frac{-192}{-202} -\frac{202}{-212} \mu A$ $\frac{FB = 10b}{FB = 10} \bullet \frac{-192}{-202} -\frac{202}{-212} \mu A$ $\frac{FB = 10b}{FB = 10} \bullet \frac{-192}{-202} -\frac{202}{-212} \mu A$ $\frac{FB = 10b}{FB = 10} \bullet \frac{-192}{-202} -\frac{202}{-212} \mu A$ $\frac{FB = 10b}{FB = 10} \bullet \frac{-192}{-202} -\frac{202}{-212} \mu A$ $\frac{FB = 10b}{FB = 10} \bullet \frac{-192}{-202} -\frac{202}{-212} \mu A$ $\frac{FB = 10b}{FB = 10} \bullet \frac{-192}{-202} -\frac{202}{-212} \mu A$ $\frac{FB = 10b}{FB = 10} \bullet \frac{-192}{-202} -\frac{202}{-212} \mu A$ $\frac{FB = 10b}{FB = 10} \bullet \frac{-192}{-202} -\frac{20}{-212} \mu A$ $\frac{FB = 10b}{FB = 10} \bullet \frac{-192}{-20} -\frac{20}{2} -\frac{20}{FB} +\frac{10}{FB} +\frac{10}{FB}$ |                                 |   | DRNS = 1.8V, IMR = 1V  | FB = 01b |   | -96          | -102     | -108         | μA       |
| $\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$   |                                 |   |  | FB = 10b |   | -39          | -42      | -45          | μA       |
| $ \begin{array}{ c c c c c c c c c c c c c c c c c c c$  |                                 |   |  | FB = 11b |   | -20          | -22      | -24          | μA       |
| Hard Short in Normal OperationDRNS = 1.8V, TMR = 1V•192202212μAITMR(DN)TMR Pull-Down CurrentDRAIN < VD,FET(TH) or Start into dV/dt<br>Control, THERM_TMR = 0, TMR = 1V•1.622.3μAITMR(RST)TMR Reset CurrentEN# = High, TMR = 0, TMR = 1V•358mAVTMRH(TH)TMR Fault ThresholdTMR Rising•2.0282.0482.068VVTMRH(HYST)TMR Fault Hysteresis20mVVTMRL(TH)TMR Low Status ThresholdTMR Falling•80100120mVVTMRL(HYST)TMR Low Hysteresis20mVMVMV  |                                 | Startup in dV/dt  | dV/dt Control Enabled, DRNS =<br>TMR = 1V  | = 1.8V,  | • | -192         | -202     | -212         | μA       |
| ITMR(DN)TMR Pull-Down CurrentDRAIN < V_D,FET(TH) or Start into dV/dt<br>Control, THERM_TMR = 0, TMR = 1V1.622.3µAITMR(RST)TMR Reset CurrentEN# = High, TMR = 0, TMR = 1V•358mAV_TMRH(TH)TMR Fault ThresholdTMR Rising•2.0282.0482.068VV_TMRH(HYST)TMR Fault Hysteresis20mVmVV_TMRL(TH)TMR Low Status ThresholdTMR Falling•80100120mVV_TMRL(HYST)TMR Low Hysteresis20mVMVMV   |                                 | Hard Short in Normal Operation  | DRNS = 1.8V, TMR = 1V  |          |   | -192         | -202     | -212         | μA       |
| ITMR (RST)         TMR Reset Current         EN# = High, TMR = 1V         Image: 3 state   | I <sub>TMR(DN)</sub>            | TMR Pull-Down Current   | DRAIN < V <sub>D,FET(TH)</sub> or Start into dV/dt<br>Control, THERM_TMR = 0, TMR = 1V |          | • | 1.6          | 2        | 2.3          | μΑ       |
| VTMRH(TH)TMR Fault ThresholdTMR Rising2.0282.0482.068VVTMRH(HYST)TMR Fault Hysteresis20mVVTMRL(TH)TMR Low Status ThresholdTMR Falling80100120mVVTMRL(HYST)TMR Low Hysteresis20mVmV   | I <sub>TMR(RST)</sub>           | TMR Reset Current   | EN# = High, TMR = 1V   |          |   | 3            | 5        | 8            | mA       |
| VTMRH(HYST)TMR Fault Hysteresis20mVVTMRL(TH)TMR Low Status ThresholdTMR Falling●80100120mVVTMRL(HYST)TMR Low Hysteresis20mV  | V <sub>TMRH(TH)</sub>           | TMR Fault Threshold   | TMR Rising   |          |   | 2.028        | 2.048    | 2.068        | V        |
| VTMRL(TH)TMR Low Status ThresholdTMR Falling80100120mVVTMRL(HYST)TMR Low Hysteresis20mV  | V <sub>TMRH(HYST)</sub>         | TMR Fault Hysteresis  |  |          |   |              | 20       |              | mV       |
| V <sub>TMRL(HYST)</sub> TMR Low Hysteresis 20 mV   | V <sub>TMRL(TH)</sub>           | TMR Low Status Threshold  | TMR Falling  |          |   | 80           | 100      | 120          | mV       |
|  | V <sub>TMRL(HYST)</sub>         | TMR Low Hysteresis  |  |          |   |              | 20       |              | mV       |

|                          |  | <i>N &gt;</i> <b>N</b> <i>T</i> 2                 |                   |        | - `              | ,      |                  |       |
|--------------------------|--|---|-------------------|--------|------------------|--------|------------------|-------|
| SYMBOL                   | PARAMETER  | CONDITIONS  |                   |        | MIN              | TYP    | MAX              | UNITS |
| Input Pins               |  |   |                   |        |                  |        |                  |       |
| V <sub>UVH(TH)</sub>     | UVH Input Threshold  | UVH Rising  |                   |        | 2.028            | 2.048  | 2.068            | V     |
| V <sub>UVL(TH)</sub>     | UVL Input Threshold  | UVL Falling                                       |                   |        | 1.815            | 1.833  | 1.851            | V     |
| $\Delta V_{UV(HYST)}$    | Built-In UV Hysteresis                                     | UVH and UVL Tied Together                         |                   | •      | 204              | 215    | 226              | mV    |
| δV <sub>UV(HYST)</sub>   | UVH, UVL Minimum Hysteresis                                |   |                   |        |                  | 11     |                  | mV    |
| V <sub>UVLR(TH)</sub>    | UVL Reset Threshold  | UVL Falling                                       |                   | •      | 1                | 1.024  | 1.05             | V     |
| $\Delta V_{UVLR(HYST)}$  | UVL Reset Hysteresis                                       |   |                   |        |                  | 21     |                  | mV    |
| V <sub>OV(TH)</sub>      | OV Input Threshold   | OV Rising   |                   | •      | 1.392            | 1.406  | 1.42             | V     |
| $\Delta V_{OV(HYST)}$    | OV Input Hysteresis  |   |                   |        | 10               | 24     | 38               | mV    |
| V <sub>OUTL(TH)</sub>    | V <sub>OUT</sub> Low Threshold                             | RTNS – DRNS Falling, VOUT                         | TH = 0.8V         | •      | VOUTTH<br>- 0.06 | VOUTTH | VOUTTH +<br>0.06 | V     |
| $\Delta V_{OUTL(HYST)}$  | V <sub>OUT</sub> Low Hysteresis                            |   |                   |        |                  | 40     |                  | mV    |
| V <sub>EN#(TH)</sub>     | EN# Input Threshold  | EN# Falling                                       |                   | •      | 1.248            | 1.28   | 1.312            | V     |
| $\Delta V_{EN\#(HYST)}$  | EN# Input Hysteresis                                       |   |                   |        |                  | 18     |                  | mV    |
| V <sub>WP(TH)</sub>      | WP Input Threshold   | WP Rising   | WP Rising         |        | 1.2              | 1.65   | 2.1              | V     |
| $\Delta V_{WP(HYST)}$    | WP Input Hysteresis  |   |                   |        |                  | 100    |                  | mV    |
| V <sub>INPUT(TH)</sub>   | ADI01-4, PGI01-4 Input Threshold                           | ADI01-4, PGI01-4 Rising                           |                   |        | 1.248            | 1.28   | 1.312            | V     |
| $\Delta V_{INPUT(HYST)}$ | ADI01-4, PGI01-4 Input Hysteresis                          |   |                   |        |                  | 18     |                  | mV    |
| IINPUT                   | DRNS, EN#, OV, RTNS, UVL, UVH,<br>VOUTTH, WP Input Current | DRNS, EN#, OV, RTNS, UVL, UVH, VOUTTH,<br>WP = 3V |                   | •      |                  | 0      | ±1               | μA    |
| Output Pins              |  |   |                   | -<br>- |                  |        |                  |       |
| V <sub>OL</sub>          | ADI01-4, PGI01-4 Output Low Voltage                        | I = 5mA   |                   |        |                  | 0.15   | 0.4              | V     |
| I <sub>LEAK</sub>        | ADI01-4, PGI01-4 Leakage Current                           | ADI01-4 = INTV <sub>CC</sub> , PGI01-4            | = V <sub>IN</sub> |        |                  | 0      | ±1               | μA    |
| V <sub>REF</sub>         | VREF Output Voltage  | I <sub>VREF</sub> = -200μΑ, 0, 400μΑ              |                   | •      | 1.01             | 1.024  | 1.038            | V     |
| r <sub>REF</sub>         | V <sub>REF</sub> to ADC V <sub>FS</sub> Ratio              | I <sub>VREF</sub> = -200μA, 0, 400μA              |                   |        | 0.495            | 0.5    | 0.505            |       |
| ADC                      | ·  | ÷   |                   |        |                  |        |                  |       |
|                          | Resolution (No Missing Codes) (Note 6)                     | RTNS, ADIN1-4, ADI01-4,                           | ADC = 000b        |        | 8                |        |                  | Bits  |
|                          |  | DRNS, DRAIN, (SENSE+ –                            | ADC = 010b        |        | 10               |        |                  | Bits  |
|                          |  |   | ADC = 100b        | •      | 12               |        |                  | Bits  |
|                          |  |   | ADC = 110b        |        | 14               |        |                  | Bits  |
|                          |  |   | ADC = xx1b        |        | 14               | 16     |                  | Bits  |
|                          |  | (ADIN2 – ADIN1),                                  | ADC = 000b        |        | 7                |        |                  | Bits  |
|                          |  | (ADIN4 – ADIN3),                                  | ADC = 010b        | •      | 9                |        |                  | Bits  |
|                          |  | (ADIO4 – ADIO3)                                   | ADC = 100b        | •      | 11               |        |                  | Bits  |
|                          |  |   | ADC = 110b        |        | 13               |        |                  | Bits  |
|                          |  |   | ADC = xx1b        |        | 13               | 15     |                  | Bits  |

**ELECTRICAL CHARACTERISTICS** The  $\bullet$  denotes the specifications which apply over the full operating temperature range, otherwise specifications are at  $T_A = 25^{\circ}$ C,  $I_{IN} + I_{VZ} = 4$ mA with  $V_{IN}$  Connected to  $V_Z$ . (Note 2)

| SYMBOL                  | PARAMETER  | CONDITIONS  |               |   | MIN | ТҮР     | MAX          | UNITS             |
|-------------------------|--|---|---------------|---|-----|---------|--------------|-------------------|
| V <sub>FS</sub>         | Full-Scale Voltage   | Single-Ended Inputs Differential Inputs                                   |               |   |     | 2.048   |              | V                 |
|                         |  |   |               |   |     | 32.768  |              | mV                |
| LSB                     | LSB Step Voltage   | RTNS, ADIN1-4, ADIO1-4,   | ADC = 000b    |   |     | 8       |              | mV                |
|                         |  | DRNS, DRAIN   | ADC = 010b    |   |     | 2       |              | mV                |
|                         |  |   | ADC = 100b    |   |     | 0.5     |              | mV                |
|                         |  |   | ADC = 110b    |   |     | 0.125   |              | mV                |
|                         |  |   | ADC = xx1b    |   |     | 0.03125 |              | mV                |
|                         |  | SENSE <sup>+</sup> – SENSE <sup>-</sup>                                   | ADC = 000b    |   |     | 128     |              | μV                |
|                         |  |   | ADC = 010b    |   |     | 32      |              | μV                |
|                         |  |   | ADC = 100b    |   |     | 8       |              | μV                |
|                         |  |   | ADC = 110b    |   |     | 2       |              | μV                |
|                         |  |   | ADC = xx1b    |   |     | 0.5     |              | μV                |
|                         |  | ADIN2 – ADIN1,  | ADC = 000b    |   |     | 256     |              | μV                |
|                         |  | ADIN4 - ADIN3,<br>ADIO2 - ADIO1   | ADC = 010b    |   |     | 64      |              | μV                |
|                         |  | ADIO2 – ADIO1,<br>ADIO4 – ADIO3   | ADC = 100b    |   |     | 16      |              | μV                |
|                         |  |   | ADC = 110b    |   |     | 4       |              | μV                |
|                         |  |   | ADC = xx1b    |   |     | 1       |              | μV                |
| V <sub>OS</sub>         | Offset Error (Note 7)  | Single-Ended Inputs   |               |   |     | 0       | ±0.125       | % V <sub>FS</sub> |
|                         |  | Differential Inputs   |               |   |     | 0       | ±0.25        | % V <sub>FS</sub> |
| INL                     | Integral Nonlinearity (Note 7)                                 | ADIN1-4, ADIO1-4, RTNS, DI<br>SENSE <sup>+</sup> – SENSE <sup>-</sup>     | RNS, DRAIN,   | • |     | ±0.01   | ±0.06        | % V <sub>FS</sub> |
|                         |  | ADIN2 – ADIN1, ADIN4 – ADIN3,<br>ADIO2 – ADIO1,<br>ADIO4 – ADIO3          |               | • |     | ±0.02   | ±0.12        | % V <sub>FS</sub> |
| FSE                     | Full-Scale Error (Note 7)                                      | Single-Ended Inputs, C-Grade (Note 6)<br>Single-Ended Inputs, I-, H-Grade |               | • |     |         | ±0.5<br>±0.7 | %                 |
|                         |  | Differential Inputs, C-Grade (Note 6)<br>Differential Inputs, I-, H-Grade |               | • |     |         | ±1<br>±1.2   | %                 |
|                         |  | Power, C-Grade (Note 6)<br>Power, I-, H-Grade                             |               | • |     |         | ±1<br>±1.2   | %                 |
|                         |  | Energy  |               |   |     |         | ±5           | %                 |
| f <sub>CONV</sub>       | Refresh Rate in Continuous Mode (Table 12)                     |   |               | • |     |         | ±5           | %                 |
| R <sub>ADIN(SE)</sub>   | ADIN1-4, ADIO1-4 Input Impedance,<br>Single-Ended              | V = 3V  |               | • | 3   |         |              | MΩ                |
| I <sub>ADIN(SE)</sub>   | ADIN1-4, ADIO1-4 Input Current,<br>Single-Ended                | V = 3V  |               | • |     | 0       | ±1           | μA                |
| I <sub>ADIN(DIFF)</sub> | ADIN1, ADIN3, ADIO1, ADIO3 Input<br>Current, Differential Mode | ADIN1, ADIN3, ADIO1, ADIO<br>ADIN4, ADIO2, ADIO4 = 0                      | 3 = 0, ADIN2, | • |     | -3      | -7           | μA                |
|                         | ADIN2, ADIN4, ADIO2, ADIO4 Input<br>Current, Differential Mode | ADIN2, ADIN4, ADIO2, ADIO4 = 33mV   |               | • |     | 0       | ±1           | μA                |

| SYMBOL                     | PARAMETER  | CONDITIONS                        |   | MIN                          | ТҮР                          | MAX                          | UNITS  |
|----------------------------|--|-----------------------------------|---|------------------------------|------------------------------|------------------------------|--------|
| I <sup>2</sup> C Interface | 1  |                                   |   |                              |                              |                              | 1      |
| V <sub>ADR(H)</sub>        | ADR0, ADR1 Input High Threshold                        |                                   | • | INTV <sub>CC</sub><br>- 0.85 | INTV <sub>CC</sub><br>- 0.55 | INTV <sub>CC</sub><br>- 0.25 | V      |
| V <sub>ADR(L)</sub>        | ADR0, ADR1 Input Low Threshold                         |                                   |   | 0.4                          | 0.7                          | 1                            | V      |
| I <sub>ADR(IN)</sub>       | Allowable Leakage Current                              |                                   |   |                              |                              | ±10                          | μA     |
| V <sub>ALERT#(OL)</sub>    | ALERT# Output Low Voltage                              | I = 5mA                           |   |                              | 0.15                         | 0.4                          | V      |
| V <sub>SDAO(OL)</sub>      | SDAO Output Low Voltage                                | I = 20mA                          |   |                              | 0.25                         | 0.6                          | V      |
| I <sub>SDAO,ALERT#</sub>   | SDAO, ALERT# Input Current                             | SDAO, ALERT# = INTV <sub>CC</sub> |   |                              | 0                            | ±1                           | μA     |
| V <sub>SDAI,SCL(TH)</sub>  | SDAI, SCL Input Threshold                              |                                   |   | 1.5                          | 1.75                         | 2                            | V      |
| ISDAI,SCL                  | SDAI, SCL Input Current                                | SDAI, SCL = INTV <sub>CC</sub>    |   |                              | 0                            | ±1                           | μA     |
| I <sup>2</sup> C Interface | Fiming (Note 6)  |                                   |   |                              |                              |                              |        |
| f <sub>SCL(MAX)</sub>      | Maximum SCL Clock Frequency                            |                                   |   | 400                          |                              |                              | kHz    |
| t <sub>LOW</sub>           | Minimum SCL Low Period                                 |                                   |   |                              | 0.65                         | 1.3                          | μs     |
| t <sub>HIGH</sub>          | Minimum SCL High Period                                |                                   |   |                              | 50                           | 600                          | ns     |
| t <sub>BUF(MIN)</sub>      | Minimum Bus Free Time Between Stop/<br>Start Condition |                                   |   |                              | 0.12                         | 1.3                          | μs     |
| t <sub>HD,STA(MIN)</sub>   | Minimum Hold Time After (Repeated)<br>Start Condition  |                                   |   |                              | 140                          | 600                          | ns     |
| t <sub>su,sta(min)</sub>   | Minimum Repeated Start Condition<br>Set-Up Time        |                                   |   |                              | 30                           | 600                          | ns     |
| t <sub>SU,STO(MIN)</sub>   | Minimum Stop Condition Set-Up Time                     |                                   |   |                              | 30                           | 600                          | ns     |
| t <sub>HD,DATI(MIN)</sub>  | Minimum Data Hold Time Input                           |                                   |   |                              | -100                         | 0                            | ns     |
| t <sub>HD,DATO(MIN)</sub>  | Minimum Data Hold Time Output                          |                                   |   | 300                          | 600                          | 900                          | ns     |
| t <sub>SU,DAT(MIN)</sub>   | Minimum Data Set-Up Time Input                         |                                   |   |                              | 30                           | 100                          | ns     |
| t <sub>SP(MAX)</sub>       | Maximum Suppressed Spike Pulse Width                   |                                   |   | 50                           | 110                          | 250                          | ns     |
| t <sub>RST</sub>           | Stuck-Bus Reset Time                                   | SCL or SDAO Held Low              |   | 26                           | 30                           | 34                           | ms     |
| C <sub>X</sub>             | SCL, SDA Input Capacitance                             | SDAI Tied to SDAO                 |   |                              | 5                            | 10                           | pF     |
| Single-Wire E              | roadcast Timing  |                                   |   |                              |                              |                              |        |
| f <sub>BC</sub>            | Broadcast Data Rate (Table 11)                         |                                   |   |                              |                              | ±10                          | %      |
| EEPROM                     |  |                                   |   |                              |                              |                              |        |
|                            | Endurance  | 1 Cycle = 1 Write (Notes 8, 9)    |   | 10,000                       |                              |                              | Cycles |
|                            | Data Retention   | (Notes 8, 9)                      |   | 20                           |                              |                              | Years  |
| t <sub>WRITE</sub>         | EEPROM Write Time per Byte                             |                                   |   | 1.2                          | 2.2                          | 3                            | ms     |

### **ELECTRICAL CHARACTERISTICS**

**Note 1:** Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. Exposure to any Absolute Maximum Rating condition for extended periods may affect device reliability and lifetime.

**Note 2:** All Currents into device pins are positive and all currents out of device pins are negative. All voltages are referenced to  $V_{EE}$  unless otherwise specified.

**Note 3:** When  $V_Z$  is connected to  $V_{IN}$ , an internal shunt regulator limits the voltage to a minimum of 11V. Driving the pins above 11V may damage the part. These pins can be safely biased by a higher voltage using a resistor or current source that limits the current below 50mA.

**Note 4:** An internal clamp limits DRAIN to a minimum of 3.2V. Driving this pin to voltages above the clamp may damage the part. The pin can

be safely tied to higher voltages through a resistor that limits the current below 1.5mA.

**Note 5:** An internal clamp limits EN# to a minimum of 6V. Driving this pin to voltages above the clamp may damage the part. The pin can be safely tied to higher voltages through a resistor that limits the current below 5mA.

**Note 6:** Guaranteed by design and characterization. Not tested in production.

**Note 7:** Tested at 12-bit resolution and guaranteed for other resolutions by design and characterization.

**Note 8:** EEPROM endurance and retention are guaranteed by design, characterization and correlation with statistical process controls.

Note 9: EEPROM endurance and retention will be degraded when  $T_J > 85^{\circ}C$ .

## I<sup>2</sup>C TIMING DIAGRAM



### TYPICAL PERFORMANCE CHARACTERISTICS





**GATE Pull-Down Current vs** 

FAST PULL-DOWN

**SENSE Input Voltage** 

V<sub>GATE</sub> = 7V, V<sub>ILIM</sub> = 15mV

10

1

0.1

0.01

0.001

0

20



**GATE Output High Voltage vs** Leakage Current



**GATE Fast Pull-Down Current vs GATE Voltage** 



**Current Limit Voltage Error vs** 

40



**GATE Turn-Off Time vs SENSE Input Voltage** 



**Current Limit Foldback Profiles** 20 CURRENT LIMIT VOLTAGE (mV) -- 01 51 LPFB = 0FB = 00LPFB = 10. 10 POWER GOOD LATCHED  $V_{ILIM} = 15mV$ V<sub>RTNS</sub> = 1.8V 0 0 0.3 0.6 0.9 1.2 1.5 1.8 V<sub>RTNS</sub> - V<sub>DRNS</sub> (V) 4283 G09

**ILIM Code** 

SENSE INPUT VOLTAGE (mV)

CURRENT LIMIT

60

80

100

4283 G05

### **TYPICAL PERFORMANCE CHARACTERISTICS**



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### **TYPICAL PERFORMANCE CHARACTERISTICS**







16-Bit Voltage ADC Noise Histogram



12-Bit ADC Input Signal Attenuation (Extended Frequencies)



16-Bit Current ADC Noise Histogram



12-Bit ADC Input Signal Attenuation (Low Frequencies)



ADC FSE Shift Due to IR Reflow 20 **59 UNITS** 260°C 3 CYCLES INPUT = V<sub>ADIN1</sub> 15 NUMBER OF UNITS 10 5 0 -0.4 -0.2 0 0.2 0.4 0.6 FSE SHIFT (%) 4283 G26

VILIM Shift Due to IR Reflow



### PIN FUNCTIONS

**ADIN1 – ADIN4 (Pins 7 – 10):** ADC Inputs. A single-ended voltage between OV and 2.048V applied to each ADIN is measured by the on-chip ADC. Two differential voltages ADIN2 – ADIN1 and ADIN4 – ADIN3, if enabled, are also measured by the ADC with a full scale of 32.768mV. Connect to  $V_{EE}$  if unused.

**ADIO1 – ADIO4 (Pins 20 – 23):** General Purpose Inputs/ Outputs and ADC Inputs. Configurable to logic inputs and general purpose outputs (open-drain). See Table 13 for details. The single-ended voltages at ADIOs are measured by the ADC with a full scale of 2.048V. The differential voltages ADIO2 – ADIO1 and ADIO4 – ADIO3, if enabled, are also measured by the ADC with a full scale of 32.768mV. Connect to V<sub>EE</sub> if unused.

**ADR0, ADR1 (Pin 33, Pin 34):** Serial Bus Address Inputs. Connecting to  $V_{EE}$ , OPEN or INTV<sub>CC</sub> configures one of nine possible addresses, with one dedicated to the single-wire broadcast mode. Do not bias with an external supply. See Table 1 in Applications Information for address decoding.

**ALERT# (Pin 29):** Fault Alert Output. Open-drain logic output that pulls to  $V_{EE}$  when a fault occurs to alert the host controller. A fault alert is enabled by the FAULT\_ALERT and ADC\_ALERT registers. See Tables 15 and 16 in Applications Information for details. Connect to  $V_{EE}$  if unused.

**DRAIN (Pin 15):** Drain Sense Input. Connect an external 100k resistor between this pin and the drain terminal of the N-channel MOSFET. A DRAIN voltage below 2.048V is one of the conditions to assert power good outputs. When DRAIN voltage is above a voltage configurable between 72mV and 203mV, the FET Bad fault timer is started and the TMR output current is enabled when not in current limit. DRAIN is internally clamped to a minimum of 3.2V.

**DRNS (Pin 16):** Attenuated Drain Sense Input. Connect to the tap of an external resistive divider between the drain terminal of the N-channel MOSFET and  $V_{EE}$  to monitor the drain voltage. DRNS coupled with RTNS monitors the output voltage for the load, which controls dV/dt inrush current and current limit foldback. DRNS operates from 0 to 2.8V. Connect to  $V_{EE}$  if unused.

**EN# (Pin 1):** Device Enable Input. Pull low to enable the GATE output to turn-on after a startup debounce delay. When pulled high, GATE is turned off. A high-to-low transition clears faults. Transitions are recorded. Requires external pull-up. Debouncing with an external capacitor is recommended when used to monitor board present. Connect to  $V_{EE}$  if unused.

**Exposed Pad (Pin 39):** Exposed Pad may be left open or connected to device ground ( $V_{EE}$ ).

**GATE (Pin 14):** N-Channel MOSFET Gate Drive Output. GATE is pulled high by internal current sources (>80µA) when  $V_{IN}$  and INTV<sub>CC</sub> cross the UVLO thresholds, UV and OV conditions are satisfied, no other faults are present and the debounce delay expires. The GATE voltage higher than  $V_{IN} - 1.8V$  satisfies one of the conditions to assert power good outputs. Upon a low impedance output short, a 2.3A fast pull-down current is immediately activated.

**INTV<sub>CC</sub> (Pin 36):** 5V Internal Supply Output. The output of the internal linear regulator sources up to 30mA with an UVLO threshold of 4V. The supply powers the data converters, logic control circuitry,  $I^2C$  interface and EEPROM. Bypass with  $1\mu$ F capacitor to V<sub>EE</sub>. INTV<sub>CC</sub> is not current limited. When driving INTV<sub>CC</sub> with an external supply, V<sub>IN</sub> and V<sub>Z</sub> must be left open or connected to INTV<sub>CC</sub>.

**OV (Pin 4):** Overvoltage Detection Input. Connect to an external resistive divider from  $V_{EE}$ . When OV is above its threshold of 1.406V, the GATE output pulls low to turn off the MOSFET and an overvoltage fault is recorded. The overvoltage fault does not affect the status of the power good outputs. Connect to  $V_{EE}$  if unused.

**PGI01, PGI02 (Pin 24, Pin 25):** General Purpose Inputs/Outputs. Configurable to sequenced, inverted and non-inverted power good outputs, general purpose logic inputs and open-drain outputs. See Table 12 in Application Information for details. If the PGI02\_ACLB bit in CONTROL\_1 register 0x0A is set, PGI02 is configured as inverted current limit engagement indicator after startup. Connect to V<sub>EE</sub> if unused.

### PIN FUNCTIONS

**PGI03 (Pin 26):** General Purpose Input/Output. Configurable to inverted and non-inverted power good watchdog input (PGI# and PGI), general purpose logic input and open-drain output. See Table 12 in Application Information for details. Connect to V<sub>EE</sub> if unused.

**PGI04 (Pin 27):** General Purpose Input/Output. Configurable to inverted and non-inverted external fault input (EXT\_FAULTIN# and EXT\_FAULTIN), general purpose logic input and open-drain output. See Table 12 in Application Information for details. Connect to INTV<sub>CC</sub> if unused.

**RAMP (Pin 18):** Ramp Control. Connect a capacitor between RAMP and  $V_{EE}$  to set inrush current in dV/dt startup mode. During the dV/dt control, RAMP acts as an attenuated output and feeds a fixed 2.5µA current through the RAMP capacitor to set the slew rate of the output voltage. The dV/dt inrush control is disabled after startup when power good signals are asserted. Leave open if unused.

**RTNS (Pin 17):** RTN Sense Input. Connect to the tap of an external resistive divider between RTN and  $V_{EE}$  to monitor the board input voltage. When selected, the RTNS voltage is measured by the ADC and used to calculate the input power. Monitors the output voltage for the load when coupled with DRNS, which controls dV/dt inrush current and current limit foldback. Operates from 0V to 2.8V. Connect to INTV<sub>CC</sub> if unused.

**SCL (Pin 32):** Serial Bus Clock Input. Data at SDAI is shifted in and data at SDAO is shifted out on rising edges of SCL. This is a high impedance input that is generally connected to the output of the incoming isolator driven by the SCL port of the master controller. An external pull-up resistor or current source is required. Pull up to  $INTV_{CC}$  if unused.

**SDAI (Pin 31):** Serial Bus Data Input. This is a high impedance input used for shifting in command bits, data bits, and SDAO acknowledge bits. An external pull-up resistor or current source is required. Normally connected to the output of the incoming isolator that is driven by the SDA port of the master controller. Pull up to INTV<sub>CC</sub> if unused.

**SDAO (Pin 30):** Serial Bus Data Output. Open-drain output used for sending data back to the master controller or acknowledging a write operation. An external pull-up resistor or current source is required. Normally connected to the input of the outgoing isolator that outputs to the SDA port of the master controller. In the single-wire broadcast mode, SDAO sends out selected data that is Manchester encoded with an internal clock. The broadcast bit rate is configurable between 2Mbit/s and 32kbit/s.

**SENSE<sup>+</sup>** (Pin 13): Positive Current Sense Kelvin Input. Connect to the high side of the current sense resistor. The active current limit amplifier controls GATE to limit the sense voltage SENSE<sup>+</sup> – SENSE<sup>-</sup> from 15mV to 30mV, configurable in 1mV steps. SENSE<sup>+</sup> – SENSE<sup>-</sup> is also measured by the ADC with a full scale of 32.768mV. Connect to V<sub>EE</sub> if unused.

**SENSE<sup>-</sup> (Pin 12):** Negative Current Sense Kelvin Input. Connect to the low side of the current sense resistor.

**TMR (Pin 19):** Timer Current Output. The current sourced out of TMR is proportional to the power dissipation in the MOSFET. If an RC network that represents the thermal behavior of the MOSFET is connected between TMR and V<sub>EE</sub>, the voltage at TMR represents the real-time temperature rise of the MOSFET. When the TMR voltage reaches its threshold of 2.048V that corresponds to  $T_{J(MAX)}$  of the MOSFET, GATE pulls low to turn off the MOSFET and an overcurrent fault is logged. If a single capacitor is connected between TMR and V<sub>EE</sub>, TMR sets the delay for MOSFET turn-off based on the power dissipation in the MOSFET. In this mode the 2µA pull-down current must be enabled to discharge the capacitor when the MOSFET power drops to near zero. When EN# is low, TMR is discharged by a 5mA current. Connect to V<sub>EE</sub> if unused.

### PIN FUNCTIONS

**UVH (Pin 3):** Undervoltage High Level Input. Connect to an external resistive divider from  $V_{EE}$ . If UVH rises above 2.048V and UVL is above 1.833V, the GATE output pulls high to turn on the MOSFET. A capacitor of at least 10nF between UVH and  $V_{EE}$  prevents transients and switching noise from affecting the UV threshold. Connect to INTV<sub>CC</sub> if unused.

**UVL (Pin 2):** Undervoltage Low Level Input. Connect to an external resistive divider from  $V_{EE}$ . If UVL drops below 1.833V and UVH is below 2.048V, the MOSFET is turned off. Pulling below 1.024V resets faults and allows the MOSFET to turn back on when undervoltage is cleared. Connect to INTV<sub>CC</sub> if unused.

 $V_{EE}$  (Pin 11 and Pin 28): Negative Supply Voltage Input and Device Ground. Connect to the negative side of the power supply. The connection between any component and device ground must be made to a dedicated plane that connects directly to V<sub>EE</sub>, not to the main current-carrying trace of -48V on the board.

 $V_{IN}$  (Pin 37): Positive Supply Input to the Device. Connect to  $V_Z$  directly or through an external buffer transistor driven by  $V_Z$ . The voltage at  $V_{IN}$  is internally regulated at 11.5V. An undervoltage lockout (UVLO) circuit holds the GATE output low until  $V_{IN}$  is above 8.1V. Bypass with at least 0.1µF capacitor to  $V_{EE}$ . If it is desired to log fault information into EEPROM upon brown-out, bypass  $V_{IN}$  with at least 68µF capacitor to  $V_{EE}$  (See Applications Information for details).

**VOUTTH (Pin 6):** Output Low Threshold Input. Connect to an external reference voltage for output voltage low threshold. RTNS – DRNS below VOUTTH sets the  $V_{OUT}$  low status bit. RTNS – DRNS above VOUTTH satisfies one of the conditions to assert power good outputs. Connect to  $V_{EE}$  if unused.

**VREF (Pin 5):** Reference Voltage Output. Regulated at 1.024V or half of the ADC full-scale. Sources up to  $200\mu$ A and sinks up to  $400\mu$ A. It can drive a capacitive load of up to 10nF. Leave open if unused.

 $V_Z$  (Pin 38): Shunt Regulator Input. Operates with a bias of 20µA to 30mA. Connect to the positive supply (RTN) through a dropping resistor. To supply external loads with  $V_{\rm IN}$ , use  $V_Z$  to drive an external buffer transistor with the emitter or source connected to  $V_{\rm IN}$ . Bypass with a 0.1µF capacitor to  $V_{\rm EE}$ .

**WP (Pin 35):** EEPROM Write Protect Input. All write operations to the EEPROM except fault logging are blocked when the voltage at WP is above 1.65V.

### **BLOCK DIAGRAM**



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### OPERATION

The LTC4283 is designed to turn a board's supply voltage on and off in a controlled manner, allowing the board to be safely inserted or removed from a live, power system. In normal operation after a startup debounce delay, the LTC4283 turns on the external N-channel MOSFET, passing the power to the load. The inrush control during startup is configurable between two methods. One is programmable active current limiting with an adjustable foldback factor. The other is constant dV/dt ramp control of the output voltage using a capacitor connected between RAMP and V<sub>EE</sub>. The inrush current is a function of the RAMP capacitor, the load capacitor and the attenuated load voltage seen between RTNS and DRNS.

An 11.5V shunt regulator on  $V_{IN}$  powers the LTC4283 with an external dropping resistor from the system RTN node. It also provides the gate drive. An optional buffer transistor driven by  $V_Z$  boosts sourcing capability to supply external loads.

An internally generated 5V supply on  $INTV_{CC}$  supplies the logic control circuits, communication interface, data converters and EEPROM. Prior to turning on the MOSFET, both V<sub>IN</sub> and  $INTV_{CC}$  voltages must exceed their undervoltage lockout thresholds. In addition, the control inputs UVH, UVL, OV, EN#, PGIO3 and PGIO4 are monitored by comparators. The MOSFET is held off until all startup conditions are met.

The DRAIN, RTNS – DRNS and GATE voltages are monitored to determine if power is available for the load. Two power good signals are sequenced on PGIO1 and PGIO2, each with a delay that is twice the startup debounce delay. Additionally, PGIO3 serves as a watchdog input to monitor the output of the DC/DC module. If the module output fails to come up, the LTC4283 turns off the MOSFET. PGIO4 defaults as an external fault input (inverted). PGIO1-4 can also be configured into general purpose inputs or outputs.

An overcurrent fault at the output may result in excessive MOSFET power dissipation during Active Current Limiting (ACL). To limit this power, the ACL amplifier regulates the SENSE<sup>+</sup> – SENSE<sup>-</sup> voltage at precise, programmable values (15mV to 30mV in 1mV steps). When the output voltage is low, power dissipation is further reduced by folding back the current limit, with the foldback ratio configurable to 10%, 20%, or 50% of nominal. In the event of a catastrophic output short when the sensed current is twice of the current limit, fast response comparator immediately pulls the GATE pin down with 2.3A.

When active current limiting is engaged, TMR is pulled up by a current that is proportional to the power dissipation in the MOSFET. With an RC network representing the thermal behavior of the MOSFET connected between TMR and V<sub>FF</sub>, the TMR voltage is proportional to the temperature rise in the MOSFET. When TMR voltage reaches its threshold of 2.048V (representing  $T_{J(MAX)}$  of the MOSFET), the overcurrent fault is logged and GATE turns off, allowing protection of the MOSFET based on true SOA. TMR can also be configured to drive a single capacitor. Following the overcurrent fault, the LTC4283 can either latch off the MOSFET or auto-retry after a cooling delay. Both the retry delay and the number of retries are configurable, too. The LTC4283 also logs and responds to other faults including overvoltage, undervoltage, FET bad, Power Good Input (PGI) fault, FET short and external fault.

Included in the LTC4283 is a pair of analog to digital converters (ADCs). The ADCs are configurable from 8-bit at 1kHz to 16-bit at 1Hz in five settings. As shown in the Block Diagram, ADC1 continuously monitors the current sense voltage between SENSE<sup>+</sup> and SENSE<sup>-</sup>. ADC2 is synchronized to ADC1 and measures the attenuated input voltage at RTNS or the attenuated MOSFET drain voltage at DRNS plus one of the fourteen auxiliary inputs. Every time the ADCs finish taking a measurement, the current sense voltage is multiplied by the measurement. Every time power is measured, it is added to an energy accumulator that tracks the input energy or the energy consumption of the MOSFET. The energy accumulator can generate an optional alert upon overflow, and can

### OPERATION

be preset to allow it to overflow after a given amount of energy is reached. A time accumulator tallies energy increments; dividing the results of the energy accumulator by the time accumulator gives the average system power. The minimum and maximum of each ADC measurement and power are stored, and optional alerts may be generated if a measurement is above or below user configurable 8-bit thresholds.

An internal EEPROM provides nonvolatile configuration of the LTC4283 operation behaviors and parameters. It also records fault information and selected ADC data. Seven bytes of uncommitted memory are reserved for general purpose storage.

An I<sup>2</sup>C/SMBus interface accesses the ADC data registers and allows the host to poll the device and determine if a fault has occurred. If the ALERT# line is used as an interrupt, the host can respond to a fault in real time. A reboot command turns off the MOSFET and automatically restarts after a configurable delay. The SDA line is divided into SDAI (input) and SDAO (output) to facilitate opto-coupling with the system host. Two three-state pins, ADR0 and ADR1, are used to decode eight device addresses.

The communication interface can also be configured through ADR0 and ADR1 for a single-wire broadcast mode, sending ADC data and faults status through SDA0 to the host without clocking the SCL line. This single-wire, one-way communication simplifies system design by eliminating two opto-couplers on SCL and SDAI that are required by an I<sup>2</sup>C interface. The transmission speed is configurable from 32kHz to 2MHz with four settings.

### **APPLICATIONS INFORMATION**

The LTC4283 is ideally suited for high availability distributed power systems, allowing a board to be safely inserted or removed from a live negative voltage backplane. Figure 1 shows a basic 600W application circuit. Figure 2 shows a more complete application circuit in a dual-feed system with board insertion detection and opto-coupling.

### Input Power Supply

The LTC4283 features a floating topology that allows a wide operating voltage range and is robust to faults. For a –48V system, supply to the LTC4283 is derived from the –48V RTN through an external shunt resistor R<sub>IN</sub> to the V<sub>IN</sub> and V<sub>Z</sub> pins (Figure 1). An internal shunt regulator clamps V<sub>IN</sub> to 11.5V relative to V<sub>EE</sub> and provides power to the GATE driver. V<sub>Z</sub> acts as the shunt path of the regulator. A bypass capacitor of at least 0.1µF is recommended between V<sub>IN</sub>/V<sub>Z</sub> and V<sub>EE</sub>. If EEPROM fault log is enabled

(see Fault Log), the minimum bypass capacitance at  $V_{\rm IN}$  for the fault log operation to complete upon an undervoltage or power loss condition is

$$C_{\text{IN}} \geq 15 \left[\frac{\mu F}{mA}\right] \bullet (I_{\text{IN}(\text{MAX})} + I_{\text{EXTERNAL}})$$

An internal 5V linear regulator that derives from the 11.5V supply powers data converters, logic control circuits,  $I^2C$  interface and EEPROM. The 5V output is available at the INTV<sub>CC</sub> pin for driving external circuits. A bypass capacitor of 1µF is recommended between INTV<sub>CC</sub> and V<sub>EE</sub>. To only test data converters or program EEPROM, the main –48V supply is not needed. Instead, a 5V supply may be applied between INTV<sub>CC</sub> and V<sub>EE</sub>, with V<sub>IN</sub> and V<sub>Z</sub> connected to INTV<sub>CC</sub>.

 $R_{IN}$  should be chosen to accommodate the maximum supply current requirement of the LTC4283 ( $I_{IN(MAX)} = 4mA$ ) plus the supply current required by any external devices



Figure 1. –48V/600W Hot Swap Controller with SOA Timer and Current Limited Inrush Control

driven by  $V_{IN}$  and  $INTV_{CC}$  at the minimum supply voltage,  $V_{S(MIN)}$  and the maximum  $V_{IN}$  voltage,  $V_{IN(MAX)}$ :

$$R_{IN} \leq \frac{V_{S(MIN)} - V_{IN(MAX)}}{I_{IN(MAX)} + I_{EXTERNAL}}$$

The maximum power dissipation in the resistor is

$$P_{MAX} = \frac{\left(V_{S(MAX)} - V_{IN(MIN)}\right)^2}{R_{IN}}$$

If the power dissipation of  $R_{\rm IN}$  is too high for a single resistor, use multiple resistors in series, which provides additional clearance spacing for high voltage surges. Another option uses an external NPN transistor ( $Q_{\rm IN}$ ) as illustrated in Figure 2b. Each of  $V_{\rm IN}$  and  $V_Z$  should be bypassed with a capacitor of at least  $0.1 \mu F.$  In this case  $R_Z$  is chosen according to

$$R_{Z} \leq \frac{V_{S(MIN)} - V_{IN(MAX)} - V_{BE}}{\frac{I_{IN(MAX)} + I_{EXTERNAL}}{\beta} + 20\mu A}$$

where  $V_{BE}$  and  $\beta$  are the base-emitter voltage and DC current gain of the NPN transistor, respectively and 20  $\mu$ A represents the minimum V<sub>Z</sub> operating current. The maximum power dissipation of Q<sub>IN</sub> is

$$P_{QIN,MAX} = (V_{S(MAX)} - V_{IN(MIN)}) \bullet I_{IN(MAX)}$$

 $R_{IN}$  or  $R_Z$  may be split into multiple segments in order to achieve the desired standoff voltage or dissipation. Whereas 1206 size resistors are commonly rated for 200V working and 400V peak, pad spacing and circuit board design rules may limit the working rating to as little as 100V.

For applications at very high voltages (>300V), a high voltage MOSFET can be used. Figure 3 shows an application circuit with a depletion mode N-channel MOSFET that can withstand up to 1000V drain-to-source voltage. In this case  $R_Z$  is chosen according to

$$R_{Z} \leq \frac{V_{S(MIN)} - V_{IN(MAX)} - V_{GS}}{20\mu A}$$

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Figure 2a. -48V/600W Dual-Feed Hot Swap Controller with LTC4283 (Part One)

where  $V_{GS}$  is the gate-to-source voltage of the MOSFET (positive for an enhancement mode and negative for a depletion mode transistor). When using an enhancement mode transistor,  $V_Z$  voltage must be kept lower than its absolute maximum of 16V:

$$V_{Z(MAX)} = V_{IN(MAX)} + V_{GS} < 16V$$

In Figure 2b and Figure 3, the voltage drop and power dissipation in the NPN or the MOSFET may be augmented by the use of one or more resistors in series with the collector or drain. If an external 12V supply is available on the application board, it may be used to drive the  $V_{\rm IN}$  pin directly as shown in Figure 4.

#### **Turn-On Sequence**

The following conditions must be satisfied before the turn-on sequence is started. First the voltage at  $V_{\rm IN}$  must exceed the undervoltage lockout level of 8.1V. Next the

internal supply INTV<sub>CC</sub> must cross its 4V undervoltage lockout level. This generates a 1.3ms power-on-reset delay. After the delay times out, the voltages at UVH, UVL and OV must satisfy UVH > 2.048V, UVL > 1.833V and OV < 1.406V to indicate that the input power is within the acceptable range, and EN# must be pulled low. All the above conditions must be satisfied throughout the duration of the startup debounce delay of 128ms. If any of the above conditions is violated during the delay, the delay is reset and restarted. After the delay expires, if the ON bit in CONTROL 1 register 0x0A is high, the LTC4283 turns on the MOSFET. Otherwise, the MOSFET will be turned on (without additional delay) when the ON bit is set to 1 through the I<sup>2</sup>C interface. When all turn-on conditions are satisfied, the FET\_ON\_STATUS bit in SYSTEM\_STATUS register 0x00 is set to 1, indicating the MOSFET is commanded on.



Figure 2b. -48V/600W Dual-Feed Hot Swap Controller with LTC4283 (Part Two)



Figure 3. The LTC4283 Can Operate to >300V Using a Depletion Mode N-Channel MOSFET



Figure 4. Using an External 12V Supply

The turn-on sequence continues by charging up GATE with 100µA current source. When the GATE voltage reaches the MOSFET threshold voltage, the MOSFET begins to turn on and the inrush current charges the load capacitor  $C_L$  to ramp the MOSFET drain towards  $V_{EE}$  in a controlled manner (see Inrush Control). When the MOSFET drain is ramped down to  $V_{EE}$  or the output is ramped up to the supply voltage, GATE is pulled up to  $V_{IN}$  and the MOSFET is fully enhanced. The GATE\_HIGH bit in SYSTEM\_STATUS register 0x00 is set when GATE is above  $V_{IN} - 1.8V$ . Figure 5 illustrates the startup sequence of the LTC4283.

During the power-on-reset delay of 1.3ms, the fault registers are cleared and the control registers are loaded with the data held in the corresponding EEPROM registers. The power-on-reset can be detected using the PORB bit in register 0x0E, which will be cleared when  $INTV_{CC}$  dips below 3.8V. Set this bit to 1 in normal operating conditions and keep monitoring this bit. A 0 from subsequent reading indicates a power-on-reset has occurred.





#### **Inrush Control**

Inrush current control can be configured in two ways. First, if the DVDT bit in CONTROL\_1 register 0x0A is set to 1, the inrush current is controlled in dV/dt mode by an external capacitor connected between RAMP and V<sub>EE</sub> (the RAMP capacitor, C<sub>R</sub>), as shown in Figure 6. In dV/dt mode, the inrush current is limited by controlling a constant output voltage ramp rate (dV/dt). During startup, when the GATE voltage reaches the MOSFET threshold voltage, RAMP outputs a fixed 2.5µA current to charge C<sub>R</sub> while the inrush current charges load capacitor C<sub>L</sub>. During dV/dt control the LTC4283 regulates the RAMP to the attenuated load voltage between RTNS and DRNS with an offset:

 $V_{RAMP} = V_{RTNS} - V_{DRNS} + 0.18V$ 

and regulates the inrush current to a fixed value that is a function of the attenuation ratio, r and the ratio between load capacitance and RAMP capacitance:

$$I_{\text{INRUSH}} = 2.5 \mu \text{A} \cdot \text{r} \cdot \frac{\text{C}_{\text{L}}}{\text{C}_{\text{R}}}$$

The attenuation ratio r is set by the external resistive dividers at RTNS ( $R_{RT}$  and  $R_{RB}$ ) and DRNS ( $R_{DT}$  and  $R_{DB}$ ) in Figure 6:

$$r = \frac{R_{RT} + R_{RB}}{R_{RB}} = \frac{R_{DT} + R_{DB}}{R_{DB}}$$

RTNS and DRNS represent the attenuated input voltage and MOSFET drain voltage, respectively. The differential



voltage between RTNS and DRNS therefore represents the attenuated load voltage. The operation range of  $V_{\text{RTNS}}$ ,  $V_{\text{DRNS}}$  and  $V_{\text{RTNS}} - V_{\text{DRNS}}$  is from 0V to 2.8V.

The dV/dt control is only active during initial startup. After the turn-on sequence is completed and power good signals are activated, the dV/dt inrush control mode is disabled and RAMP is discharged with a 4mA current. RAMP will also be discharged under any GATE turn-off conditions. In the dV/dt mode the inrush current must be set lower than the folded back current limit level to avoid triggering the current limit (see below).

The second inrush control mechanism is active current limiting. This is enabled by clearing the DVDT bit in CONTROL\_1 register 0x0A. In this mode the inrush current is regulated to the folded back current limit:

 $I_{INRUSH} = I_{LIM} \bullet \alpha_{STARTUP}$ 

where I<sub>LIM</sub> is the current limit and  $\alpha_{STARTUP}$  is the startup foldback factor. I<sub>LIM</sub> is determined by the current limit sense voltage V<sub>ILIM</sub> and the sense resistance R<sub>S</sub>.

$$I_{\text{LIM}} = \frac{V_{\text{ILIM}}}{R_{\text{S}}}$$

 $V_{ILIM}$  is configurable from 15mV to 30mV in 1mV steps.  $\alpha_{STARTUP}$  is configurable to 10%, 20%, 50% and 100% (no foldback) of current limit. During startup the current limit foldback profile is flat and does not change with output voltage. See Current Limit Adjustment and Current Limit Foldback for details. In this mode the RAMP capacitor C<sub>R</sub> at the RAMP pin no longer takes effect. If C<sub>R</sub> is omitted, RAMP must be left open.

#### **Power Good Monitors and PGI Fault**

After the MOSFET is turned on, the following conditions must be met before the power good signals are activated. First, the DRAIN voltage must fall below 2.048V to indicate the MOSFET drain is low. Second, RTNS – DRNS must be higher than the external threshold voltage at VOUTTH to indicate the output voltage is high. Last, GATE voltage must satisfy the GATE high (>V<sub>IN</sub> – 1.8V) condition. When all three conditions are met, an internal power good signal is latched, the PG\_STATUS bit in SYSTEM\_STATUS register 0x00 is set, and a series of three delay cycles are started

as illustrated in Figure 5. When the first delay of 256ms expires, the first power good signal PGIO1 turns on the first load. When the second delay of 256ms expires, the second power good signal PGIO2 can be used to turn on a second load.

Following the two 256ms delays, a third delay of 512ms is started for monitoring PGIO3 as a power good input (PGI) watchdog. Before this delay expires, PGIO3 must be pulled low or high (polarity configurable by register 0x10) by an external supply monitor to indicate the load is working properly. Otherwise, the MOSFET is turned off and a PGI fault is logged in FAULT register 0x04. The MOSFET is allowed to auto-retry after a delay of 128ms following the PGI fault if the PGI\_RETRY bit in CONTROL\_2 register 0x0B is set to 1. Both power good signals and the power good input can be configured into inverted or non-inverted polarity using PGIO\_CONFIG\_1 register 0x10 (see Table 12). To disable the PGI watchdog, connect PGIO3 to V<sub>EE</sub> or INTV<sub>CC</sub> depending on the configured polarity, or configure PGIO3 as general purpose input or output using register 0x10.

Power good signals are reset in two configurable ways. If the PWRGD\_RESET\_CNTRL bit in CONTROL\_1 register 0x0A is set to 1, power good signals are reset by an output low condition as indicated by RTNS – DRNS < VOUTTH. In Figure 2a VOUTTH is biased at 0.8V, so power good signals will be reset when RTNS – DRNS drops below 0.8V, which corresponds to  $V_{OUT}$  < 32V. If the PWRGD\_RESET\_CNTRL bit is cleared, power good signals are reset by any GATE turn-off conditions except overvoltage fault. When the power good signals are reset, the power good delays and the PGI delay are also reset.

#### **Turn-Off Sequence**

In any of the following conditions, the MOSFET is turned off by pulling down the GATE pin with 18mA current source and the FET\_ON\_STATUS bit in SYSTEM\_STATUS register 0x00 is cleared.

- 1.  $V_{IN}$  is lower than 7.6V ( $V_{IN}$  undervoltage lockout).
- 2.  $\text{INTV}_{\text{CC}}$  is lower than 3.8V (INTV\_{\text{CC}} undervoltage lockout).
- 3. EN# is high.
- 4. ON bit in CONTROL\_1 register 0x0A is cleared.

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- 5. OV is higher than 1.406V (overvoltage fault).
- 6. UVL is lower than 1.833V and UVH is lower than 2.048V (undervoltage fault).
- 7. TMR reaches its 2.048V threshold (overcurrent fault).
- 8. DRAIN rises above 2.048V or GATE dips below  $V_{\text{IN}}$  1.8V and this condition lasts longer than a preconfigured delay (FET bad fault).
- 9. PGI03, when configured as PGI#/PGI input, is high/ low when the PGI check delay of 512ms expires (PGI fault).
- 10. PGIO4 pin, when configured as EXT\_FAULT#/EXT\_ FAULT, is low/high (external fault).
- 11. The RBT\_EN bit in REBOOT register 0xA2 is set.

For condition 8, if the FET\_BAD\_TURN\_OFF bit in CONTROL\_1 register 0x0A is cleared, the MOSFET remains on following a FET bad fault. For condition 10, if the EXT\_FAULT\_TURN\_OFF bit in CONFIG\_3 register 0x0F is cleared, the MOSFET remains on following an external fault. For condition 11, the LTC4283 will automatically reboot after a programmable delay. See Reboot on I<sup>2</sup>C Command. For each independent GATE turn-off fault, the LTC4283 can be configured to latch off the MOSFET or go into an auto-retry sequence after the fault occurs.

### **Overcurrent Protection**

The LTC4283 features two levels of protection from shortcircuit and overcurrent conditions. Load current is monitored by SENSE<sup>+</sup> and SENSE<sup>-</sup> pins and sense resistor. There are two distinct thresholds for the sense voltages: V<sub>ILIM</sub> and V<sub>ILIM(FAST)</sub>. V<sub>ILIM</sub> is configurable from 15mV to 30mV in 1mV steps and V<sub>ILIM(FAST)</sub> is always twice V<sub>ILIM</sub>. See Current Limit Adjustment for details.

If the sense voltage reaches V<sub>ILIM</sub>, GATE is pulled down by 50mA current until the active current limit loop is engaged. In the event of a catastrophic short-circuit or a sudden input step, where the sense voltage reaches V<sub>ILIM(FAST)</sub>, the GATE is immediately pulled down by a 2.3A current to limit peak current through the MOSFET. When the sense voltage drops to V<sub>ILIM</sub>, the active current limit loop is engaged.

### SOA Timer

During active current limit, the power dissipation in the MOSFET is large. If this power dissipation persists, the MOSFET can reach temperatures that cause damage. MOSFET manufacturers specify the safe limits on operating voltage, current and time as a curve referred to as the Safe Operating Area (SOA). Commonly, a circuit breaker timer sets a maximum time for the MOSFET to operate in a current limit mode. When this timer expires, the MOSFET is turned off to protect it from overheating. Traditional circuit breakers often employ a fixed current charging an external capacitor. The minimum timer timeout must be set to allow the worst-case operating condition, such as completely charging a large bypass capacitor at output during startup or riding through a large input step. Then upon fault conditions such as an output short-circuit at full supply voltage, the MOSFET must withstand the large power throughout the entire timer duration. Therefore, the MOSFET must be selected to withstand the worstcase SOA condition that occurs during any possible normal operating condition or fault condition. This not only substantially increases the cost of the MOSFET, but also complicates the design procedure and MOSFET selection.

The LTC4283 features a circuit breaker timer that better fits the SOA of the MOSFET. When active current limit is engaged, the OC STATUS bit in FAULT STATUS register 0x03 is set, and the TMR pin is activated and charged up by a current proportional to the power dissipation in the MOSFET. A proper electric model (RC network) is selected to represent the thermal behavior of the MOSFET. When this RC network is connected between TMR and  $V_{EE}$ , the TMR voltage is proportional to the rise in the MOSFET junction temperature. The LTC4283 compares the TMR voltage to a fixed threshold voltage of 2.048V, which represents the maximum allowable junction temperature rise in the MOSFET. When the TMR voltage crosses this threshold, the LTC4283 turns off the MOSFET. Therefore, to provide an appropriate protection of a MOSFET, one simply selects the MOSFET that meets the SOA requirement for allowable operating conditions such as startup and input step. The MOSFET is automatically turned off before it is subject to any condition that would exceed its SOA rating.

**Case 1.** If active current limit is engaged in normal operation (power good signals are asserted), the TMR pull-up current of the LTC4283 is proportional to the attenuated drain voltage of the MOSFET at DRNS (top line in Figure 7). This is proportional to the power dissipation since the current through the MOSFET is fixed during current limit (provided that foldback is disabled in normal operation by setting the FB\_DIS bit in CONFIG\_1 register 0x0D). The TMR pull-up current in this condition is:

$$I_{\text{TMR}(\text{UP})} = 111.1 \left[\frac{\mu A}{V}\right] \cdot V_{\text{DRNS}} + 2\mu A$$

where  $111.1\mu$ A/V is the transconductance. The TMR pullup current reaches  $202\mu$ A at V<sub>DRNS</sub> = 1.8V, which is tested and specified. The offset of  $2\mu$ A is introduced to guarantee a minimum pull-up current that prevents TMR from hanging in a resistive short-circuit condition.

The above equation also applies to startup in dV/dt mode (DVDT bit in CONTROL\_1 register 0x0A = 1), when the current limit is triggered under a fault condition such as a short-circuit. The accelerated timeout combined with startup foldback (see Current Limit Foldback) protects MOSFET from overstress.



Figure 7. TMR Pull-Up Current vs  $\Delta V_{SENSE}$  and DRNS Voltage

*Case 2.* During startup in dV/dt mode when current limit is not engaged, TMR pull-up current is disabled:

 $I_{TMR(UP)} = 0$ 

In this case a  $2\mu$ A pull down current holds TMR low if the THERM\_TMR bit in control register 0x0A is set. This avoids undesired timeout before the load capacitor is fully charged by the inrush current, which is set to such a low level that the power dissipation in MOSFET is insignificant.

**Case 3.** If current limit is engaged during startup in current limit mode (DVDT bit in CONTROL\_1 register 0x0A = 0), the TMR pull-up current is reduced by the foldback ratio:

$$I_{\text{TMR}(\text{UP})} = \alpha_{\text{STARTUP}} \bullet 111.1 \left[\frac{\mu A}{V}\right] \bullet V_{\text{DRNS}} + 2\mu A$$

where  $\alpha_{\text{STARTUP}}$  is the startup foldback ratio that is controlled by the FB bits in CONFIG\_1 register 0x0D (see Current Limit Foldback). The reduction keeps the transconductance unchanged compared to that in normal operation with foldback disabled.

**Case 4.** If current limit is not engaged, either in normal operation or during startup in current limit mode, the TMR pull-up current is gated by the DRAIN voltage. If DRAIN is lower than its threshold,  $V_{D,FET(TH)}$ , the TMR pull-up current is disabled.  $V_{D,FET(TH)}$  is programmable from 72mV to 203mV in geometric scale using the VDTH bits in CONFIG\_2 register 0x0E. This is a typical case in normal operating conditions when the MOSFET is fully enhanced. If DRAIN is higher than  $V_{D,FET(TH)}$ , an internal multiplier charges up TMR with a current approximately proportional to power dissipation in the MOSFET:

If 
$$\Delta V_{\text{SENSE}} \ge 0.1 V_{\text{ILIM}}$$
,  
 $I_{\text{TMR}(\text{UP})} = 111.1 \left[ \frac{\mu A}{V} \right] \bullet V_{\text{DRNS}} \bullet \left( \frac{\Delta V_{\text{SENSE}}}{V_{\text{ILIM}}} - 0.1 \right) + 2\mu A$ 

If  $\Delta V_{SENSE} < 0.1 V_{ILIM}$ ,  $I_{TMR(UP)} = 2\mu A$ 

Figure 7 shows the TMR pull-up currents vs  $V_{DRNS}$  at four different  $\Delta V_{SENSE}$  levels below current limit.

If using an RC network representing the MOSFET thermal model between TMR and  $V_{EE}$ , the THERM\_TMR bit in CONTROL\_1 register 0x0A must be set to 1 to disable the internal 2µA pull-down current. The total resistance in the RC network provides the discharge path to TMR.

The configuration of the RC network for a particular MOSFET starts with selection of a desired number of resistive and capacitive elements and their values in thermal domain based on the thermal impedance plot provided by the MOSFET manufacturer. Three resistors and three capacitors are usually enough to fit the plot fairly well from 10µs to 100ms, which covers the timing range of typical operating and fault conditions. Two resistors and two capacitors may provide an acceptable accuracy for some MOSFETs or conditions. If better fitting accuracy or wider fitting range is desired, more elements may be used. After the thermal RC network is configured, the thermal quantities are then converted to electric quantities according to

$$R_{E} = k \bullet R_{\theta}$$
$$C_{E} = \frac{C_{\theta}}{k}$$

where  $R_E$  and  $C_E$  are electric resistance and capacitance, respectively and  $R_\theta$  and  $C_\theta$  are thermal resistance and capacitance, respectively. The conversion constant k is given by

$$k = \frac{V_{DS,MAX} \bullet I_{D,MAX}}{I_{TMR}(UP),MAX} \bullet \frac{V_{TMR}(TH)}{\Delta T_{MAX}}$$

where V<sub>DS,MAX</sub> and I<sub>D,MAX</sub> are the maximum drainto-source voltage and maximum drain current of the MOSFET, respectively, I<sub>TMR(UP),MAX</sub> is the TMR pull-up current corresponding to the maximum power dissipation P<sub>MAX</sub> = V<sub>DS,MAX</sub> • I<sub>D,MAX</sub>, V<sub>TMR(TH)</sub> is TMR threshold voltage (2.048V), and  $\Delta$ T<sub>MAX</sub> is the maximum allowable temperature rise of the MOSFET. For example, if V<sub>DS,MAX</sub> = 72V, I<sub>D,MAX</sub> = 32A, I<sub>TMR(UP),MAX</sub> = 202µA (at V<sub>DRNS</sub> = 1.8V, in current limit) and  $\Delta$ T<sub>MAX</sub> = 65°C (maximum junction temperature of MOSFET = 150°C and ambient temperature = 85°C), k = 3.6 • 10<sup>5</sup> [V<sup>2</sup>/°C]. An RC network consisting of two resistors and capacitors that represent the electric model for the thermal behavior of PSMN4R8-100BSE is show in Figure 2a.

The LTC4283 also allows a single capacitor connected between TMR and  $V_{EE}$  (see Figure 13). In this case, the THERM\_TMR bit in the CONTROL\_1 register must be cleared to enable the internal 2µA pull-down current.

Once enabled, the 2µA pull-down current keeps TMR low in normal conditions when the pull-up current is disabled. When the pull-up current is enabled under fault conditions, the 2µA pull-down is switched off. A minimum capacitance must be selected to keep the MOSFET on during worst-case operating conditions, and the MOSFET must be selected to withstand the worst-case SOA condition during normal operating or fault conditions. Regardless of the value of the THERM\_TMR bit, when EN# is higher than its 1.28V threshold, TMR is discharged by a 5mA current. When TMR is below 0.1V, the TMR\_LOW bit in SYSTEM\_STATUS register 0x00 is set to 1.

### **Overcurrent Fault and Auto-Retry**

Under an overcurrent condition, when the active current limit loop is engaged and TMR is being charged up, the overcurrent present bit, OC\_STATUS, in FAULT\_STATUS register 0x03 is set. When the TMR voltage reaches its 2.048V threshold, the overcurrent fault bit, OC\_FAULT, in the FAULT register 0x04 is set and the GATE pin is pulled down to turn off the MOSFET.

After the MOSFET is turned off, the OC\_STATUS bit is cleared. The MOSFET is allowed to turn on again after a cooling delay if the OC RETRY bits in CONTROL 2 register 0x0B have not been cleared. The auto-retry cooling delay is configurable from 512ms to 65.5s in binary scale using the COOLING DL bits in CONFIG 2 register 0x0E (See Table 11). During the cooling delay the DELAY\_STATUS bit in REBOOT register 0xA2 is set to 1 to indicate the delay timer is running. It will be cleared when the delay expires. The number of retries following an overcurrent fault can be configured to 1, 7 or infinity using the OC RETRY bits (see Table 10). If a finite retry number is selected, a retry counter reset timer of 16.4s is started upon the retry following an overcurrent fault. If the next overcurrent fault occurs before the timer times out, the retry counter increments and the timer is restarted. Otherwise the retry counter is restarted. When the programmed number of retries is reached, the MOSFET will be latched off if the next overcurrent fault occurs before the counter reset timer times out. During startup when power good conditions are not met, the counter reset timer is disabled. The retry counter and the counter reset timer for the overcurrent fault are independent of those for the FET bad fault.

If the OC\_RETRY bits in the CONTROL\_2 register 0x0B have been cleared, the MOSFET will remain off until the OC\_FAULT bit is reset (see Resetting Faults). When the OC\_FAULT bit is reset, the MOSFET is allowed to turn on after the auto-retry delay expires.

#### **Current Limit Adjustment**

The current limit voltage, V<sub>ILIM</sub>, is programmable between 15mV and 30mV in 1mV steps through the I<sup>2</sup>C interface using the ILIM bits in CONFIG 1 register 0x0D. The default values are stored in EE CONFIG 1 register 0xAD in the onboard EEPROM. The fast GATE pull-down sense voltage, VILIM(FAST), is set to twice of VILIM through the whole configuration range. The fine scales are useful in adjusting the sense voltage to achieve a given current limit using the limited selection of standard sense resistor values available around  $1m\Omega$ . The adjustability allows the LTC4283 to reduce available current for light loads or increase it in anticipation of a surge. This feature also enables the use of board-trace as sense resistors by trimming the sense voltage to match measured copper resistance during final test. The measured copper resistance may be written to the undedicated scratch pad area of the EEPROM (0xE9-0xEF) so that it is available to scale ADC current measurements.

#### **Current Limit Foldback**

The LTC4283 current limit can be configured to fold back to four levels: 10%, 20%, 50% and 100% (no foldback) of full current limit using the FB bits in the CONFIG\_1 register 0x0D. During the startup inrush control the foldback profile is flat (Figure 8a), resulting in a constant current limit. This is to protect the MOSFET more effectively upon a resistive output short during startup. With a traditional resistive foldback profile, if the output short resistance is the same as the slope of the foldback profile, the foldback has no effect and a MOSFET with larger SOA must be selected to withstand the full stress, substantially increasing the MOSFET cost.

After the internal power good signal is latched (see Power Good Monitors and PGI Fault), the LTC4283 goes into normal operation and the foldback is determined by the attenuated output voltage for the load, RTNS – DRNS

(Figure 8b). If the output voltage or RTNS – DRNS drops to OV in an event such as a catastrophic output short, the current limit sense voltage is folded back to the ratio configured by the FB bits. As shown in Figure 8b, the foldback ratio increases linearly with RTNS – DRNS and reaches 100% when RTNS – DRNS reaches 0.9V, which corresponds to the minimum supply voltage of an application. Above 0.9V the current limit sense voltage stays constant unless the load power foldback (LPFB) bit in the CONFIG\_1 register 0x0D is set. If the LPFB bit is set, the current limit sense voltage decreases linearly to 50% when RTNS – DRNS reaches 1.8V (corresponding to the maximum supply voltage). This profile approximately tracks the load power when the output voltage increases with a constant power load.



Figure 8a. Current Limit Foldback During Startup





The LTC4283 foldback profile can differentiate an output short fault from an allowed input step. Upon an output short, RTNS – DRNS drops and current limit is folded back to protect the MOSFET from overstress. In the event of an input step, RTNS – DRNS increases while the load is charged up. The current limit either stays constant or approximates constant load power (based on the LPFB bit) to approach the optimum output ramp and minimize the temperature rise of the MOSFET (see Input Step and Optimum Output Ramp). This is superior to a foldback profile capacitance based upon V<sub>DS</sub> or power dissipation of the MOSFET. In that case, the output short and input step conditions cannot be differentiated, often resulting in unwanted turn-off upon an input step.

Foldback in normal operation can be independently disabled by setting the FB\_DIS bit in the CONFIG\_1 register 0x0D. With this configuration foldback is only effective during startup, and it should only be used when an RC network representing the thermal model of the MOSFET is connected to TMR. If a single capacitor is used, it is recommended to enable foldback in normal operation by clearing the FB\_DIS bit for more conservative protection of the MOSFET. Note that the load power foldback controlled by the LPFB bit is not affected by the FB\_DIS bit.

### FET Bad Fault and Auto-Retry

In a hot swap application several possible faults can prevent the MOSFET from turning on fully. A damaged MOSFET may have leakage from gate to drain or have degraded  $R_{DS(ON)}$ . Debris on the board may also produce leakage or a short from the GATE pin to  $V_{EE}$  or the MOSFET drain. In these conditions the LTC4283 may not be able to pull the GATE pin high enough to fully enhance the MOSFET, or the MOSFET may not reach the intended  $R_{DS(ON)}$  when the GATE pin is fully enhanced. This can put the MOSFET in a condition where the power in the MOSFET is higher than its continuous power capability, even though the current is below the current limit. The LTC4283 monitors the integrity of the MOSFET in two ways, and acts on both of them in the same manner.

First, the LTC4283 monitors the MOSFET drain voltage at the DRAIN pin. A comparator detects a DRAIN high condition whenever DRAIN is above a reference voltage,  $V_{D,FET(TH)}$  that can be configured to 72mV, 102mV, 143mV or 203mV (geometric scale) using the VDTH bits in the CONFIG\_2 register 0x0E. Second, the LTC4283 monitors the GATE voltage. If the MOSFET is turned on, but the GATE voltage is lower than  $V_{IN}$  – 1.8V, a GATE low condition is detected.

When either a DRAIN high or a GATE low condition is present when the MOSFET is commanded on, the FET\_BAD\_STATUS bit in FAULT\_STATUS register 0x03 is set and an internal FET bad fault timer is started. The FTBD\_DL bits in CONFIG\_2 register 0x0E configures the timer duration to 256ms, 512ms, 1.02s and 2.05s. If the DRAIN voltage falls below V<sub>D,FET(TH)</sub> and the GATE low condition is cleared before the timer times out, the FET\_BAD\_STATUS bit is cleared and the timer is reset. If the timer does time out, the FET\_BAD\_FAULT bit in FAULT register 0x04 is set and the MOSFET is turned off if the FET\_BAD\_TURN\_OFF bit in CONTROL\_1 register 0x0A has been set. The DRAIN high condition also activates TMR pull-up current when not in current limit (see SOA Timer).

Note that during startup while the load is being charged, the FET\_BAD\_STATUS bit is set and the FET bad fault timer is running. To avoid undesired turn-off, the timer duration must be configured long enough for the load to be fully charged.

After the MOSFET is turned off following a FET bad fault. the FET\_BAD\_STATUS bit is cleared. The MOSFET is allowed to turn on again after a cooling delay if the FET BAD\_RETRY bits in CONTROL\_2 register 0x0B have not been cleared. The cooling delay is the same as that for an overcurrent fault and is configurable from 512ms to 65.5s in binary scale using the COOLING\_DL bits in CONFIG\_2 register 0x0E (see Table 11). During the cooling delay the DELAY STATUS bit in REBOOT register 0xA2 is set. It will be cleared when the delay expires. The FET\_BAD\_RETRY bits configures the number of retries following a FET bad fault to 1, 7 or infinity (see Table 10). If a finite retry number is selected, a retry counter reset timer of 16.4s is started upon the retry following a FET bad fault. If the next FET bad fault occurs before the timer expires, the retry counter increments and the timer is reset. Otherwise the

retry counter is reset. The retry counter and the counter reset timer for the FET bad fault are independent of those for the overcurrent fault.

If the FET\_BAD\_RETRY bits in CONTROL\_2 register 0x0B have been cleared, the MOSFET will remain off until the FET\_BAD\_FAULT bit is reset (see Resetting Faults) or the FET\_BAD\_TURN\_OFF bit is cleared through I<sup>2</sup>C. In either of those two cases, the MOSFET is allowed to turn on after the auto-retry delay expires.

#### Input Step and Optimum Output Ramp

In events such as battery hot swapping or supply surge, the input voltage may experience a sudden step. The magnitude of the input step,  $\Delta V$ , can be as large as tens of volts. As long as the input voltage does not exceed the overvoltage limit, the input step is not a fault condition and the system should stay on and operate through it. In the presence of the load capacitor, the output does not follow the input immediately, but rather ramps up from the initial supply voltage to the new supply voltage while charging the load capacitor. The V<sub>DS</sub> of the MOSFET initially jumps to  $\Delta V$  and then ramps down. Additionally, during the output ramp the MOSFET not only carries the load current, I<sub>1</sub> but also the capacitance charging current, I<sub>CI</sub>, so the total power dissipation in the MOSFET can be very large. If a large input step is possible, it is usually the worst-case operating condition for the SOA of the MOSFET, and a proper MOSFET must be selected to withstand the stress.

In such a condition, the minimum temperature rise of the MOSFET is achieved when  $I_{CL}$  matches  $I_L$ , or the total current is twice the load current. In other words, the current limit should be set to twice the load current during the output ramp:

$$I_{\text{LIM(OPT)}} = 2 \bullet I_{\text{L}}$$

This is in contrast to the concept of foldback that is used to protect the MOSFET in a short-circuit condition. The foldback profile of the LTC4283 automatically takes care of both input step and output short-circuit conditions by relating the foldback ratio to the output voltage for the load instead of  $V_{DS}$  of the MOSFET. See Figure 8b and

Current Limit Foldback for details. Additionally, if the load follows a constant power relationship, the LPFB bit in CONFIG\_1 register 0x0D can be set to enable load power foldback so that the current limit approximately tracks twice the load current during the output ramp. The waveforms in Figure 9 show how the LTC4283 responds to a -36V to -72V input step to achieve the optimum output ramp rate. Note that the power good signals on PGIO1 and PGIO2 are not interrupted during an input step.



Figure 9. LTC4283 Responds to –36V to –72V Input Step with a Constant Power Load

#### **Overvoltage Fault and Auto-Retry**

The OV pin can be used to monitor a supply overvoltage condition using an external resistive divider. An overvoltage fault occurs when OV rises above its 1.406V threshold. This condition turns off the MOSFET immediately and sets the OV\_STATUS bit in FAULT\_STATUS register 0x03 and the OV\_FAULT bit in FAULT register 0x04. Note that the power good signals are not affected by the overvoltage fault. If OV subsequently falls back below the threshold

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minus hysteresis of 24mV, the OV\_STATUS bit is cleared and the MOSFET will be allowed to turn on again (without delay) unless overvoltage auto-retry has been disabled by clearing the OV\_RETRY bit in CONTROL\_2 register 0x0B.

#### **Undervoltage Fault and Auto-Retry**

The LTC4283 features two undervoltage pins, UVH and UVL, for precise undervoltage monitoring and adjustable hysteresis. UVH has an accurate rising threshold:

 $V_{UVH(TH)} = 2.048V$ , UVH rising

UVL has an accurate falling threshold:

V<sub>UVL(TH)</sub> = 1.833V, UVL falling

Both pins have a small built-in hysteresis,  $\delta V_{UV}$  (11mV typical). With either a rising or a falling input supply, the undervoltage comparator works in such a way that both UVH and the UVL have to cross their threshold for the comparator output to change state.

The UVH, UVL and OV threshold ratio is designed to match the standard telecom operating range of 43V to 71V and UV hysteresis of 4.5V when UVH and UVL are connected together as in Figure 1, where the UV hysteresis referred to UVL is:

 $\Delta V_{UV(HYST)} = V_{UVH(TH)} - V_{UVL(TH)} = 0.215V$ 

Using R1 = 10k, R2 = 14.3k and R3 = 487k as in Figure 1 gives a typical operating range of 43.1V and 70.7V, with an undervoltage shutdown threshold of 38.6V and an overvoltage shutdown threshold of 71.9V.

The UV hysteresis can be adjusted by separating UVH and UVL with a resistor  $R_H$  as shown in Figure 10. To increase the UV hysteresis, place the UVL tap above the UVH tap as in Figure 10a. To reduce the UV hysteresis, place the UVL tap under the UVH tap as in Figure 10b. UV hysteresis referred to UVL is given by:

If 
$$V_{UVL} \ge V_{UVH}$$
,  

$$\Delta V_{UVL(HYST)} = \Delta V_{UV(HYST)} + 2.048 V \bullet \frac{R_{H}}{R1 + R2}$$

If  $V_{UVL} < V_{UVH}$ ,

 $\Delta V_{\text{UVL}(\text{HYST})} = \Delta V_{\text{UV}(\text{HYST})} - 2.048 \text{V} \bullet \frac{\text{R}_{\text{H}}}{\text{R1} + \text{R2} + \text{R}_{\text{H}}}$ 



Figure 10. Adjustment of Undervoltage Thresholds for Larger (10a) or Smaller (10b) Hysteresis

In the latter case, the minimum UV hysteresis allowed is the built-in hysteresis of UVH and UVL:

 $\Delta V_{UVL(HYST,MIN)} = \delta V_{UV} = 11 \text{mV}$ 

which occurs when  $\mathsf{R}_\mathsf{H}$  reaches its maximum value:

 $R_{H(MAX)} = 0.11 \bullet (R1 + R2)$ 

LTC4283 ensures that the UV comparator is immune to chattering even when  $R_H$  is larger than  $R_{H(MAX)}$ .

An undervoltage fault occurs when UVL falls below 1.833V and UVH falls below 2.048V –  $\delta V_{UV}$ . This condition turns off the MOSFET and sets the UV\_STATUS bit in FAULT\_STATUS register 0x03 and the UV\_FAULT bit in FAULT register 0x04.

Following the undervoltage fault, the UV\_STATUS bit is cleared when the UVH pin rises above 2.048V and UVL rises above 1.833V +  $\delta V_{UV}$ . After a delay of 128ms, the MOSFET will be allowed to turn on again unless the undervoltage auto-retry has been disabled by clearing the UV\_RETRY bit in CONTROL\_2 register 0x0B.

When power is applied to the device, if UVL is below the 1.833V threshold and UVH is below 2.048V –  $\delta V_{UV}$  after INTV<sub>CC</sub> crosses its undervoltage lockout threshold of 4V, an undervoltage fault will be logged in FAULT register 0x04 and can be cleared using the I<sup>2</sup>C interface after power-up.

Because of the compromises of selecting from a table of discrete resistor values (1% resistors in 2% increments, 0.1% resistors in 1% increments), best possible OV and UV accuracy is achieved using separate dividers for each pin, This increases the total number of resistors from three or four to as many as six, but maximizes accuracy, greatly simplifies calculations and facilitates running changes to accommodate multiple standards or custom-ization without any board changes.

To improve noise immunity, put the resistive divider to the UV and OV pins close to the chip and keep traces to RTN and  $V_{EE}$  short. A 0.1µF capacitor from UVH or UVL (and OV through resistor R2 as in Figure 10) to  $V_{EE}$  helps reject supply noise.

#### **FET Short Fault**

A FET short fault will be reported if the data converter measures a current sense voltage between SENSE<sup>+</sup> and SENSE<sup>-</sup> greater than  $255\mu$ V while the MOSFET is turned off. This condition sets the FET\_SHORT\_STATUS bit in FAULT\_STATUS register 0x03 and the FET\_SHORT\_FAULT bit in FAULT register 0x04.

#### **Power Failed Fault**

The LTC4283 continuously monitors the output voltage for the load. The differential voltage between RTNS and DRNS represents the attenuated output voltage for the load. An output low status will be reported if RTNS – DRNS is lower than the external reference voltage at VOUTTH. This condition sets the VOUT\_LOW status bit in FAULT\_STATUS register 0x03. If this condition occurs after the internal power good signal is latched, the POWER\_FAILED fault bit in FAULT register 0x04 will also be set. This fault does not turn off the MOSFET. After RTNS – DRNS rises above VOUTTH, the VOUT\_LOW bit is cleared.

#### **External Fault and Auto-Retry**

PGIO4 can be configured as EXT\_FAULT# or EXT\_FAULT using PGIO\_CONFIG\_1 register 0x10 bits [7:6] to monitor an external fault condition. If the input polarity is configured as EXT\_FAULT#, an external fault occurs when PGIO4 falls below its 1.28V threshold. This condition sets the EXT\_FAULT\_STATUS bit in FAULT\_STATUS register 0x03 and the EXT\_FAULT bit in FAULT register 0x04. This condition also turns off the MOSFET if the EXTFLT\_TURN\_OFF bit in CONFIG\_3 register 0x0F has been set. When PGIO4 subsequently rises above 1.28V, the EXT\_FAULT\_STATUS bit is cleared. After an auto-retry delay, the MOSFET will be allowed to turn on again unless the external fault auto-retry has been disabled by clearing the EXT\_FAULT\_RETRY bit in CONTROL\_2 register 0x0B. The auto-retry delay for the external fault is configurable from 512ms to 65.5s in binary scale using the COOLING\_DL bits in CONFIG\_2 register 0x0E. During the delay the DELAY\_STATUS bit in REBOOT register 0xA2 is set to 1. It will be cleared when the delay expires.

In Figure 11, PGIO4 is configured as EXT\_FAULT and used to monitor MOSFET temperature. When the MOSFET temperature rises above 115°C, the EXT\_FAULT bit in FAULT register 0x04 is set and the MOSFET is turned off.

If the EXTFLT\_TURN\_OFF bit in CONFIG\_3 register 0x0F has been cleared, an external fault condition at PGI04 will not turn off the MOSFET. Regardless of the value of the EXTFLT\_TURN\_OFF bit, if the EXT\_FAULT\_ALERT bit in FAULT\_ALERT register 0x15 is set, the high state of the EXT\_FAULT bit in FAULT register 0x04 will generate an alert by pulling ALERT# low.

PGI01-4 and ADI01-4, when configured as general purpose inputs, can be used to monitor external conditions without turning the MOSFET off or generating alerts. If any of these pins is pulled above the 1.28V threshold, the associated input status bit in INPUT\_STATUS register 0x02 is set.





#### **Cooling Delay**

The cooling delay (configurable by the COOLING\_DL bits, 0x0E [3:1]) after an overcurrent fault, FET bad or external Rev. 0

fault, will not be interrupted by any other fault. If, before expiration of the cooling delay, another overcurrent, FET bad or external fault occurs, the cooling delay will restart and extend the total cooling time. During the cooling delay the DELAY\_STATUS bit 0xA2 [1] is set to indicate the delay timer is running. This bit resets when the delay expires. The cooling delay can be terminated by initiating an I<sup>2</sup>C reboot command, and is also terminated by UVLO (INTV<sub>CC</sub> < 3.8V).

#### **Resetting Faults**

Faults are reset with any of the following conditions. First, writing zeros to FAULT register 0x04 will clear the associated fault bits. Second, the entire FAULT register is cleared when the ON bit in CONTROL\_1 register 0x0A goes from high to low, or if INTV<sub>CC</sub> falls below its 3.8V undervoltage lockout. EN# falling from high to low also clears the entire FAULT register. Finally, when UVL is pulled below its 1.024V reset threshold, all fault bits in the FAULT register are cleared. When UVL is brought back above 1.024V but below 1.833V, the UV\_FAULT bit is set if UVH is below 2.048V. This can be avoided by holding UVH above 2.048V while toggling UVL to reset faults.

Fault bits with associated fault conditions that are still present (as indicated in FAULT\_STATUS register 0x03) cannot be cleared. The FAULT register will not be cleared when auto-retrying. When auto-retry of a specific GATE turnoff fault is disabled using CONTROL\_2 register 0x0B, the existence of the associated fault bit keeps the MOSFET off. After the fault bit is cleared and the associated retry delay expires, the MOSFET is allowed to turn on again. If auto-retry of a fault is enabled, then a high state of the associated fault status bit in 0x03 will hold the MOSFET off and the FAULT register is ignored. Subsequently, when the condition causing the fault is cleared (and so is the fault status bit in 0x03), the MOSFET is allowed to turn on again.

#### Alarms

Besides the fault bits and the EN#\_CHANGED bit, the LTC4283 also logs ADC alarms in ADC\_ALARM\_LOG registers 0x05-0x09 when ADC results are higher than the pre-configured MAX thresholds or lower than the

pre-configured MIN thresholds. In addition, when the tick counter or energy meter overflows, the TICK\_OVERFLOW bit or METER\_OVERFLOW bit is logged into METER\_CONTROL register 0x84. Finally, when EEPROM is written through I<sup>2</sup>C, the EEPROM\_WRITTEN bit is logged into ADC\_ALARM\_LOG register 0x05. Similar to the fault bits, these alarm bits indicate the history of corresponding conditions and do not reflect the present status of the conditions. Any alarm bit can only be reset by two methods: writing a zero to the alarm bit using I<sup>2</sup>C or bringing INTV<sub>CC</sub> below its undervoltage lockout voltage.

#### EN# Pin

EN# has a 1.28V logic threshold relative to  $V_{EE}$  with a maximum leakage current of 1µA at 3V. It must be pulled low and remain low during the 128ms debounce delay. When the delay expires, the MOSFET is allowed to turnon. An internal clamp limits EN# to a minimum of 6V. The pin can be safely connected to higher voltages through a resistor that limits the current up to 5mA. It can be used to monitor board present as shown in Figure 2.

The EN# bit in SYSTEM\_STATUS register 0x00 indicates the present state of EN#, and the EN#\_CHANGED bit in ADC\_ALARM\_LOG\_1 register 0x05 is set high whenever EN# changes state. The EN#\_CHANGED bit can be cleared using the same methods as those for resetting faults (see Resetting Faults) except pulling EN# from high to low. Pulling EN# from high to low sets the EN#\_CHANGED bit while clearing the entire FAULT register 0x04.

#### ON Bit

The ON bit in CONTROL\_1 register 0x0A allows one to turn on (ON bit = 1) and turn off (ON bit = 0) the MOSFET through the  $I^2C$  interface. There is no debounce delay associated with this bit, so the MOSFET is immediately turned on after the bit is flipped from 0 to 1 while all other turn-on conditions are met.

When the ON bit is changed from 1 to 0, the MOSFET is turned off and all bits in FAULT register 0x04 plus the EN#\_CHANGED bit in ADC\_ALARM\_LOG\_1 register 0x05 are cleared.

#### Turning the LTC4283 On and Off

Many methods of on/off control are possible using the EN#, UV/OV, PGIO3 or PGIO4 pins along with the I<sup>2</sup>C port. EN# works well with logic inputs or floating switch contacts; I<sup>2</sup>C control is intended for systems where the board operates only under command of a central control processor and UV (UVH, UVL) and OV are useful with signals reference to RTN, as are PGIO3 and PGIO4 when configured as power good input and external fault, respectively.

On/off control is possible with or without  $I^2C$  intervention. Further, the LTC4283 may reside on either the removable board or on the backplane. Even when operating autonomously, the  $I^2C$  port can still exercise control over the GATE output. UV, OV and other fault conditions seize control as needed to turn off the GATE output, regardless of the state of EN# or the  $I^2C$  port. Figure 12 shows three configurations of on/off control of the LTC4283.

*Ejector Switch or Backplane Connection Sense with Insertion Debounce Delay.* A high state of EN# turns the GATE output off. A low state of EN# turns the GATE output on with a debounce delay of 128ms. Figure 12a shows an ejector switch or backplane connection driving EN# as an on/off control with extra insertion debounce delay through the RC constant. This circuit works in both backplane and board resident applications.

*Short Pin to RTN.* Figure 12b uses the UV divider string to detect board insertion. This method achieves an insertion debounce delay of 128ms and works equally well in both backplane and board resident applications.

*I<sup>2</sup>C Only Control.* The circuit in Figure 12c locks out EN# and controls the GATE output with the ON bit in CONTROL\_1 register 0x0A. To default on or off at powerup, program the corresponding EEPROM bit (bit[7] in EE\_CONTROL\_1 register 0xAA) to 1 or 0, respectively. Any of the PGI01–PGI04 or ADI01–ADI04 pins, when configured as general purpose input, can be used to monitor a connection sense or other control signal. When the ON bit in CONTROL\_1 register 0x0A changes from 0 to 1, the LTC4283 turns on the GATE output without a delay.

The I<sup>2</sup>C port can also be used to write a fault bit in FAULT register 0x04 to turn off the GATE output if the corresponding fault has been configured to latch off the GATE



a) Contact Debounce Delay upon Insertion for Use with an Ejector Switch or Backplane Connection Sense







Figure 12. On/Off Control of the LTC4283

output using CONTROL\_2 register 0x0B. To turn the GATE output back on afterwards, clear the fault bit. The GATE output will be turned on after an auto-retry delay (except for OV). If a fault has been configured to auto-retry (in either finite or infinite times), setting the corresponding fault bit through  $I^2C$  will not turn off the GATE output.

### **Configuring PGIO and ADIO Pins**

The LTC4283 has four PGIO pins and four ADIO pins, all of which can be configured as general purpose inputs/ outputs using PGIO\_CONFIG\_1 register 0x10 and ADIO\_ CONFIG register 0x12. Additionally, PGIO1 and PGIO2 can be configured as two sequential inverted or non-inverted power good signals, PGIO3 can be configured as inverted or non-inverted power good input signal (see Power Good Monitors and PGI Fault), and PGIO4 can be configured as

inverted or non-inverted external fault (see External Fault and Auto-Retry). When configured as general purpose outputs, the output data for PGI01–PGI04 and ADI01– ADI04 are stored in bits[7:4] in PGI0\_CONFIG\_2 register 0x11 and bits[3:0] in ADC\_CONFIG register 0x12, respectively. When selected, ADI01–ADI04 are also monitored by the on-board ADC (see Data Converters).

If the PGI02\_ACLB bit in CONTROL\_1 register 0x0A is set, PGI02 is configured as an inverted indicator of active current limit after startup. During startup PGI02 is held low. After the internal power good signal is latched, if the OC\_STATUS bit in FAULT\_STATUS register 0x03 is 0, PGI02 goes high impedance. If the OC\_STATUS bit is set to indicate that active current limit is engaged, PGI02 is pulled low.

Regardless of the configurations, PGIO1–PGIO4 and ADIO1–ADIO4 all have comparators monitoring the voltage on these pins with a threshold of 1.28V. The results are stored in INPUT\_STATUS register 0x02.

### **Design Examples**

# Example 1: Design Procedure for Systems with Large Input Steps

Consider a battery operated system with maximum load power of 600W, a supply voltage range of -36V to -72V (-36V to -72V input step is allowed), and a load capacitance of C<sub>L</sub> =  $500\mu$ F as shown in Figure 2.

The maximum load current is calculated as

$$I_{L(MAX)} = \frac{P_{L(MAX)}}{V_{S(MIN)}} = \frac{600W}{36V} = 16.7A$$

Step 1. Configure current limit and select current sense resistor. Since a -36V to -72V input step is a valid operating condition, the current limit should be twice the maximum load current to minimize the temperature rise in the MOSFET following a large input step:

 $I_{\text{LIM}} = 2 \bullet I_{\text{L(MAX)}} = 33.3 \text{A}$ 

With a constant power load, when the load voltage ramps from 36V to 72V following the input step, the load current is halved. The LPFB (load power foldback) bit in CONFIG\_1 register 0x0D is set to 1 so that the current limit will be maintained at approximately twice the load current during the output ramp.

Sense resistor is selected assuming they will carry the maximum current, or 33.3A in this example. Selection is a matter of total cost, sense voltage (configurable from 15mV to 30mV in 1mV steps), allowable dissipation, availability of discrete resistance values, using multiple devices to reduce the sensing errors associated with high current density at the interface between the PCB and resistor, and using multiple devices to ballast current flow across a wide path, between 2 or more connectors, or between 2 or more MOSFET. These factors are iterated until an acceptable solution is found. First, determine the number of resistors needed to handle the total sense power. Compute the total sense power starting with the minimum sense voltage or 15mV:

$$P_S = V_{ILIM(MIN)} \bullet I_{LIM} = 15mV \bullet 33.3A = 500mW$$

Second, compute the number of resistors needed to handle this power. For example, 1206 resistors are rated for 250mW dissipation. A conservative design is half as much, or 125mW.

$$N_{\rm RS} = \frac{P_{\rm S}}{125 {\rm mW}} = \frac{500 {\rm mW}}{125 {\rm mW}} = 4$$

Thus at least four parallel 1206 resistors are needed for each channel. Third, compute the resistance value:

$$R_{S} = \frac{V_{ILIM}}{I_{LIM}} = \frac{15mV}{33.3A} = 450\mu\Omega$$

Four resistors of  $1.8m\Omega$  each would give the correct sense resistance. Fourth, use the closest next-larger available sense resistor value and adjust the sense voltage as needed to restore the current. In this case, a  $2m\Omega$  sense resistor value is selected and the sense voltage is adjusted to 16mV. Recompute the numbers:

$$R_{S} = \frac{2m\Omega}{4} = 500\mu\Omega$$
$$I_{LIM} = \frac{16mV}{500\mu\Omega} = 32A$$

 $P_S = 16mV \bullet 32A = 512mW$ 

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The power dissipation of each resistor package is now 512 mW/4 = 128 mW. The current limit is now 32A, close enough to the optimum value of 33.3A. The above process might be iterated for several combinations of different resistor counts, different package sizes, and even combinations of mixed resistor values.

When a specific design is actually built, there can be small inaccuracies in the current sensing owing to contact and copper trace resistances. An immediate remedy without changing sense resistors is to readjust the sense voltage in 1mV steps. For instance, moving sense voltage from 16mV to 17mV gives a 6.25% increase in current.

Step 2. Select resistive dividers for DRNS (drain sense), RTNS (RTN sense) and VOUTTH (output low threshold). DRNS and RTNS serve multiple purposes. First, they are the inputs to a differential amplifier that measures the attenuated load voltage for dV/dt control at startup (see Inrush Control). In the event of an output overload or short-circuit, the current limit foldback profile in normal operation depends upon the differential input between RTNS and DRNS that represents the output voltage across the load. The current limit starts to fold back when BTNS -DRNS drops below 0.9V and reaches the minimum when RTNS – DRNS drops to zero (see Current Limit Foldback). Additionally, in current limit the DRNS input monitors the MOSFET's  $V_{DS}$  and uses this information to scale the TMR pull-up current accordingly. When not in current limit, DRNS monitors  $V_{DS}$  and serves as one input to a multiplier which generates the TMR pull-up current. Finally, RTNS and DRNS also serve as inputs to the ADCs so that the input voltage and MOSFET drain voltage can be read remotely. RTNS and DRNS have a maximum useable input voltage of 2.8V, so resistive dividers are required.

To select resistive dividers for RTNS and DRNS, compute the divider ratio r using the maximum supply voltage:

$$r = \frac{V_{S(MAX)}}{1.8V} = \frac{72V}{1.8V} = 40$$

where 1.8V is the operating point of DRNS at which the TMR pull-up current is tested and specified. The resulting ADC measurement full scale for input (at RTNS) and MOSFET drain (at DRNS) voltages is

$$V_{FS(MEAS)} = r \bullet 2.048V = 40 \bullet 2.048V = 81.92V$$

which gives a LSB size of 20mV in 12-bit mode. If it was desired to measure gross overvoltage inputs, such as 100V, then a decision would have to be made to sacrifice control dynamic range in favor of ADC measurement range by using a higher divider ratio. An alternative approach is to use ADIN1–ADIN4 inputs for ADC measurements, leaving RTNS and DRNS for control purpose only.

With 72V load voltage corresponding to RTNS – DRNS = 1.8V, in normal operation the current limit starts to fold back when load voltage drops below 36V (or RTNS – DRNS < 0.9V) in overload conditions. This means there is no foldback in normal operating input range between –36V and –72V, allowing the MOSFET to pass the full load current.

Standard values of 200k and 5.11k give a divider ratio of 40.1. DRNS and RTNS must use identical dividers. While the exact ratio is not important, matching between them is very important. For this reason, 1% resistor tolerance is the minimum requirement; 0.25% or 0.1% is better.

VOUTTH pin sets the threshold of RTNS – DRNS that indicates the low limit of the output voltage to reset power good signals if the PWRGD\_RESET\_CNTRL bit in CONTROL\_1 register 0x0A is set to 1. The low limit is set below the minimum input voltage, so 32V is selected in this example. With a divider ratio of 40 on DRNS and RTNS, the VOUTTH threshold is 32V/40 = 0.8V. This voltage may be realized with a resistive divider between INTV<sub>CC</sub> (5V) and V<sub>EE</sub>, or for a better tolerance, between VREF (1.024V) and V<sub>EE</sub>. For the latter case, a divider of 5.62k and 20k as shown in Figure 2a results in 0.8V at VOUTTH. The source current of VREF is  $40\mu$ A, well within its specified limit of  $200\mu$ A.

*Step 3.* Design the overcurrent timer behavior. The TMR pin can be configured into a SOA timer or a single capacitor timer. The SOA timer requires an RC network representing the MOSFET thermal model to be connected to TMR (see SOA Timer). At least two resistors and two capacitors are needed for minimum accuracy of the thermal behavior. More RC elements are desired for better accuracy. Thus the cost and board area are larger than the single-capacitor timer. The benefit of the SOA timer is that the TMR voltage represents the temperature rise of

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the MOSFET and its trip threshold represents the maximum allowable peak temperature of the MOSFET. With the SOA timer, selection of a MOSFET is much simpler: it just needs to meet the worst-case operation requirements. In fault conditions such as output short, the SOA timer automatically protects the MOSFET by turning it off once the maximum allowable peak temperature is reached (TMR tripped). With the single capacitor timer, the minimum capacitor must first be selected to keep the MOSFET on during worst-case operating conditions, then the MOSFET must be selected to withstand the worst-case SOA conditions during normal operating and fault conditions. The cost of a MOSFET selected based on the single capacitor timer may be substantially higher than that using the SOA timer. It is recommended to use the SOA timer for applications with large input steps. In this example the TMR pin is configured as an SOA timer by setting the THERM\_TMR bit in CONTROL\_1 register 0x0A to 1, which disables the internal TMR pull-down current.

With the SOA timer protecting the MOSFET, current limit foldback may be disabled after startup. This can be done by setting the FB\_DIS bit in CONTROL\_1 register 0x0A to 1. The foldback during startup is not affected by the FB\_DIS bit.

Step 4. Select the MOSFET. With the SOA timer, two operating requirements must be met: (1) the  $R_{DS(ON)}$  must be low enough to carry maximum load current; (2) the SOA must be sufficient to stand the worst-case operating condition. The selection for the  $R_{DS(ON)}$  requirement is a combination of total MOSFET cost and maximum desired dissipation per package. For the maximum current of 32A, two 5m $\Omega$  devices result in 1.28W per device. With air flow 1.28W dissipation is acceptable and a third device is unnecessary. The chosen MOSFETs are two PSMN4R8-100BSE devices (each  $R_{DS(ON)} < 4.8m\Omega$ ). The components selected so far are shown in Figure 1 and Figure 2.

The worst-case MOSFET drain voltage with maximum allowable load is

$$V_{D(ON),MAX} = \frac{I_{LIM} \cdot R_{DS(ON),MAX}}{2} = \frac{32A \cdot 4.8m\Omega}{2} = 76.8mV$$

The DRAIN threshold V<sub>D,FET(TH)</sub> must be set higher than this number with sufficient margin to account for component inaccuracies and temperature coefficient. When the MOSFET drain voltage is higher than this threshold, two things will happen. First, the FET\_BAD\_STATUS bit in FAULT\_STATUS register 0x03 will be set and the FET bad timer will be started. When the timer expires the FET BAD FAULT bit in FAULT register 0x04 will be set and the MOSFET will be turned off if the FET\_BAD\_TURN\_OFF bit in CONTROL 1 register 0x0A has been set. Second, the TMR pull-up current will be enabled even if current limit is not engaged. This current is produced by an internal multiplier monitoring the power dissipation in the channel. V<sub>D.FET(TH)</sub> has four discrete settings: 72mV, 102mV, 143mV and 203mV. In this example 143mV is selected by setting the VDTH bits in CONFIG 2 register 0x0E to 10b.

A large input step is usually the worst-case operating condition for SOA. To verify the temperature rise of the MOSFET, it is necessary to run simulations in this condition. With the above selected components and configurations, the temperature rise of the MOSFET when riding through a -36V to -72V input step with full load (600W and 500µF) is 46°C (simulated with the LTspice SOAtherm model). At worst-case operating temperature of 85°C, this translates to 131°C in the MOSFET, which has substantial margin from the manufacturer specified maximum temperature of 175°C.

*Step 5.* Design the startup current and FET bad timer. First the startup mode is selected. As pointed out in Inrush Control, the startup current (or inrush current) can be controlled either by a RAMP capacitor in dV/dt mode or by startup foldback in current limit mode. The current limit mode is selected in this example, which is a better choice to work with the SOA timer that has been selected in Step 3. This is because if the dV/dt mode was selected, the TMR pull-up current would be disabled in normal startup conditions and the SOA timer would not be able to track the temperature rise of the MOSFET during startup.

Choice of the charging current is a trade-off between maximum charging time, maximum inrush current drawn from the backplane, and more importantly, peak power dissipated in the MOSFET. When charging a capacitor from a voltage source, the charging process dissipates
an energy in the pass MOSFET equal to the energy stored in the capacitor. The maximum input voltage results in the maximum energy:

$$E_{MAX} = C_L \bullet V_{S(MAX)}^2 = 500 \mu F \bullet (72V)^2 = 2.59 J$$

This indirectly sets a limit on how quickly the load capacitor can be charged, since the average power dissipation in the MOSFET is energy/time. In general, the faster the charge rate, the higher the peak temperature. For this reason, it is a good idea to lower the inrush current to no more than necessary to achieve the required startup time. Therefore, the smallest foldback ratio, 10%, is selected by setting the FB bits in CONFIG\_1 register 0x0D to 11b, and the startup inrush current is

 $I_{\text{INRUSH}} = I_{\text{LIM}} \bullet \alpha_{\text{FB}} = 32\text{A} \bullet 10\% = 3.2\text{A}$ 

The maximum startup charging time of the load capacitor is then computed:

$$t_{\text{STARTUP(MAX)}} = \frac{C_{\text{L}} \bullet V_{\text{S(MAX)}}}{I_{\text{INRUSH}}} = \frac{500 \mu F \bullet 72 V}{3.2 \text{A}} = 11.25 \text{ms}$$

This charging time is short enough for most applications. Simulation shows the temperature rise of the MOSFET in this worst-case startup condition is  $40^{\circ}$ C, lower than that for the -36V to -72V input step calculated in Step 4.

During startup the FET\_BAD\_STATUS bit is high and the FET bad timer is running and serves as a watchdog over the controlled startup. The load capacitor must be fully charged before this timer expires, or the GATE outputs will be turned off if the FET\_BAD\_TURN\_OFF bit in CONTROL\_1 register 0x0A has been set. There is no concern with this example since the maximum charging time of 11.25ms is much shorter than the minimum FET bad timer delay (256ms).

*Step 6.* Select the RC network for the SOA timer following the procedure as shown in the SOA Timer section. It was found that two thermal capacitors and two thermal resistors provide fairly good curve fitting for the thermal impedance plot of the chosen MOSFET, PSMN4R8-100BSE in the range between 100µs and 100ms (wide

enough for typical operating conditions of this application):  $C_{\theta 1} = 0.002 \text{ J/°C}$ ,  $R_{\theta 1} = 0.05 ^{\circ}\text{C/W}$ ,  $C_{\theta 2} = 0.03 \text{ J/°C}$ ,  $R_{\theta 2} = 0.35 ^{\circ}\text{C/W}$ . The conversion constant is given by

$$k = \frac{V_{DS,MAX} \bullet I_{D,MAX}}{I_{TMR(UP),MAX}} \bullet \frac{V_{TMR(TH)}}{\Delta T_{MAX}} = \frac{72V \bullet 32A}{202\mu A} \bullet \frac{2.048V}{65^{\circ}C} = 3.6 \bullet 10^{5} \left[\frac{V^{2}}{^{\circ}C}\right]$$

where  $\Delta T_{MAX}$  is the maximum allowable temperature rise and chosen to be 65°C, which corresponds to a maximum MOSFET temperature of 150°C at an operating temperature of 85°C, with 25°C margin from the manufacturer specified maximum temperature of 175°C. The thermal R and C values are then converted to electric R and C values as shown in SOA Timer. After the electrical R and C values are computed, choose the closest next-larger available resistor value and the closest next-smaller available capacitor value. Then the resistance corresponding to the thermal resistance of the board is added to the termination resistance (the largest one). If the computed resistance for the board thermal resistance is over  $1M\Omega$ , choose  $1M\Omega$ . Assuming a 5°C/W board thermal resistance in this application, it is converted to  $5 \cdot 3.6 \cdot 10^5 = 1.8 M\Omega$ . So  $1M\Omega$  is selected. This avoids accuracy degradation due to board leakage currents. The resulting electrical capacitors and resistors are  $C_{E1} = 4.7$ nF,  $R_{E1} = 18.2$ k,  $C_{E2} = 68$ nF,  $R_{F2} = 1.13M$ , as shown in Figure 1 and Figure 2a.

After the SOA timer is configured, rerun simulations to ensure TMR does not reach its 2.048V trip point in all operating conditions including startup and input step. When it trips in fault conditions such as output overload or short-circuit, verify the peak temperature of the MOSFET matches the proposed maximum temperature. Iterations of the above procedure may be needed before the RC network is finalized.

Step 7. Select resistive dividers for UV/OV inputs.

Select resistive dividers so that UV rising threshold is set just below the minimum input voltage and OV falling threshold is set just above the maximum input voltage. A single, 4-resistor divider as shown in Figure 2a gives UV shutdown at 32.4V, UV release at 35.3V, OV shutdown

at 74.5V and OV release at 73.2V. This configured range is just wide enough to cover the full input voltage range between 36V to 72V. A 100nF bypass capacitor is selected to filter out noises at UVL/UVH and OV.

The current ADC has a full scale of 32.768mV. A  $0.5m\Omega$  of sense resistor, gives a full-scale current of 65.5A, with a 16mA LSB size in 12-bit mode.

### Example 2: Design Procedure for Systems with Regulated Inputs

The second example is a line operated –48V system with supply tolerance of 10% (–43.2V to –52.8V) and maximum load power of 800W as shown in Figure 13. The load capacitance is specified as  $C_L$  = 1000 $\mu F.$ 

The maximum load current is calculated as

$$I_{L(MAX)} = \frac{P_{L(MAX)}}{V_{S(MIN)}} = \frac{800W}{43.2V} = 18.5A$$

*Step 1.* Configure current limit and select current sense resistors. Since the input voltage is well regulated, there is no need to set the current limit to twice the load current

to minimize temperature rise upon a large input step as in Example 1. The current limit in this example just needs to cover the maximum load current, with enough margin to account for device tolerances. Set current limit to 20A, which provides sufficient margin for the maximum load current of 18.5A:

 $I_{LIM} = 20A$ 

Compute the sense power starting with the minimum sense voltage or 15mV:

$$P_S = V_{ILIM(MIN)} \bullet I_{LIM} = 15mV \bullet 20A = 300mW$$

With 250mW rated 1206 resistors, use 125mW for conservative design and the minimum number of sense resistors to handle the power is

$$N_{\rm RS} = \frac{P_{\rm S}}{125 {\rm mW}} = \frac{300 {\rm mW}}{125 {\rm mW}} = 2.4$$

Thus at least 3 parallel 1206 resistors are needed. The SENSE resistance is

$$R_{S} = \frac{V_{ILIM(MIN)}}{I_{LIM}} = \frac{15mV}{20A} = 0.75m\Omega$$



Figure 13. -48V/800W Hot Swap Controller with dV/dt Inrush Control

Three resistors of  $2.25m\Omega$  each would give the correct sense resistance. The closest next-larger available sense resistor value is  $3m\Omega$ :

$$R_{S} = \frac{3m\Omega}{3} = 1m\Omega$$

Adjust the sense voltage to 20mV to restore the current by setting the ILIM bits in CONFIG\_1 register 0X0D to 0101b:

$$I_{LIM} = \frac{V_{ILIM}}{R_S} = \frac{20mV}{1m\Omega} = 20A$$

Recompute the sense power:

 $P_S = 20mV \bullet 20A = 400mW$ 

The power dissipation of each resistor package is now 400mW/3 = 133mW, still an acceptable value for 1206 resistors. Sense voltage may need to be readjusted to account for current sensing inaccuracies such as contact and copper trace resistances, as explained in Example 1, Step 1.

*Step 2.* Select resistive dividers for DRNS (drain sense), RTNS (RTN sense) and VOUTTH (output low reference). See Example 1, Step 2 for detailed design considerations. First compute the divider ratio r for RTNS and DRNS:

$$r = \frac{V_{S(MAX)}}{1.8V} = \frac{52.8V}{1.8V} = 29.3$$

Standard values of  $280k\Omega$  and  $10k\Omega$  give a divider ratio of 29. The ADC measurement full-scale for input (at RTNS) and MOSFET drain (at DRNS) voltages is

 $V_{FS(MEAS)} = r \cdot 2.048V = 29 \cdot 2.048V = 59.4V$ 

which gives a LSB size of 14.5mV in 12-bit mode.

With  $V_{LOAD} = 29 \cdot 1.8V = 52.2V$  corresponding to RTNS – DRNS = 1.8V, the current limit starts to fold back when  $V_{LOAD}$  drops below 26.1V in overload conditions. There is no foldback at normal input between –43.2V and –52.8V, allowing the MOSFETs to pass the full load current.

If 40V is chosen as the output voltage threshold to reset power good signals, with a divider ratio of 29 on DRNS and RTNS, the VOUTTH threshold is 40V/29 = 1.379V. This

voltage can be obtained with a resistive divider between INTV<sub>CC</sub> (5V) and V<sub>EE</sub>. The divider ratio is 5V/1.379V = 3.63. A divider of 26.7k and 10.2k as shown Figure 13 gives a close enough ratio of 3.62.

*Step 3.* Design the TMR behavior. See Example 1, Step 3 for general design considerations. Since there is no concern about a large input step after startup, a very short timer delay is needed for MOSFET turn-off upon a fault such as output short-circuit. Therefore, the TMR function is essentially a filtered circuit breaker and a single timer capacitor on TMR works just fine for this purpose.

It has been found that  $20\mu s$  of circuit breaker filtering is sufficient to reject noise encountered in most systems. The TMR pull-up current is  $202\mu A$  at maximum overload, with a voltage threshold of 2.048V. Compute the timer capacitance, C<sub>t</sub>, for  $20\mu s$  filter delay:

$$C_{t} = \frac{I_{TMR(UP),MAX} \bullet t_{FILTER}}{V_{TMR(TH)}} = \frac{202\mu A \bullet 20\mu s}{2.048V} = 2nF$$

Select the closest next-larger available capacitance:  $C_t = 2.2nF$ . With single capacitor on TMR, the THERM\_ TMR bit in CONTROL\_1 register 0x0A must be cleared to enable the internal 2µA pull down current. Additionally, the FB\_DIS bit in CONTROL\_1 register 0x0A should be cleared to keep foldback enabled after startup to protect MOSFET from damage upon a low impedance short-circuit.

*Step 4.* Design the startup current and FET bad timer. Since in Step 3 the TMR function is designed as a short circuit-breaker delay, it is desired to use the dV/dt startup mode so that a small trickle current charges the load capacitance without triggering current limit. (see discussions in Example 1, Step 5). The design procedure involves selecting a RAMP capacitor to set the dV/dt rate for desired charging current, selecting a proper startup current limit and checking the temperature rise of the MOSFET under a resistive short condition.

Choice of the charging current is a trade-off between maximum charging time and peak temperature of the MOSFET. As discussed in Example 1, Step 5, the charging current should be set to a low level that is just necessary to achieve the required charging time. Suppose an upper limit of 300ms charging time is desired for a  $1000\mu$ F load

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capacitor at the maximum input of 52.8V. The necessary charging current is

 $I_{\text{INRUSH(MIN)}} = \frac{C_{\text{L}} \bullet V_{\text{S(MAX)}}}{t_{\text{STARTUP(MAX)}}} = \frac{1000 \mu \text{F} \bullet 52.8 \text{V}}{300 \text{ms}} = 176 \text{mA}$ 

The RAMP capacitor is selected according to

$$C_{R} = I_{RAMP} \bullet r \bullet \frac{C_{L}}{I_{INRUSH}} = 2.5\mu A \bullet 29 \bullet \frac{1000\mu F}{176mA} = 412nF$$

An acceptable value is 330nF, resulting in a nominal inrush of

$$I_{\text{INRUSH}} = I_{\text{RAMP}} \bullet r \bullet \frac{C_{\text{L}}}{C_{\text{R}}} = 2.5 \mu \text{A} \bullet 29 \bullet \frac{1000 \mu \text{F}}{330 \text{nF}} = 220 \text{mA}$$

and a maximum startup time of

$$t_{\text{STARTUP(MAX)}} = \frac{C_{\text{L}} \bullet V_{\text{S(MAX)}}}{I_{\text{INRUSH}}} = \frac{1000 \mu \text{F} \bullet 52.8 \text{V}}{220 \text{mA}} = 240 \text{ms}$$

which is below the upper limit of 300ms.

The FET bad timer must be set longer than the startup time for the load capacitor to be fully charged, so it is configured to 512ms by setting the FTBD\_DL bits in CONFIG\_2 register 0x0E to 01b to account for all tolerances.

The startup current limit should also be configured to a low level to minimize the temperature rise of the MOSFET under a resistive short condition, but must be higher than the dV/dt inrush current to avoid current limit being triggered in normal startup conditions. With a foldback ratio of 10%, the startup current limit is

 $I_{LIM(STARTUP)} = 20A \bullet 10\% = 2A$ 

which is well above the inrush current of 220mA. Select the 10% foldback ratio by setting the FB bits in CONFIG\_1 register 0x0D to 11b.

Since the inrush current is very low, SOA requirement in normal startup is not critical. However, the MOSFET must be able to withstand the resistive short condition during startup as discussed below. Step 5. Select a sufficient MOSFET to carry the maximum load current and withstand the startup stress. The decision is a combination of MOSFET cost, maximum desired dissipation, and startup stress. For the maximum current of 20A, two PSMN4R8-100BSE ( $R_{DS(ON)} < 4.8m\Omega$ ) devices result in 0.48W per package, an easily manageable dissipation.

With full load the worst-case drain voltage of the MOSFET is  $20A \cdot 2.4m\Omega = 48mV$ . Select 102mV as the DRAIN threshold for starting FET bad timer and enabling TMR pull-up current, with sufficient margin to account for inaccuracies. Set the VDTH bits in CONFIG\_2 register 0x0E to 01b for this configuration. See detailed design considerations in Example 1, Step 4.

*Step 6.* Run simulations to verify temperature rises of the MOSFET under all operating and fault conditions are within the acceptable range. This is a necessary step when using a single capacitor circuit breaker timer as selected in Step 3.

First, check temperature rise in the MOSFET during startup. The conditions include normal dV/dt startup to fully charge the 1000µF load capacitor and a fault condition in which the MOSFET charges both the load capacitor and a parallel fault resistor, both at the maximum input voltage. If temperature rise is too high in normal startup condition, the inrush current may be reduced by selecting a larger RAMP capacitor. If the inrush current must be reduced less than the value required to achieve the desired maximum charging time, a larger MOSFET has to be selected. For the fault condition, the worst-case is found iteratively by changing the fault resistor value while monitoring the temperature rise. As a starting point, use a resistor of  $V_{S(MAX)}/(4 \bullet I_{LIM(STARTUP)})$  or 52.8/(4 • 2) =  $6.6\Omega$  for this example. If the temperature rise is too high, startup current limit may be reduced by selecting a steeper foldback ratio. If the startup current limit must be reduced to less than or close to the dV/dt inrush required for the maximum charging time or the foldback ratio must be reduced below 10%, a larger MOSFET must be selected. Using the conditions of this example, it is found the worst-case temperature rise in the MOSFET either in

normal startup condition or with different fault resistors is lower than 64°C, an acceptable figure. This verifies the selected MOSFET, PSMN4R8-100BSE, has enough SOA to handle the worst-case dissipation during startup.

Second, check temperature rises in the MOSFET after startup when TMR times out under different overload conditions. The worst-case could be shorting the output to half of the available output voltage so there is no foldback while the  $V_{DS}$  of the MOSFET is still high. If the worst-case temperature rise is too high, a larger MOSFET must be selected. In this example, the worst-case temperature rise is an insignificant value of about 16°C thanks to the short circuit-breaker delay of 20µs.

### Step 7. Select resistive dividers for UV/OV inputs

Although it is possible to use a single, four-resistor (or three-resistor if UVH and UVL connected together) divider as shown in Example 1, Step 7, two independent dividers with 2 (OV) or 2 to 3 (UV) resistors in each divider make it easier to make non-interactive changes at a later time. The two dividers as shown in Figure 13 gives UV shutdown at 38.6V, UV release at 40.2V, OV shutdown at 55.3V and OV release at 54.3V, which covers the full input voltage range of this example. 10nF capacitors filter out noises on UVL and OV.

With an ADC full scale of 32.768mV, the  $1m\Omega$  sense resistance gives a full-scale current of 32.768A and a LSB size of 8mA in 12-bit mode.

### **Layout Considerations**

To achieve accurate current sensing, Kelvin connections are required. The minimum trace width for 1oz copper foil is 0.02" per amp to make sure the trace stays at a reasonable temperature. Using 0.03" per amp or wider is recommended. Note that 1oz copper exhibits a sheet resistance of about  $530\mu\Omega/square$ . Use 2oz or heavier copper for high current applications.

The  $V_{EE}$  pin of the LTC4283 should be connected to a separate plane from the main -48V input plane. To improve

noise immunity, as shown in Figure 14, the V<sub>EE</sub> connections of all capacitors, resistive dividers, opto-isolators and I<sup>2</sup>C common must be made directly to the local V<sub>EE</sub> plane, not the –48V input plane.

The mechanical stress of soldering a part to a board and the heat of an IR reflow or convection soldering oven can cause the ADC full-scale error (FSE) and the current limit voltage ( $V_{ILIM}$ ) to shift. Refer to Typical Performance Characteristics for ADC FSE and  $V_{ILIM}$  shifts of 300 units of LTC4283 after three cycles of the lead-free IR reflow process.



Figure 14. Layout Example of V<sub>EE</sub> Plane, -48V Input Plane and Sense Resistor Connection

### Reboot on I<sup>2</sup>C Command

The LTC4283 features a reboot command bit, RBT\_EN in REBOOT register 0xA2. Setting this bit will cause the LTC4283 to shut down and reboot after a delay. The reboot delay is programmable from 512ms to 65.5s using the three RBT\_DL bits in the REBOOT register. A reboot delay allows load capacitance to fully discharge. During the reboot delay the DELAY\_STATUS bit in the REBOOT register is set to 1. It will be cleared when the delay expires. The reboot will also copy the contents of the EEPROM to volatile registers in the same way as after initial power-up. On systems where the hot swap controller supplies power

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to the I<sup>2</sup>C master, this allows the master to issue a command that power cycles the entire board, including itself. Once set, the RBT\_EN bit remains 1 after reboot is completed. Clear it before issuing the next reboot command.

### **Data Converters**

The LTC4283 incorporates a pair of Sigma-Delta A/D converters (ADCs) that are configurable from 8-bit at 1kHz conversion rate to 16-bit at 1Hz conversion rate in five settings using the ADC bits in PGIO CONFIG 2 register 0x11 (see Table 12). In the default continuous mode, the first ADC (ADC1) continuously monitors the input current through a sense resistor between SENSE<sup>+</sup> and SENSE<sup>-</sup>. The second ADC (ADC2) is synchronized to ADC1 and monitors VPWR for power multiplication plus one of the 14 auxiliary inputs. VPWR is selectable between the attenuated input voltage at RTNS and the attenuated MOSFET drain voltage at DRNS using the VPWR SELECT bit in CONFIG\_3 register 0x0F. The auxiliary inputs include 10 single-ended signals and 4 differential signals and are selectable using ADC SELECT registers 0x13-0x14 (see Table 14). If multiple auxiliary inputs are selected, ADC2 will rotate between them in the continuous mode as illustrated in Figure 15. The AUX ADC CH bits in ADC\_STATUS register 0x01 are refreshed at the end of each conversion to indicate the auxiliary input that completed the latest measurement (see Table 5). If all bits in ADC SELECT registers 0x13-0x14 are cleared while the ADCs are running in continuous mode, ADC1 and ADC2 continue to measure SENSE<sup>+</sup> – SENSE<sup>-</sup> and VPWR (RTNS/DRNS), respectively. The auxiliary measurements of ADC2 are disabled and the data in 0x41-0x79 from

the previous measurement are preserved except 0x4A (ADIN1), which is overwritten by a small number.

The full-scale voltage of any single-ended input is 2.048V. For each differential input, one terminal must be at the same potential of  $V_{EE}$ . Normally the negative terminal is at  $V_{EE}$  and the full-scale is 32.768mV. If the positive terminal is at  $V_{EE}$ , the full scale becomes 33.301mV. When using ADIN1–ADIN4 and ADI01–ADI04 as differential inputs, ADIN1, ADIN3, ADI01 and ADI03 must be the negative terminals, and ADIN2, ADIN4, ADI02, ADI04 must be positive terminals, respectively. Note that for each resolution setting, the resolution of differential auxiliary inputs of ADC2 is one bit less than that of the SENSE<sup>+</sup> – SENSE<sup>-</sup> input of ADC1 or the single-ended inputs.

After each conversion of the two synchronized ADCs, the measured current sense voltage (SENSE<sup>+</sup> – SENSE<sup>-</sup>) is multiplied by the measured VPWR (RTNS or DRNS) voltage to calculate input power or MOSFET power, configurable using the VPWR\_SELECT bit in CONFIG\_3 register 0x0F. All measured results and calculated power are stored to corresponding data registers (see Table 3). They are also compared to the minimum and maximum values that are stored in the minimum and maximum data registers. If the measurement is a new minimum or maximum value, then the corresponding minimum or maximum data registers are updated. Note that all ADC data registers from 0x41 to 0x79 have a length of two bytes or 16 bits, and the data for all resolutions are left justified.

The ADC measurements are compared to the 8-bit minimum and maximum alarm thresholds that are configured using registers 0x1B through 0x40 and will set the



Figure 15. LTC4283 ADC Measurement Pattern in Continuous Mode

corresponding ADC alarm bits in ADC\_ALARM\_LOG registers 0x05 to 0x09. If the associated ADC alert bit in ADC\_ALERT registers 0x16 to 0x1A is set, an ADC alarm bit will generate an alert by pulling ALERT# low and set the ALERT\_GENERATED bit in METER\_CONTROL register 0x84.

At the end of each ADC measurement, calculated power is added to an accumulator that meters energy. The 6-byte energy meter 0x7A to 0x7F is capable of accumulating 12 days of power at full scale in 12-bit ADC mode, which is several months at a nominal power level. When the meter overflows the METER\_OVERFLOW bit in METER\_ CONTROL register 0x84 is set to 1 and an optional alert is generated if the METER\_OVERFLOW\_ALERT bit in CONFIG\_3 register 0x0F is preset to 1. To measure coulombs, the energy meter may be configured to accumulate current rather than power by setting the INTEGRATE\_I bit in CONFIG\_3 register 0x0F.

The tick counter 0x80 to 0x83 keeps track of how many times power has been added into the energy meter. Dividing the energy by the tick count will yield the average power over the accumulation interval. The 4-byte tick counter will keep count for 9 years in the 12-bit mode before overflowing. When it overflows the TICK\_OVERFLOW bit in METER\_CONTROL register 0x84 is set to 1 and an optional alert is generated if the TICK\_OVERFLOW\_ALERT bit in CONFIG\_3 register 0x0F is preset to 1. Multiplying the value in the counter by the ADC conversion time yields the time that the energy meter has been accumulating.

Both the energy accumulator and the tick counter are writable, allowing them to be preloaded with a given energy and/or time before overflow so that the LTC4283 will generate an overflow alert after either a specified amount of energy has been delivered or time has passed.

The following formulas are used to convert the values in the ADC data registers into physical units. Since the data are left justified, the same equations apply to all resolutions.

To calculate single-ended voltages measured by ADC2:

$$V = \frac{\text{CODE(word)} \bullet 2.048V}{2^{16}}$$

To calculate currents in amperes measured by ADC1 and differential mode ADC2:

$$I = \frac{\text{CODE(word)} \cdot 32.768\text{mV}}{2^{16} \cdot \text{R}_{\text{SENSE}}}$$

To calculate power in watts:

$$P = \frac{CODE(word) \cdot 32.768mV \cdot 2.048V}{2^{16} \cdot R_{SENSE}}$$

To calculate energy in joules:

$$\mathsf{E} = \frac{\mathsf{CODE}(48\,\mathsf{Bits}) \bullet 32.768\mathsf{mV} \bullet 2.048\mathsf{V} \bullet \mathsf{t}_{\mathsf{CONV}}}{2^{24}} \bullet \mathsf{R}_{\mathsf{SENSE}}$$

where  $t_{CONV}$  is the ADC conversion time depending upon the configured resolution (see Table 12).

To calculate coulombs:

$$Q = \frac{CODE(48 \text{ Bits}) \bullet 32.768 \text{mV} \bullet \text{t}_{CONV}}{2^{16} \bullet \text{R}_{SENSE}}$$

To calculate average power over the energy accumulation period:

$$P_{AVG} = \frac{E}{t_{CONV} \bullet CODE(COUNTER)}$$

To calculate average current:

$$I_{AVG} = \frac{Q}{t_{CONV} \bullet CODE(COUNTER)}$$

To calculate voltage alarm thresholds:

$$V_{ALARM} = \frac{CODE(byte) \cdot 2.048V}{256}$$

To calculate current Alarm threshold in amperes:

$$I_{ALARM} = \frac{CODE(byte) \cdot 32.768mV}{256 \cdot R_{SENSE}}$$

To calculate power Alarm threshold in watts:

$$P_{ALARM} = \frac{CODE(byte) \cdot 32.768mV \cdot 2.048V}{256 \cdot R_{SENSE}}$$

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To synchronize multiple bytes of data from the tick counter and energy meter, use the Read Page protocol (see Data Synchronization and Arbitration). An I<sup>2</sup>C read latches the tick counter and energy meter data in buffers while the tick counter and energy meter still increment. Alternatively one can set the METER\_HALT bit in METER\_CONTROL register 0x84 before reading the data. This will halt the ticker counter and energy meter. Clear the METER\_HALT bit afterwards to reactivate incrementing.

The LTC4283 ADCs also feature a snapshot mode that allows a one time measurement of a single data packet: SENSE<sup>+</sup> – SENSE<sup>-</sup>, VPWR (RTNS or DRNS), and an auxiliary input selected by the SNAPSHOT SEL bits in ADC SNAPSHOT register 0x85. To enable the snapshot mode, set the ADC HALT bit in the ADC SNAPSHOT register to 1 and write the SNAPSHOT SEL bits for the desired auxiliary input in one I<sup>2</sup>C command. At the falling edge of SCL after bit 0 is received, the ADCs start a single conversion of the selected data packet and the ADC IDLE bit in ADC STATUS register 0x01 is cleared to indicate the data is not ready. After completing the conversion, the ADCs are halted, the ADC IDLE bit is set to indicate the data is ready, and the AUX\_ADC\_CH bits in the ADC\_STATUS register are set to indicate the auxiliary input that is just measured. To make another snapshot measurement, write the ADC SNAPSHOT register again. To go back to the continuous mode, clear the ADC HALT bit.

The 14 auxiliary inputs with the LTC4283 ADCs allow for extensive monitoring of board level signals. Figure 16 shows an example of using ADI01–ADI04 as single-ended inputs to monitor individual input voltages of a dual-feed system. The 1.024V VREF is exactly half of the ADC reference voltage and level shifts the ADI01–ADI04 inputs within measurable range of the ADC. In Figure 16 one input is –36V (V<sub>INPUT1</sub>) and the other is –72V (V<sub>INPUT2</sub>). All node voltages are noted in the circuit. The voltage values in parenthesis are referred to system ground RTN and the others are referred to V<sub>EE</sub>. With the ADI01–ADI04 voltages measured by the ADC and R1/R2 = R3/R4 = R5/R6 = R7/R8, the input voltages are

$$V_{\text{INPUT1}} = (V_{\text{ADIO3}} - V_{\text{ADIO1}}) \frac{\text{R1} + \text{R2}}{\text{R2}}$$

$$V_{INPUT2} = (V_{ADI04} - V_{ADI02}) \frac{R1 + R2}{R2}$$

The forward voltage drop of the conducting diode D2 is

$$V_{D2} = V_{REF} \frac{R7}{R8} - V_{ADIO4} \frac{R7 + R8}{R8}$$

 $V_{\text{REF}}$  is ratiometric to the ADC full-scale voltage and can be measured by ADC with one of the ADIN1–ADIN4 pins to calibrate out errors.

The circuit in Figure 16 also monitors fuses on both the RTN and -48V sides. If any one of the four fuses is open, it can be detected by the ADC measurement of the corresponding ADIO input:  $V_{ADIO1} = V_{REF}$  indicates fuse F3 is open;  $V_{ADIO2} = V_{REF}$  indicates fuse F4 is open;  $V_{ADIO3} = V_{REF}$  indicates fuse F1 is open;  $V_{ADIO4} = V_{REF}$ indicates fuse F2 is open. Additionally, chassis ground is monitored with the ADIN1 pin as shown in Figure 16.

Figure 17 shows an example that monitors individual feed currents using two differential input pairs. Note that the ADIN2 – ADIN1 and ADIN4 – ADIN3 inputs have a full scale of 33.301mV (positive terminals are at V<sub>EE</sub>), while the SENSE<sup>+</sup> – SENSE<sup>-</sup> input has a normal full scale of 32.768mV (negative terminals are at V<sub>EE</sub>).



Figure 16. Feed Voltage and Open Fuse Monitoring



Figure 17. Individual Feed Current and Channel Current Monitoring

The output voltage across the load may be calculated from the measured RTNS and DRNS voltages. If a direct measurement of the load voltage is desired, the circuit as shown in Figure 18 may be used.

### EEPROM

The LTC4283 has an onboard EEPROM to allow nonvolatile configuration and fault logging. The EEPROM registers are denoted by EE\_ in the first column of register Table 3. The EEPROM registers may be read and written like any other register except that the EEPROM takes about 2.2ms to write data.

While the EEPROM is writing, the EEPROM\_BUSY bit in the SYSTEM\_STATUS register is set. During this time, the I<sup>2</sup>C interface will NACK attempted writes to EEPROM registers. EEPROM registers will return 0xFF if read while the EEPROM is busy. The FAULT\_LOG\_CONTROL register is tied together with EEPROM and can't be written while EEPROM is busy. See the Fault Log section for more detail. Other registers may be accessed while EEPROM write is busy. When the EEPROM finishes writing, the





EEPROM\_BUSY bit will be cleared and the EEPROM\_ WRITTEN bit in the ADC\_ALARM\_LOG\_1 register will be set.

If the corresponding EEPROM\_WRITTEN\_ALERT bit in register ADC\_ALERT\_1 is set, a rising edge on EEPROM\_ WRITTEN will set ALERT\_GENERATED in the METER\_ CONTROL register. As a result, the ALERT# pin is pulled down. This will alert the host that the LTC4283 EEPROM is ready for more accesses.

When the LTC4283 comes out of UVLO or receives a REBOOT command, the contents of the EEPROM are copied to the corresponding operating registers. This process takes about 1.3ms. During this time, the I<sup>2</sup>C bus is not available. Any command code received will be NACKed. Registers in the address range 0x0A through 0x40 correspond to EEPROM locations 0xAA through 0xE0. Register 0x90 corresponds to EEPROM location 0xF0. The seven EEPROM bytes in the EE\_SCRATCH area are available for any general purpose use. EEPROM is also used to support the fault logging feature. See details in the Fault Log section.

The WP pin prevents I<sup>2</sup>C writes to the EEPROM when high. Attempts to write to the EEPROM while WP is high will result in a NACK and no action. Fault log writes can take place with WP high, except when the LTC4283 is in single-wire broadcast mode. The EEPROM can be read regardless of the WP pin setting. The current WP pin status is available for reading at the WP\_STATUS bit in the REBOOT register.

Factory programmed parts may optionally have the EEPROM locked. In this case the WP pin has no impact. No EEPROM writes are possible. Fault logging is also



disabled when the EEPROM is locked. Bit EE\_LOCK in the METER\_CONTROL register is a 1 when the EEPROM is locked.

### Fault Log

The LTC4283's EEPROM supports a fault logging feature. Twelve bytes hold a log for a single fault event (Table 22). In addition, a thirteenth byte provides an EEPROM backup copy for the fault log control register (FAULT\_LOG\_ CONTROL, register 0x90, see Table 21).

Writes to FAULT\_LOG\_CONTROL always cause a write to the EEPROM backup byte (EE\_FAULT\_LOG\_CONTROL). This causes the EEPROM to go busy, disabling access to all EEPROM registers for about 2.2ms. During this time, FAULT\_LOG\_CONTROL can be read but not written. If another EEPROM register is written first, FAULT\_LOG\_ CONTROL can't be written until the busy condition clears.

*Conditions Leading to a Fault Log Write.* A fault condition is defined as any condition in which a bit in the FAULT register (0x04) is set or the EN#\_CHANGED bit is set in the ADC\_ALARM\_LOG\_1 register (0x05).

A fault condition will result in a fault log being written if several conditions are met:

- 1. The fault condition causes GATE to be pulled low.
- 2. V<sub>IN</sub> is above the UVLO limit.
- 3. FAULT\_LOG\_ENABLE in the FAULT\_LOG\_CONTROL register (0x90) is set.
- 4. FAULT\_LOG\_UNLOCK, FAULT\_LOG\_START and FAULT\_LOG\_DONE in the FAULT\_LOG\_CONTROL register are all clear (this ensures any previous fault log has been completely serviced).

The FET\_SHORT\_FAULT and POWER\_FAILED bits don't cause GATE to be pulled low, so they don't cause a fault log to be written. Also, the EN#\_CHANGED bit doesn't cause a fault log to be written if it is set by the falling edge of EN#.

In addition, fault log writing is disabled if the WP pin is high while the LTC4283 is in single-wire broadcast mode.

*Fault Log Writing Sequence.* This sequence takes place in the LTC4283 in response to a condition that calls for a fault log write:

- 1. Freeze a shadow copy of fault bits (register 0x04 and bit [7] of 0x05).
- 2. Block I<sup>2</sup>C access.
- 3. Set FAULT\_LOG\_START in the FAULT\_LOG\_ CONTROL register.
- 4. Write FAULT\_LOG\_CONTROL to its backup copy in EEPROM.
- 5. Write the 12 bytes of fault information as detailed in Table 22, fault bits come from the shadow copy.
- 6. Set FAULT\_LOG\_DONE in FAULT\_LOG\_CONTROL.
- 7. Write FAULT\_LOG\_CONTROL to its backup copy in EEPROM.
- 8. Set alert if FAULT\_LOG\_ALERT is set.
- 9. Unfreeze the shadow copy of fault bits.
- 10. Allow I<sup>2</sup>C access

The I<sup>2</sup>C bus is blocked for about 31ms (14 time  $t_{WRITE}$ ). During this time, any incoming byte from I<sup>2</sup>C will be NACKed. If a fault log write starts in the middle of an I<sup>2</sup>C read, bytes of 0xFF will be returned to I<sup>2</sup>C in place of expected data.

*Resolving Fault Priority.* When one fault bit is set, more bits will typically be set soon afterward. With too many bits set, the original cause of the problem is harder to determine. The LTC4283's fault logging logic is designed to capture the first fault indication and disregard subsequent fault bits set until after fault log writing finishes.

The frozen copy of fault bits mentioned in the fault log writing sequence is part of this philosophy. As soon as the first fault bit is set which leads to GATE low, the frozen copy of fault bits is closed and remains closed until after logging is complete. In the fault log, fault data comes from the frozen copy. During this time, fault information is still accumulated in the main fault registers.

*Servicing a Fault Log.* After one fault log has been written, further fault log writes will be disabled until the first fault log has been serviced.

The FAULT\_LOG\_START and FAULT\_LOG\_DONE bits can't be set or cleared directly by I<sup>2</sup>C accesses. To prevent an accidental clearing of fault log information, a multibyte sequence is required to fully service one fault log so another fault log can be written. The sequence is:

- 1. Write FAULT\_LOG\_CONTROL with FAULT\_LOG\_ UNLOCK set
- 2. Write a second time with FAULT\_LOG\_UNLOCK set and all other bits clear. This write will clear FAULT\_ LOG\_START and FAULT\_LOG\_DONE.
- Write again with FAULT\_LOG\_UNLOCK, FAULT\_LOG\_ START and FAULT\_LOG\_DONE all clear. At this time, the FAULT\_LOG\_ENABLE and FAULT\_LOG\_ALERT bits may be set as desired.

Additionally, to avoid inadvertently overwriting the logged data through I<sup>2</sup>C, bring WP high during servicing.

*Incomplete Fault Logs.* A fault condition is a likely precursor to an overall loss of power in the LTC4283. For accurate fault logging, the system design must provide sufficient external capacitance as described in Input Power Supply to hold  $INTV_{CC}$  up during the time required to write 14 bytes to EEPROM.

The fault log writing sequence described earlier provides a way to detect if the fault log doesn't complete successfully. The first EEPROM write saves FAULT\_LOG\_ CONTROL with the FAULT\_LOG\_START bit set. Then the final EEPROM write saves FAULT\_LOG\_CONTROL with both FAULT\_LOG\_START and FAULT\_LOG\_DONE bits set.

After a loss of power, the FAULT\_LOG\_CONTROL register is loaded back from the saved EEPROM copy. If power was lost before a fault log completed, the FAULT\_LOG\_ CONTROL register will have FAULT\_LOG\_START set, but not FAULT\_LOG\_END. Also after a loss of power, if the FAULT\_LOG\_ALERT bit is set and FAULT\_LOG\_START, FAULT\_LOG\_DONE or FAULT\_LOG\_UNLOCK are set, the ALERT# pin will be pulled down to alert the system that an unserviced fault log remains in the chip.

### **Digital Interface**

The LTC4283 communicates with a bus master using a serial 2-wire interface, compatible with both  $I^2C$  and SMBus. The 2-wire interface is supplemented by an SMBus-compatible ALERT# output. The LTC4283 is always a bus slave and doesn't use clock stretching.

Many LTC4283 applications require unidirectional isolators such as opto-couplers between the serial interface and the host system. For convenience of opto-coupling with the host, the SDA function is split into SDAI (input) and SDAO (output). For a conventional SDA line, tie SDAI and SDAO together.

When using opto-couplers, connect the SDAI pin to the output of the incoming opto-coupler and connect the SDAO pin to the input of the outgoing opto-coupler (see Figure 2b). If the ALERT# line is used, connect it in the same way as the SDAO pin as shown in Figure 2b.

### **Bus Compatibility**

The basic LTC4283 serial interface is compliant with I<sup>2</sup>C and SMBus AC and DC specifications. The timing is compatible with 400Kbit operation for both. This includes the SMBus legacy tHD:DATO timing of 300ns minimum.

In addition, the LTC4283 supports 1Mbit operation which is compatible with I<sup>2</sup>C FastMode+ and SMBus 3.0. To use this timing, the FAST\_I2C\_EN bit in the CONFIG\_3 register must be set. This bit may be set to 1 as default by EEPROM, or it can be manually written to 1. If the bit is 0 before writing, the write must be done at 400Kbit or less. With FAST\_I2C\_EN set, tHD:DATO is reduced to allow higher speed transfers.

The LTC4283 SDAO output is guaranteed to pull down 20mA. This allows the use of a lower value pull-up resistor to reduce the low-to-high delay time.

### START, REPEATED START and STOP Conditions

When the bus is idle, SCL and SDA are high. A bus master signals the start of a transfer with a START condition. START is defined by a falling edge on SDA while SCL is high. The end of the transfer is signaled by a STOP condition. STOP is defined by a rising edge on SDA while SCL is high (see Figure 19).

In between START and STOP, data and handshake bits are transferred with a data value on SDA and a high pulse on SCL. For data or handshake bits, SDA changes only while SCL is low.

A bus master may also signal a REPEATED START condition in the middle of a transfer. Like START, REPEATED START is defined by a falling edge on SDA while SCL is high. REPEATED START is used in read transfers (see Transfer Protocol Types).

### ACK/NACK

Data is transferred as a series of 8-bit bytes. Following each data byte is a handshake bit driven by the receiver. SDA low during this bit is interpreted as acknowledge (ACK). SDA high is interpreted as not-acknowledge (NACK).

In all cases, a transfer stops after a NACK bit. If the bus master is sending a data byte, a NACK from the slave

indicates an error condition. If all bytes written are ACK'ed, the bus master may also terminate a write by making a STOP condition after the final byte. If the bus master is receiving a data, it returns NACK after the last byte it wants to receive. This is normal, no error condition is implied.

### I<sup>2</sup>C Device Addressing

The bus master addresses a slave by sending a slave address byte after either a START or REPEATED START condition. Bit 0 of the slave address byte is high to select a read transfer and low to select a write. See Transfer Protocol Types for more detail. The LTC4283 ADR1 and ADR0 pins can be configured to select its slave addresses as shown in Table 1.

Single-wire broadcast mode replaces the normal serialbus interface with a one-wire option which continuously broadcasts important status from the LTC4283. See more details in Single-Wire Broadcast.

### **Transfer Protocol Types**

Figure 19 shows basic elements of the  $I^2C$  protocol. These are combined to form complete read and write transfers. Figures 20 to 26 show the transfer protocol types supported by the LTC4283.

| 10010 1. 2104200 | D D G VIGG P               | านนาธรรกกรุ    | 1  |                       |    |    |    |    |    |      |      |      |  |
|------------------|----------------------------|----------------|----|-----------------------|----|----|----|----|----|------|------|------|--|
| DESCRIPTION      | HEX D<br>Addf              | EVICE<br>Ress* |    | BINARY DEVICE ADDRESS |    |    |    |    |    |      |      |      |  |
|                  | 7-Bit                      | 8-Bit          | a6 | a5                    | a4 | a3 | a2 | a1 | a0 | R/W# | ADR1 | ADRO |  |
| Mass Write       | 1F                         | 3E             | 0  | 0                     | 1  | 1  | 1  | 1  | 1  | 0    | Х    | Х    |  |
| Alert Response   | 0C                         | 19             | 0  | 0                     | 0  | 1  | 1  | 0  | 0  | 1    | Х    | Х    |  |
| 0                | 10                         | 20             | 0  | 0                     | 1  | 0  | 0  | 0  | 0  | Х    | L    | L    |  |
| 1                | 11                         | 22             | 0  | 0                     | 1  | 0  | 0  | 0  | 1  | Х    | L    | NC   |  |
| 2                | 12                         | 24             | 0  | 0                     | 1  | 0  | 0  | 1  | 0  | Х    | Н    | NC   |  |
| 3                | 13                         | 26             | 0  | 0                     | 1  | 0  | 0  | 1  | 1  | Х    | L    | Н    |  |
| 4                | 14                         | 28             | 0  | 0                     | 1  | 0  | 1  | 0  | 0  | Х    | NC   | L    |  |
| 5                | 15                         | 2A             | 0  | 0                     | 1  | 0  | 1  | 0  | 1  | Х    | NC   | NC   |  |
| 6                | 16                         | 20             | 0  | 0                     | 1  | 0  | 1  | 1  | 0  | Х    | Н    | Н    |  |
| 7                | 17                         | 2E             | 0  | 0                     | 1  | 0  | 1  | 1  | 1  | Х    | NC   | Н    |  |
| 8                | Single-Wire Broadcast Mode |                |    |                       |    |    |    |    | Н  | L    |      |      |  |

 Table 1. LTC4283 Device Addressing

H = Tie to INTV<sub>CC</sub>; L = Tie to  $V_{EE}$ ; NC = No connect or open; X = Don't Care

\*8-bit hexadecimal address with LSB R/ $\overline{W}$  bit = 0

7-bit hexadecimal address with MSB a7 = 0





R: READ BIT (HIGH) W: WRITE BIT (LOW) S: START CONDITION SR: REPEATED START CONDITION P: STOP CONDITION

# 001 a3:a0 0 0 b7:b0 0 b7:b0

WA

ADDRESS

S

#### Figure 20. Write Byte Protocol

Figure 21. Write Word Protocol

A DATA

DATA A P

4283 F21

A

0 b7:b0 0

COMMAND

| S | ADDRESS   | W | A | COMMAND | A | DATA  |     | A | DATA  | A  | Р       |
|---|-----------|---|---|---------|---|-------|-----|---|-------|----|---------|
|   | 001 a3:a0 | 0 | 0 | b7:b0   | 0 | b7:b0 | ••• | 0 | b7:b0 | 0  |         |
|   |           |   |   |         |   |       |     |   |       | 4: | 283 F22 |

Figure 22. Write Page Protocol

| S | ADDRESS   | W | A | COMMAND | A | SR | ADDRESS   | R | A | DATA  | Ā  | Р       |
|---|-----------|---|---|---------|---|----|-----------|---|---|-------|----|---------|
|   | 001 a3:a0 | 0 | 0 | b7:b0   | 0 |    | 001 a3:a0 | 1 | 0 | b7:b0 | 1  |         |
|   |           |   |   |         |   |    |           |   |   |       | 42 | 283 F23 |

Figure 23. Read Byte Protocol

| S | ADDRESS   | W | A | COMMAND | A | SR | ADDRESS   | R | A | DATA  | A | DATA  | Ā | Р       |
|---|-----------|---|---|---------|---|----|-----------|---|---|-------|---|-------|---|---------|
|   | 001 a3:a0 | 0 | 0 | b7:b0   | 0 |    | 001 a3:a0 | 1 | 0 | b7:b0 | 0 | b7:b0 | 1 |         |
|   |           |   |   |         |   |    |           |   |   |       |   |       | 4 | 283 F24 |

#### Figure 24. Read Word Protocol

| S | ADDRESS   | W | A | COMMAND | A | SR | ADDRESS   | R | A | DATA  | A |     | DATA  | Ā  | Р       |
|---|-----------|---|---|---------|---|----|-----------|---|---|-------|---|-----|-------|----|---------|
|   | 001 a3:a0 | 0 | 0 | b7:b0   | 0 |    | 001 a3:a0 | 1 | 0 | b7:b0 | 0 | ••• | b7:b0 | 1  |         |
|   |           |   |   |         |   |    |           |   |   |       |   |     |       | 42 | 283 F25 |

#### Figure 25. Read Page Protocol

| s | ALERT<br>RESPONSE<br>ADDRESS | R | A | DEVICE<br>Address | Ā | P |
|---|------------------------------|---|---|-------------------|---|---|
|   | 0001100                      | 1 | 0 | 001 a3:a0 0       | 1 |   |

Figure 26. Alert Response Protocol

Rev. 0

### **Command Codes and Register Addressing**

The command byte in each transfer contains the register address for the first byte being accessed. If multiple bytes are accessed in a transfer, each comes from the address following the previous byte. For example, when reading the six-byte ENERGY register, the first byte comes from address 0x7A, the second byte from address 0x7B, up through the final byte from address 0x7F (see Table 3).

It's possible to access two different registers in one transfer. For example, the SYSTEM\_STATUS and ADC\_STATUS registers can be accessed using a read word transfer with COMMAND equal 0x00. This addressing method is common for  $I^2C$  systems, but differs from SMBus. With SMBus, each register occupies a single command code, regardless of register size.

Registers 0x41 to 0x79 are implemented in 16-bit RAM words as shown in Table 3. To save command codes, each occupies only one register address. Consider a four-byte read with command code of 0x41. Data will be returned in this order:

- 1. Most significant byte of SENSE
- 2. Least significant byte of SENSE
- 3. Most significant byte of SENSE\_MIN
- 4. Least significant byte of SENSE\_MIN

### Write Protocols

For writes, all data bytes come from the bus master and are acknowledged by the slave. Bit 0 of the slave address byte is clear to select write. The COMMAND byte contains the register address for the first byte being written.

A special slave address can be used to implement mass writes. If multiple LTC4283 chips are on the same serial bus, the mass write technique can be used to write all of them at the same time. All LTC4283s respond to a slave address of 0011\_111b with the Read/Write# bit clear.

Bit MASS\_WRITE\_ENABLE in register CONTROL\_1 can be set to enable mass writes.

### **Read Protocols**

Reads consist of two parts. First the master sends a slave address byte with bit 0 clear and a COMMAND byte to select the register to be read from. After this, a REPEATED START condition and second slave address byte are sent with bit 0 set (indicating read). The LTC4283 replies with data after the second slave address byte.

### **Read Page and Write Page Protocols**

Read page and write page refer to transfers larger than two bytes. Page accesses are convenient for reading larger registers and for synchronizing data in multiple registers (see Data Synchronization and Arbitration for details). If page accesses are required, the PAGE\_READ\_ WRITE\_ENABLE bit in the CONTROL\_1 register should be set. If the bit is not set, accesses to more than two bytes of data will be terminated. For an attempted page write, the extra bytes would be NACK'ed. For an attempted page read, the LTC4283 would return 0xFF.

### **Byte Ordering**

The LTC4283 uses big endian ordering for accessing multi-byte registers. That means when a 16-bit word register is accessed, the most significant byte is transferred first, followed by the least significant byte. This is common in  $I^2C$  systems. SMBus systems use little endian ordering, with least significant byte transferred first.

### ALERT# and Alert Response Protocol

The LTC4283 fully supports the SMBus alert response mechanism. Refer to Figure 26:

- 1. If ALERT# is low, the LTC4283 will acknowledge the SMBus alert response address (ARA).
- 2. In the following data byte, the LTC4283 returns its own slave address, with bit 0 clear. Multiple slave devices on the bus may be responding to the same ARA. If a conflict is detected on any bit, the LTC4283 will back off and let the higher priority device continue.

 If the LTC4283 successfully transfers its entire slave address, it will clear its ALERT\_GENERATED bit, and stop pulling ALERT# low.

There are 52 possible conditions to set ALERT\_ GENERATED. Each condition (fault or event) has a corresponding alert enable bit. Table 24 has the list of fault/ event bits and alert enable bits.

For all cases, ALERT\_GENERATED will only be set by a rising edge on the combination of fault/event logically and'ed with alert enable bit. ALERT\_GENERATED is set whether a fault/event bit is set first or the corresponding alert enable bit is set first. Once a fault or event bit is set, it won't contribute to ALERT\_GENERATED again until the fault or event is cleared.

One event, ADC conversion completed, doesn't have a latched status bit. There is a corresponding ADC\_CONV\_ALERT bit to enable the ALERT\_GENERATED. But when servicing ALERT#, software won't have a way to verify that a completed ADC conversion caused the alert condition. Due to this limitation, the ADC conversion completed alert is not useful unless all other alert sources are masked off.

Typically, software will read the event and fault registers to check status, then write 0's to clear the bits that have been serviced. Event and fault bits can also be set directly by the  $I^2C$  bus. A bit set this way leads to ALERT\_ GENERATED set and ALERT# low in the same way as when the chip sets the bit. ALERT\_GENERATED itself can also be set by an  $I^2C$  write. These features may be helpful for software test.

### Stuck Bus Reset

The LTC4283 has an SMBus-style stuck bus reset. If the serial bus remains stuck for about 30ms, the I<sup>2</sup>C controller block will reset itself. When the controller is reset, it stops pulling down SDAO and searches for a new START condition.

In the SMBus definition, the stuck bus timer is cleared by SCL high. Many existing LTC chips including previous hot swap controllers clear the timer when SCL and SDA are

both high. This is more thorough because it can detect either SDA or SCL stuck low.

The method presents a problem with the LTC4283. With read page or write page, very long transfers are possible. For each byte of 0x00 transferred, SDA will be low for the whole byte. A long sequence of 0x00 bytes may lead to false stuck bus timeouts. The LTC4283 uses a modified stuck bus mechanism to prevent false timeouts. The timer is cleared If SCL is high and the LTC4283 is not pulling down SDAO.

As with other stuck bus timers, SCL stuck low causes a timeout. In addition, a timeout happens if the LTC4283 continuously pulls down SDAO for 30ms. This could happen if the bus stops with SCL high while the LTC4283 is still pulling down on SDAO.

### **Data Synchronization and Arbitration**

Several RAM locations and registers in the LTC4283 have control shared between ADC logic and the I<sup>2</sup>C interface. ADC logic writes data and the I<sup>2</sup>C interface reads from them. The RAM locations are at addresses between 0x41 and 0x79. Registers for ENERGY and TICK\_COUNTER are at addresses between 0x7A and 0x83. These registers are also written by ADC logic.

ADC writes to ENERGY, TICK\_COUNTER and the ADC RAM locations are always done while the  $l^2C$  interface is idle. That ensures none of the locations can change in the middle of an  $l^2C$  read. For example, when reading a two-byte RAM location, the two bytes read will always be consistent with each other.

The ENERGY and TICK\_COUNTER registers are larger, but the same technique can be used. To ensure consistency, read all bytes of each register in a single  $I^2C$  operation. For energy calculations, you may also need ENERGY and TICK\_COUNTER to be consistent with each other. This can be done by reading both registers together in a single 10-byte  $I^2C$  read. The register locations are contiguous to facilitate this approach. Read 10 bytes starting at register location 0x7A.

There are some limits on the length of  $I^2C$  transfers. If any one transfer takes longer than an ADC conversion time, some ADC data will be lost. This depends on the bus speed, transfer length and ADC conversion time. See the ADC[2:0] field in Table 12.

As detailed above, the I<sup>2</sup>C interface operates in parallel with ADC update logic. In some other cases, I<sup>2</sup>C access will be disabled:

- 1. After a power-on reset or reboot, I<sup>2</sup>C access is disabled while configuration registers are being loaded from EEPROM.
- 2. While a fault log is being written to EEPROM
- 3. After a write to the REBOOT register which sets the RBT\_EN bit.

In these cases, the  $I^2C$  controller ignores all inputs and SDAO is not pulled down. As a result, slave address and other bytes from the bus master will be NACK'ed. This behavior is common in  $I^2C$  systems. Be careful with this when operating in an SMBus system. The SMBus specification requires all slave address bytes to be ACK'ed but the LTC4283 doesn't ACK them in the three cases listed above.

While reading data from the LTC4283, the ACK for each byte comes from the bus master. There's no way for the LTC4283 to indicate a problem during the read. If the I<sup>2</sup>C controller is disabled during a read, bytes of 0xFF will be returned by the LTC4283 in place of the expected data.

### Single-Wire Broadcast

The LTC4283 can start itself up without any  $I^2C$  activity. The chip automatically loads configuration data from EEPROM to working registers after a power up or reboot. In this case, the user may not need a full  $I^2C$  interface. For many system applications, a full  $I^2C$  interface would require three isolators (see Figure 2b). Use of the singlewire broadcast mode can reduce this to one isolator.

When ADR1 is connected to  $INTV_{CC}$  and ADR0 is connected to  $V_{EE}$ , single-wire broadcast mode is selected. In this mode, I<sup>2</sup>C bus operation is disabled. In its place, status and ADC information are continually transmitted

on SDAO. A packet of 20 bytes as shown in Table 2 is transmitted once for each ADC conversion cycle using Manchester encoding.

The packet is in the following format:

| Preamble—0x2A         N/A         8           SENSE         0x41         16           VPWR         0x44         16           POWER         0x47         16           V <sub>AUX</sub> Most recent ADC aux reading         16           SYSTEM_STATUS         0x00         8           ADC_STATUS         0x01         8           INPUT_STATUS         0x02         8           FAULT_STATUS         0x03         8           FAULT_OX04         8         8           ADC_ALARM_LOG         0x05–0x09         40           PEC         N/A         8 | DATA             | ADDRESS                     | SIZE IN BITS |
|---|------------------|-----------------------------|--------------|
| SENSE0x4116VPWR0x4416POWER0x4716VAUXMost recent ADC aux reading16SYSTEM_STATUS0x008ADC_STATUS0x018INPUT_STATUS0x028FAULT_STATUS0x038FAULT0x048ADC_ALARM_LOG0x05-0x0940PECN/A8   | Preamble—0x2A    | N/A                         | 8            |
| VPWR0x4416POWER0x4716VAUXMost recent ADC aux reading16SYSTEM_STATUS0x008ADC_STATUS0x018INPUT_STATUS0x028FAULT_STATUS0x038FAULT0x048ADC_ALARM_LOG0x05–0x0940PECN/A8  | SENSE            | 0x41                        | 16           |
| POWER0x4716VAUXMost recent ADC aux reading16SYSTEM_STATUS0x008ADC_STATUS0x018INPUT_STATUS0x028FAULT_STATUS0x038FAULT0x048ADC_ALARM_LOG0x05–0x0940PECN/A8  | VPWR             | 0x44                        | 16           |
| VAUXMost recent ADC aux reading16SYSTEM_STATUS0x008ADC_STATUS0x018INPUT_STATUS0x028FAULT_STATUS0x038FAULT0x048ADC_ALARM_LOG0x05–0x0940PECN/A8   | POWER            | 0x47                        | 16           |
| SYSTEM_STATUS0x008ADC_STATUS0x018INPUT_STATUS0x028FAULT_STATUS0x038FAULT0x048ADC_ALARM_LOG0x05–0x0940PECN/A8  | V <sub>AUX</sub> | Most recent ADC aux reading | 16           |
| ADC_STATUS0x018INPUT_STATUS0x028FAULT_STATUS0x038FAULT0x048ADC_ALARM_LOG0x05-0x0940PECN/A8  | SYSTEM_STATUS    | 0x00                        | 8            |
| INPUT_STATUS         0x02         8           FAULT_STATUS         0x03         8           FAULT         0x04         8           ADC_ALARM_LOG         0x05–0x09         40           PEC         N/A         8   | ADC_STATUS       | 0x01                        | 8            |
| FAULT_STATUS         0x03         8           FAULT         0x04         8           ADC_ALARM_LOG         0x05–0x09         40           PEC         N/A         8   | INPUT_STATUS     | 0x02                        | 8            |
| FAULT         0x04         8           ADC_ALARM_LOG         0x05–0x09         40           PEC         N/A         8   | FAULT_STATUS     | 0x03                        | 8            |
| ADC_ALARM_LOG         0x05–0x09         40           PEC         N/A         8  | FAULT            | 0x04                        | 8            |
| PEC N/A 8   | ADC_ALARM_LOG    | 0x05-0x09                   | 40           |
| T   | PEC              | N/A                         | 8            |
| Iotal 160   | Total            |                             | 160          |

The preamble byte is a fixed pattern to allow hardware or software to detect the packet start and bit rate as shown in Figure 28.  $V_{AUX}$  is a selected auxiliary channel measurement. In each ADC conversion cycle, one auxiliary channel may be measured. Bits [7:4] of ADC\_STATUS contain the AUX\_ADC\_CH field to identify which ADC auxiliary input is present in the  $V_{AUX}$  field. See the Data Converters section for an explanation of the channel select sequence.

Two different conventions are followed: G.E. Thomas and IEEE 802.3 as shown in Figure 27. For G.E. Thomas convention, each data 1 bit is represented by a falling edge in the middle of the bit cell. For IEEE 802.3 convention, data 1 bits are represented by a rising edge in the middle of the bit cell. G.E. Thomas convention is used for the LTC4283. This is the same as for the LTC4261 and LTC4284.

The final byte of the packet is an SMBus-compatible PEC byte. PEC uses an 8-bit CRC with the polynomial X8 + X2 + X + 1. PEC covers all bytes of the packet including the preamble. The PEC accumulator is initialized to 0x00 at the start of the packet.

The data rate of single-wire broadcast can be selected using field BC in the CONFIG\_3 register, see Table 11. In broadcast mode, there needs to be enough time to transmit the entire 20-byte packet before another ADC update. That limit means the slowest data rates (128k and 32k) can't be used when the ADC is configured for 8-bit samples. In those two cases, the LTC4283 automatically switches to a minimum 512k data rate for single-wire broadcast.



Figure 28. Manchester Encoding for the Preamble Byte of 0x2A

#### Table 3. LTC4283 Register Address and Contents

| REGISTER NAME | REGISTER<br>ADDRESS* | DESCRIPTION   | READ/<br>WRITE | DATA<br>Length<br>(Bytes) | DEFAULT VALUE  |
|---------------|----------------------|---|----------------|---------------------------|----------------|
| SYSTEM_STATUS | 0x00                 | System status information   | R              | 1                         | N/A            |
| ADC_STATUS    | 0x01                 | ADC conversion status   | R              | 1                         | N/A            |
| INPUT_STATUS  | 0x02                 | PGI01–PGI04, ADI01–ADI04 general purpose input status                   | R              | 1                         | N/A            |
| FAULT_STATUS  | 0x03                 | Fault status information  | R              | 1                         | N/A            |
| FAULT         | 0x04                 | System fault  | R/W            | 1                         | 0x00           |
| ADC_ALARM_LOG | 0x05-0x09            | ADC measurement alarms  | R/W            | 5                         | 0x0000_0000_00 |
| CONTROL       | 0x0A-0x0B            | Controls the system on/off and auto-retry behaviors                     | R/W            | 2                         | 0xDB03         |
| Reserved      | 0x0C                 | Read only, always returns 0   | R              | 1                         | N/A            |
| CONFIG        | 0x0D-0x0F            | Configures current limit, foldback, delays, and other system parameters | R/W            | 3                         | 0x0CC0_00      |
| PGIO_CONFIG   | 0x10-0x11            | Configures I/O states and outputs of PGI01–PGI04                        | R/W            | 2                         | 0x0004         |
| ADIO_CONFIG   | 0x12                 | Configures I/O states and outputs of ADIO1–ADIO4, controls ADC          | R/W            | 1                         | 0xF0           |
| ADC_SELECT    | 0x13-0x14            | Auxiliary ADC inputs selection  | R/W            | 2                         | 0xFF0F         |
| FAULT_ALERT   | 0x15                 | Controls whether ALERT# pulls low after a system fault is logged        | R/W            | 1                         | 0x00           |
| ADC_ALERT     | 0x16-0x1A            | Controls whether ALERT# pulls low after an ADC alarm is logged          | R/W            | 5                         | 0x0000_0000_00 |
| SENSE_MIN_TH  | 0x1B                 | ADC alarm threshold for minimum SENSE <sup>+</sup> – SENSE <sup>–</sup> | R/W            | 1                         | 0x00           |
| SENSE_MAX_TH  | 0x1C                 | ADC alarm threshold for maximum SENSE <sup>+</sup> – SENSE <sup>–</sup> | R/W            | 1                         | 0xFF           |
| VPWR_MIN_TH   | 0x1D                 | ADC alarm threshold for minimum VPWR (RTNS/DRNS) voltage                | R/W            | 1                         | 0x00           |
| VPWR_MAX_TH   | 0x1E                 | ADC alarm threshold for maximum VPWR (RTNS/DRNS) voltage                | R/W            | 1                         | 0xFF           |
| POWER_MIN_TH  | 0x1F                 | ADC alarm threshold for minimum input power                             | R/W            | 1                         | 0x00           |
| POWER_MAX_TH  | 0x20                 | ADC alarm threshold for maximum input power                             | R/W            | 1                         | 0xFF           |
| ADIN1_MIN_TH  | 0x21                 | ADC alarm threshold for minimum ADIN1 voltage                           | R/W            | 1                         | 0x00           |
| ADIN1_MAX_TH  | 0x22                 | ADC alarm threshold for maximum ADIN1 voltage                           | R/W            | 1                         | 0xFF           |
| ADIN2_MIN_TH  | 0x23                 | ADC alarm threshold for minimum ADIN2 voltage                           | R/W            | 1                         | 0x00           |
| ADIN2_MAX_TH  | 0x24                 | ADC alarm threshold for maximum ADIN2 voltage                           | R/W            | 1                         | 0xFF           |
| ADIN3_MIN_TH  | 0x25                 | ADC alarm threshold for minimum ADIN3 voltage                           | R/W            | 1                         | 0x00           |
| ADIN3_MAX_TH  | 0x26                 | ADC alarm threshold for maximum ADIN3 voltage                           | R/W            | 1                         | 0xFF           |
| ADIN4_MIN_TH  | 0x27                 | ADC alarm threshold for minimum ADIN4 voltage                           | R/W            | 1                         | 0x00           |
| ADIN4_MAX_TH  | 0x28                 | ADC alarm threshold for maximum ADIN4 voltage                           | R/W            | 1                         | 0xFF           |
| ADIO1_MIN_TH  | 0x29                 | ADC alarm threshold for minimum ADIO1 voltage                           | R/W            | 1                         | 0x00           |
| ADIO1_MAX_TH  | 0x2A                 | ADC alarm threshold for maximum ADIO1 voltage                           | R/W            | 1                         | 0xFF           |
| ADIO2_MIN_TH  | 0x2B                 | ADC alarm threshold for minimum ADIO2 voltage                           | R/W            | 1                         | 0x00           |
| ADIO2_MAX_TH  | 0x2C                 | ADC alarm threshold for maximum ADIO2 voltage                           | R/W            | 1                         | 0xFF           |
| ADIO3_MIN_TH  | 0x2D                 | ADC alarm threshold for minimum ADIO3 voltage                           | R/W            | 1                         | 0x00           |
| ADIO3_MAX_TH  | 0x2E                 | ADC alarm threshold for maximum ADIO3 voltage                           | R/W            | 1                         | 0xFF           |
| ADIO4_MIN_TH  | 0x2F                 | ADC alarm threshold for minimum ADIO4 voltage                           | R/W            | 1                         | 0x00           |
| ADIO4_MAX_TH  | 0x30                 | ADC alarm threshold for maximum ADIO4 voltage                           | R/W            | 1                         | 0xFF           |
| DRNS_MIN_TH   | 0x31                 | ADC alarm threshold for minimum DRNS voltage                            | R/W            | 1                         | 0x00           |
| DRNS_MAX_TH   | 0x32                 | ADC alarm threshold for maximum DRNS voltage                            | R/W            | 1                         | 0xFF           |
| DRAIN_MIN_TH  | 0x33                 | ADC alarm threshold for minimum DRAIN voltage                           | R/W            | 1                         | 0x00           |

Table 3. LTC4283 Register Address and Contents (Cont.)

| REGISTER NAME | REGISTER<br>Address* | DESCRIPTION  | READ/<br>WRITE | DATA<br>LENGTH<br>(BYTES) | DEFAULT VALUE |
|---------------|----------------------|--|----------------|---------------------------|---------------|
| DRAIN_MAX_TH  | 0x34                 | ADC alarm threshold for maximum DRAIN voltage                      | R/W            | 1                         | 0xFF          |
| Reserved      | 0x35                 | Undefined  | R/W            | 1                         | 0x00          |
| Reserved      | 0x36                 | Undefined  | R/W            | 1                         | 0xFF          |
| Reserved      | 0x37                 | Undefined  | R/W            | 1                         | 0x00          |
| Reserved      | 0x38                 | Undefined  | R/W            | 1                         | 0xFF          |
| ADIN12_MIN_TH | 0x39                 | ADC alarm threshold for minimum ADIN2 – ADIN1                      | R/W            | 1                         | 0x00          |
| ADIN12_MAX_TH | 0x3A                 | ADC alarm threshold for maximum ADIN2 – ADIN1                      | R/W            | 1                         | 0xFF          |
| ADIN34_MIN_TH | 0x3B                 | ADC alarm threshold for minimum ADIN4 – ADIN3                      | R/W            | 1                         | 0x00          |
| ADIN34_MAX_TH | 0x3C                 | ADC alarm threshold for maximum ADIN4 – ADIN3                      | R/W            | 1                         | 0xFF          |
| ADI012_MIN_TH | 0x3D                 | ADC alarm threshold for minimum ADI02 – ADI01                      | R/W            | 1                         | 0x00          |
| ADI012_MAX_TH | 0x3E                 | ADC alarm threshold for maximum ADIO2 – ADIO1                      | R/W            | 1                         | 0xFF          |
| ADIO34_MIN_TH | 0x3F                 | ADC alarm threshold for minimum ADIO4 – ADIO3                      | R/W            | 1                         | 0x00          |
| ADI034_MAX_TH | 0x40                 | ADC alarm threshold for maximum ADIO4 – ADIO3                      | R/W            | 1                         | 0xFF          |
| SENSE         | 0x41                 | Most recent ADC output for SENSE <sup>+</sup> – SENSE <sup>-</sup> | R/W            | 2                         | 0x0000        |
| SENSE_MIN     | 0x42                 | Minimum ADC output for SENSE <sup>+</sup> – SENSE <sup>-</sup>     | R/W            | 2                         | 0x0000        |
| SENSE_MAX     | 0x43                 | Maximum ADC output for SENSE <sup>+</sup> – SENSE <sup>-</sup>     | R/W            | 2                         | 0x0000        |
| VPWR          | 0x44                 | Most recent ADC output for VPWR (RTNS/DRNS)                        | R/W            | 2                         | 0x0000        |
| VPWR_MIN      | 0x45                 | Minimum ADC output for VPWR (RTNS/DRNS)                            | R/W            | 2                         | 0x0000        |
| VPWR_MAX      | 0x46                 | Maximum ADC output for VPWR (RTNS/DRNS)                            | R/W            | 2                         | 0x0000        |
| POWER         | 0x47                 | Most recent ADC output for power                                   | R/W            | 2                         | 0x0000        |
| POWER_MIN     | 0x48                 | Minimum ADC output for power                                       | R/W            | 2                         | 0x0000        |
| POWER_MAX     | 0x49                 | Maximum ADC output for power                                       | R/W            | 2                         | 0x0000        |
| ADIN1         | 0x4A                 | Most recent ADC output for ADIN1                                   | R/W            | 2                         | 0x0000        |
| ADIN1_MIN     | 0x4B                 | Minimum ADC output for ADIN1                                       | R/W            | 2                         | 0x0000        |
| ADIN1_MAX     | 0x4C                 | Maximum ADC output for ADIN1                                       | R/W            | 2                         | 0x0000        |
| ADIN2         | 0x4D                 | Most recent ADC output for ADIN2                                   | R/W            | 2                         | 0x0000        |
| ADIN2_MIN     | 0x4E                 | Minimum ADC output for ADIN2                                       | R/W            | 2                         | 0x0000        |
| ADIN2_MAX     | 0x4F                 | Maximum ADC output for ADIN2                                       | R/W            | 2                         | 0x0000        |
| ADIN3         | 0x50                 | Most recent ADC output for ADIN3                                   | R/W            | 2                         | 0x0000        |
| ADIN3_MIN     | 0x51                 | Minimum ADC output for ADIN3                                       | R/W            | 2                         | 0x0000        |
| ADIN3_MAX     | 0x52                 | Maximum ADC output for ADIN3                                       | R/W            | 2                         | 0x0000        |
| ADIN4         | 0x53                 | Most recent ADC output for ADIN4                                   | R/W            | 2                         | 0x0000        |
| ADIN4_MIN     | 0x54                 | Minimum ADC output for ADIN4                                       | R/W            | 2                         | 0x0000        |
| ADIN4_MAX     | 0x55                 | Maximum ADC output for ADIN4                                       | R/W            | 2                         | 0x0000        |
| ADIO1         | 0x56                 | Most recent ADC output for ADIO1                                   | R/W            | 2                         | 0x0000        |
| ADIO1_MIN     | 0x57                 | Minimum ADC output for ADI01                                       | R/W            | 2                         | 0x0000        |
| ADIO1_MAX     | 0x58                 | Maximum ADC output for ADI01                                       | R/W            | 2                         | 0x0000        |
| ADI02         | 0x59                 | Most recent ADC output for ADIO2                                   | R/W            | 2                         | 0x0000        |
| ADIO2_MIN     | 0x5A                 | Minimum ADC output for ADI02                                       | R/W            | 2                         | 0x0000        |

Table 3. LTC4283 Register Address and Contents (Cont.)

| REGISTER NAME     | REGISTER<br>ADDRESS* | DESCRIPTION  | READ/<br>Write | DATA<br>LENGTH<br>(BYTES) | DEFAULT VALUE    |
|-------------------|----------------------|--|----------------|---------------------------|------------------|
| ADIO2_MAX         | 0x5B                 | Maximum ADC output for ADIO2                             | R/W            | 2                         | 0x0000           |
| ADI03             | 0x5C                 | Most recent ADC output for ADIO3                         | R/W            | 2                         | 0x0000           |
| ADIO3_MIN         | 0x5D                 | Minimum ADC output for ADIO3                             | R/W            | 2                         | 0x0000           |
| ADIO3_MAX         | 0x5E                 | Maximum ADC output for ADIO3                             | R/W            | 2                         | 0x0000           |
| ADIO4             | 0x5F                 | Most recent ADC output for ADIO4                         | R/W            | 2                         | 0x0000           |
| ADIO4_MIN         | 0x60                 | Minimum ADC output for ADIO4                             | R/W            | 2                         | 0x0000           |
| ADIO4_MAX         | 0x61                 | Maximum ADC output for ADIO4                             | R/W            | 2                         | 0x0000           |
| DRNS              | 0x62                 | Most recent ADC output for DRNS                          | R/W            | 2                         | 0x0000           |
| DRNS_MIN          | 0x63                 | Minimum ADC output for DRNS                              | R/W            | 2                         | 0x0000           |
| DRNS_MAX          | 0x64                 | Maximum ADC output for DRNS                              | R/W            | 2                         | 0x0000           |
| DRAIN             | 0x65                 | Most recent ADC output for DRAIN                         | R/W            | 2                         | 0x0000           |
| DRAIN_MIN         | 0x66                 | Minimum ADC output for DRAIN                             | R/W            | 2                         | 0x0000           |
| DRAIN_MAX         | 0x67                 | Maximum ADC output for DRAIN                             | R/W            | 2                         | 0x0000           |
| Reserved          | 0x68                 | Undefined  | R/W            | 2                         | N/A              |
| Reserved          | 0x69                 | Undefined  | R/W            | 2                         | N/A              |
| Reserved          | 0x6A                 | Undefined  | R/W            | 2                         | N/A              |
| Reserved          | 0x6B                 | Undefined  | R/W            | 2                         | N/A              |
| Reserved          | 0x6C                 | Undefined  | R/W            | 2                         | N/A              |
| Reserved          | 0x6D                 | Undefined  | R/W            | 2                         | N/A              |
| ADIN12            | 0x6E                 | Most recent ADC output for ADIN2 – ADIN1                 | R/W            | 2                         | 0x0000           |
| ADIN12_MIN        | 0x6F                 | Minimum ADC output for ADIN2 – ADIN1                     | R/W            | 2                         | 0x0000           |
| ADIN12_MAX        | 0x70                 | Maximum ADC output for ADIN2 – ADIN1                     | R/W            | 2                         | 0x0000           |
| ADIN34            | 0x71                 | Most recent ADC output for ADIN4 – ADIN3                 | R/W            | 2                         | 0x0000           |
| ADIN34_MIN        | 0x72                 | Minimum ADC output for ADIN4 – ADIN3                     | R/W            | 2                         | 0x0000           |
| ADIN34_MAX        | 0x73                 | Maximum ADC output for ADIN4 – ADIN3                     | R/W            | 2                         | 0x0000           |
| ADI012            | 0x74                 | Most recent ADC output for ADIO2 – ADIO1                 | R/W            | 2                         | 0x0000           |
| ADIO12_MIN        | 0x75                 | Minimum ADC output for ADIO2 – ADIO1                     | R/W            | 2                         | 0x0000           |
| ADI012_MAX        | 0x76                 | Maximum ADC output for ADIO2 – ADIO1                     | R/W            | 2                         | 0x0000           |
| ADIO34            | 0x77                 | Most recent ADC output for ADIO4 – ADIO3                 | R/W            | 2                         | 0x0000           |
| ADIO34_MIN        | 0x78                 | Minimum ADC output for ADIO4 – ADIO3                     | R/W            | 2                         | 0x0000           |
| ADIO34_MAX        | 0x79                 | Maximum ADC output for ADIO4 – ADIO3                     | R/W            | 2                         | 0x0000           |
| ENERGY            | 0x7A-0x7F            | Input energy meter                                       | R/W            | 6                         | 0x0000_0000_0000 |
| TICK_COUNTER      | 0x80-0x83            | Tick counter for energy meter                            | R/W            | 4                         | 0x0000_0000      |
| METER_CONTROL     | 0x84                 | Controls energy meter and tick counter                   | R/W            | 1                         | 0x00             |
| ADC_SNAPSHOT      | 0x85                 | Controls ADC snapshot                                    | R/W            | 1                         | 0x00             |
| Reserved          | 0x86-0x8F            | Read only, always returns 0                              | R              | 10                        | N/A              |
| FAULT_LOG_CONTROL | 0x90                 | Enables logging fault and ADC data into EEPROM           | R/W            | 1                         | 0x00             |
| Reserved          | 0x91-0xA1            | Read only, 0x91–0x9F return 0xFF, 0xA0 and 0xA1 return 0 | R              | 17                        | N/A              |
| REBOOT            | 0xA2                 | Enables reboot and configures reboot delay               | R/W            | 1                         | 0x00             |

Table 3. LTC4283 Register Address and Contents (Cont.)

| REGISTER NAME    | REGISTER<br>Address* | DESCRIPTION   | READ/<br>WRITE | DATA<br>LENGTH<br>(BYTES) | DEFAULT VALUE  |
|------------------|----------------------|---|----------------|---------------------------|----------------|
| Reserved         | 0xA3                 | Read only, always returns 0                                 | R              | 1                         | N/A            |
| EE_FAULT         | 0xA4                 | Records fault register in EEPROM upon a fault               | R/W            | 1                         | 0x00           |
| EE_ADC_ALARM_LOG | 0xA5-0xA9            | Records ADC_ALARM_LOG registers in EEPROM upon a fault      | R/W            | 5                         | 0x0000_0000_00 |
| EE_CONTROL       | 0xAA-0xAB            | Stores default of CONTROL registers in EEPROM               | R/W            | 2                         | 0xDB03         |
| Reserved         | 0xAC                 | Read only, returns 0xFF if EEPROM busy, otherwise returns 0 | R              | 1                         | N/A            |
| EE_CONFIG        | 0xAD-0xAF            | Stores default of CONFIG registers in EEPROM                | R/W            | 3                         | 0x0CC0_00      |
| EE_PGIO_CONFIG   | 0xB0-0xB1            | Stores default of PGIO_CONFIG registers in EEPROM           | R/W            | 2                         | 0x0004         |
| EE_ADIO_CONFIG   | 0xB2                 | Stores default of ADIO_CONFIG register in EEPROM            | R/W            | 1                         | 0xF0           |
| EE_ADC_SELECT    | 0xB3-0xB4            | Stores default of ADC_SELECT registers in EEPROM            | R/W            | 2                         | 0xFF0F         |
| EE_FAULT_ALERT   | 0xB5                 | Stores default of FAULT_ALERT register in EEPROM            | R/W            | 1                         | 0x00           |
| EE_ADC_ALERT     | 0xB6-0xBA            | Stores default of ADC_ALERT registers in EEPROM             | R/W            | 5                         | 0x0000_0000_00 |
| EE_SENSE_MIN_TH  | 0xBB                 | Stores default of SENSE_MIN_TH register in EEPROM           | R/W            | 1                         | 0x00           |
| EE_SENSE_MAX_TH  | 0xBC                 | Stores default of SENSE_MAX_TH register in EEPROM           | R/W            | 1                         | 0xFF           |
| EE_VPWR_MIN_TH   | 0xBD                 | Stores default of VPWR_MIN_TH register in EEPROM            | R/W            | 1                         | 0x00           |
| EE_VPWR_MAX_TH   | 0xBE                 | Stores default of VPWR_MAX_TH register in EEPROM            | R/W            | 1                         | 0xFF           |
| EE_POWER_MIN_TH  | 0xBF                 | Stores default of POWER_MIN_TH register in EEPROM           | R/W            | 1                         | 0x00           |
| EE_POWER_MAX_TH  | 0xC0                 | Stores default of POWER_MAX_TH register in EEPROM           | R/W            | 1                         | 0xFF           |
| EE_ADIN1_MIN_TH  | 0xC1                 | Stores default of ADIN1_MIN_TH register in EEPROM           | R/W            | 1                         | 0x00           |
| EE_ADIN1_MAX_TH  | 0xC2                 | Stores default of ADIN1_MAX_TH register in EEPROM           | R/W            | 1                         | 0xFF           |
| EE_ADIN2_MIN_TH  | 0xC3                 | Stores default of ADIN2_MIN_TH register in EEPROM           | R/W            | 1                         | 0x00           |
| EE_ADIN2_MAX_TH  | 0xC4                 | Stores default of ADIN2_MAX_TH register in EEPROM           | R/W            | 1                         | 0xFF           |
| EE_ADIN3_MIN_TH  | 0xC5                 | Stores default of ADIN3_MIN_TH register in EEPROM           | R/W            | 1                         | 0x00           |
| EE_ADIN3_MAX_TH  | 0xC6                 | Stores default of ADIN3_MAX_TH register in EEPROM           | R/W            | 1                         | 0xFF           |
| EE_ADIN4_MIN_TH  | 0xC7                 | Stores default of ADIN4_MIN_TH register in EEPROM           | R/W            | 1                         | 0x00           |
| EE_ADIN4_MAX_TH  | 0xC8                 | Stores default of ADIN4_MAX_TH register in EEPROM           | R/W            | 1                         | 0xFF           |
| EE_ADIO1_MIN_TH  | 0xC9                 | Stores default of ADIO1_MIN_TH register in EEPROM           | R/W            | 1                         | 0x00           |
| EE_ADIO1_MAX_TH  | 0xCA                 | Stores default of ADIO1_MAX_TH register in EEPROM           | R/W            | 1                         | 0xFF           |
| EE_ADIO2_MIN_TH  | 0xCB                 | Stores default of ADI02_MIN_TH register in EEPROM           | R/W            | 1                         | 0x00           |
| EE_ADIO2_MAX_TH  | 0xCC                 | Stores default of ADIO2_MAX_TH register in EEPROM           | R/W            | 1                         | 0xFF           |
| EE_ADIO3_MIN_TH  | 0xCD                 | Stores default of ADIO3_MIN_TH register in EEPROM           | R/W            | 1                         | 0x00           |
| EE_ADIO3_MAX_TH  | 0xCE                 | Stores default of ADIO3_MAX_TH register in EEPROM           | R/W            | 1                         | 0xFF           |
| EE_ADIO4_MIN_TH  | 0xCF                 | Stores default of ADIO4_MIN_TH register in EEPROM           | R/W            | 1                         | 0x00           |
| EE_ADIO4_MAX_TH  | 0xD0                 | Stores default of ADIO4_MAX_TH register in EEPROM           | R/W            | 1                         | 0xFF           |
| EE_DRNS_MIN_TH   | 0xD1                 | Stores default of DRNS_MIN_TH register in EEPROM            | R/W            | 1                         | 0x00           |
| EE_DRNS_MAX_TH   | 0xD2                 | Stores default of DRNS_MAX_TH register in EEPROM            | R/W            | 1                         | 0xFF           |
| EE_DRAIN_MIN_TH  | 0xD3                 | Stores default of DRAIN_MIN_TH register in EEPROM           | R/W            | 1                         | 0x00           |
| EE_DRAIN_MAX_TH  | 0xD4                 | Stores default of DRAIN_MAX_TH register in EEPROM           | R/W            | 1                         | 0xFF           |
| Reserved         | 0xD5                 | Undefined   | R/W            | 1                         | 0x00           |
| Reserved         | 0xD6                 | Undefined   | R/W            | 1                         | 0xFF           |

Table 3. LTC4283 Register Address and Contents (Cont.)

| REGISTER NAME            | REGISTER<br>Address* | DESCRIPTION  | READ/<br>Write | DATA<br>LENGTH<br>(BYTES) | DEFAULT VALUE    |
|--------------------------|----------------------|--|----------------|---------------------------|------------------|
| Reserved                 | 0xD7                 | Undefined  | R/W            | 1                         | 0x00             |
| Reserved                 | 0xD8                 | Undefined  | R/W            | 1                         | 0xFF             |
| EE_ADIN12_MIN_TH         | 0xD9                 | Stores default of ADIN12_MIN_TH register in EEPROM             | R/W            | 1                         | 0x00             |
| EE_ADIN12_MAX_TH         | 0xDA                 | Stores default of ADIN12_MAX_TH register in EEPROM             | R/W            | 1                         | 0xFF             |
| EE_ADIN34_MIN_TH         | 0xDB                 | Stores default of ADIN34_MIN_TH register in EEPROM             | R/W            | 1                         | 0x00             |
| EE_ADIN34_MAX_TH         | 0xDC                 | Stores default of ADIN34_MAX_TH register in EEPROM             | R/W            | 1                         | 0xFF             |
| EE_ADI012_MIN_TH         | 0xDD                 | Stores default of ADI012_MIN_TH register in EEPROM             | R/W            | 1                         | 0x00             |
| EE_ADI012_MAX_TH         | 0xDE                 | Stores default of ADI012_MAX_TH register in EEPROM             | R/W            | 1                         | 0xFF             |
| EE_ADIO34_MIN_TH         | 0xDF                 | Stores default of ADIO34_MIN_TH register in EEPROM             | R/W            | 1                         | 0x00             |
| EE_ADIO34_MAX_TH         | 0xE0                 | Stores default of ADI034_MAX_TH register in EEPROM             | R/W            | 1                         | 0xFF             |
| EE_SENSE                 | 0xE1                 | Records MSB byte of SENSE registers in EEPROM upon a fault     | R/W            | 1                         | 0x00             |
| EE_SENSE_MIN             | 0xE2                 | Records MSB byte of SENSE_MIN registers in EEPROM upon a fault | R/W            | 1                         | 0x00             |
| EE_SENSE_MAX             | 0xE3                 | Records MSB byte of SENSE_MAX registers in EEPROM upon a fault | R/W            | 1                         | 0x00             |
| EE_RTNS                  | 0xE4                 | Records MSB byte of RTNS registers in EEPROM upon a fault      | R/W            | 1                         | 0x00             |
| EE_RTNS_MIN              | 0xE5                 | Records MSB byte of RTNS_MIN registers in EEPROM upon a fault  | R/W            | 1                         | 0x00             |
| EE_RTNS_MAX              | 0xE6                 | Records MSB byte of RTNS_MAX registers in EEPROM upon a fault  | R/W            | 1                         | 0x00             |
| POWER_PLAY_ID            | 0xE7-0xE8            | LTpowerPlay ID for LTC4283                                     | R              | 2                         | 0x0070           |
| EE_SCRATCH               | 0xE9-0xEF            | Spare EEPROM bytes   | R/W            | 7                         | 0x0000_0000_0000 |
| EE_FAULT_LOG_<br>CONTROL | 0xF0                 | EEPROM backup of FAULT_LOG_CONTROL register                    | R/W            | 1                         | 0x00             |
| Reserved                 | 0xF1-0xFF            | Read only, always returns 0xFF                                 | R              | 15                        | N/A              |

\*For the two-byte ADC data registers from 0x41 to 0x79, the address points to the MSB byte and increments to the LSB byte when using a Write Word or Read Word protocol.

### Table 4. SYSTEM\_STATUS Registers (0x00) - Read Only

| BIT | NAME          | OPERATION  |
|-----|---------------|--|
| 7   | FET_ON_STATUS | On/off status of GATE; 1 = GATE commanded on, 0 = GATE commanded off                   |
| 6   | EN#           | State of EN# pin; 1 = EN# high, 0 = EN# low  |
| 5   | GATE_HIGH     | State of GATE pin; 1 = GATE high, 0 = GATE low   |
| 4   | Reserved      | Undefined  |
| 3   | TMR_LOW       | Status of TMR pin; 1 = TMR is lower than 0.1V, 0 = TMR is higher than 0.1V             |
| 2   | EEPROM _BUSY  | Status of EEPROM writing; 1 = EEPROM is being written, 0 = EEPROM writing is completed |
| 1   | PG_STATUS     | Power good status; 1 = power good condition met, 0 = power good condition not met      |
| 0   | Reserved      | Always returns 1   |

### Table 5. ADC\_STATUS Register (0x01) - Read Only

| BIT | NAME       | OPERATION               |   |                      |  |  |  |  |
|-----|------------|-------------------------|---|----------------------|--|--|--|--|
| 7:4 | AUX_ADC_CH | Channel label of the au | Channel label of the auxiliary input that completed the latest ADC measurement in continuous or snapshot mode |                      |  |  |  |  |
|     |            | AUX_ADC_CH [7:4]        | Auxiliary ADC Input   | Register Address     |  |  |  |  |
|     |            | 0000                    | ADIN1   | 0x4A                 |  |  |  |  |
|     |            | 0001                    | ADIN2   | 0x4D                 |  |  |  |  |
|     |            | 0010                    | ADIN3   | 0x50                 | -  |  |  |  |
|     |            | 0011                    | ADIN4   | 0x53                 | -  |  |  |  |
|     |            | 0100                    | ADIO1   | 0x56                 |  |  |  |  |
|     |            | 0101                    | ADIO2   | 0x59                 | -  |  |  |  |
|     |            | 0110                    | ADIO3   | 0x5C                 | _  |  |  |  |
|     |            | 0111                    | ADIO4   | 0x5F                 | _  |  |  |  |
|     |            | 1000                    | DRNS  | 0x62                 | -  |  |  |  |
|     |            | 1001                    | DRAIN   | 0x65                 | _  |  |  |  |
|     |            | 1010                    | Reserved  | 0x68                 |  |  |  |  |
|     |            | 1011                    | Reserved  | 0x6B                 |  |  |  |  |
|     |            | 1100                    | ADIN2 – ADIN1   | 0x6E                 | -  |  |  |  |
|     |            | 1101                    | ADIN4 – ADIN3   | 0x71                 | _  |  |  |  |
|     |            | 1110                    | ADI02 – ADI01   | 0x74                 | _  |  |  |  |
|     |            | 1111                    | ADI04 – ADI03   | 0x77                 | -  |  |  |  |
| 3   | ADC_IDLE   | Conversion status of A  | DC; 1 = ADC is idle in s  | napshot mode, 0 = AD | OC is in continuous mode or ADC is busy in snapshot mode |  |  |  |
| 2   | Reserved   | Always returns 0        |   |                      |  |  |  |  |
| 1   | Reserved   | Always returns 0        |   |                      |  |  |  |  |
| 0   | Reserved   | Always returns 0        |   |                      |  |  |  |  |

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### Table 6. INPUT\_STATUS Register (0x02) - Read Only

| BIT | NAME        | OPERATION   |
|-----|-------------|---|
| 7   | PGI01_INPUT | State of PGI01 pin; 1 = PGI01 high, 0 = PGI01 low |
| 6   | PGI02_INPUT | State of PGI02 pin; 1 = PGI02 high, 0 = PGI02 low |
| 5   | PGI03_INPUT | State of PGI03 pin; 1 = PGI03 high, 0 = PGI03 low |
| 4   | PGI04_INPUT | State of PGIO4 pin; 1 = PGIO4 high, 0 = PGIO4 low |
| 3   | ADIO1_INPUT | State of ADIO1 pin; 1 = ADIO1 high, 0 = ADIO1 low |
| 2   | ADIO2_INPUT | State of ADIO2 pin; 1 = ADIO2 high, 0 = ADIO2 low |
| 1   | ADIO3_INPUT | State of ADIO3 pin; 1 = ADIO3 high, 0 = ADIO3 low |
| 0   | ADIO4_INPUT | State of ADIO4 pin; 1 = ADIO4 high, 0 = ADIO4 low |

#### Table 7. FAULT\_STATUS Register (0x03) - Read Only

| BIT | NAME             | OPERATION   |
|-----|------------------|---|
| 7   | EXT_FAULT_STATUS | State of PGIO4 pin when configured to EXT_FAULT#/EXT_FAULT; 1 = PGIO4 low/high, 0 = PGIO4 high/low              |
| 6   | FET_SHORT_STATUS | FET short status; 1 = FET shorted, 0 = FET not shorted  |
| 5   | VOUT_LOW         | $V_{OUT}$ low status; 1 = $V_{OUT} < V_{OUTTH}$ , 0 = $V_{OUT} \ge V_{OUTTH}$                                   |
| 4   | PGI_STATUS       | State of PGI03 when configured to PGI#/PGI when PGI check timer expires; 1 = PGI03 high/low, 0 = PGI03 low/high |
| 3   | FET_BAD_STATUS   | FET bad status; 1 = FET bad condition present, 0 = FET bad condition not present                                |
| 2   | OC_STATUS        | Active current limit status; 1 = active current limit engaged, 0 = active current limit not engaged             |
| 1   | UV_STATUS        | Input undervoltage status; 1 = UVH and UVL are low, 0 = UVH or UVL high   |
| 0   | OV_STATUS        | Input overvoltage status; 1 = OV high, 0 = OV low   |

#### Table 8. FAULT Register (0x04) - Read/Write

| BIT | NAME            | OPERATION  | DEFAULT |
|-----|-----------------|--|---------|
| 7   | EXT_FAULT       | External fault at PGIO4 pin; 1 = external fault detected, 0 = no external fault                        | 0       |
| 6   | FET_SHORT_FAULT | FET short fault; 1 = FET short fault occurred, 0 = no FET short fault                                  | 0       |
| 5   | POWER_FAILED    | $V_{OUT}$ was low after power good latched; 1 = $V_{OUT}$ low detected, 0 = $V_{OUT}$ has not been low | 0       |
| 4   | PGI_FAULT       | PGI fault at PGI03 pin; 1 = PGI fault occurred, 0 = no PGI fault                                       | 0       |
| 3   | FET_BAD_FAULT   | FET bad fault; 1 = FET bad fault occurred, 0 = no FET bad fault  | 0       |
| 2   | OC_FAULT        | Overcurrent fault; 1 = overcurrent fault occurred, 0 = no overcurrent fault                            | 0       |
| 1   | UV_FAULT        | Undervoltage fault; 1 = undervoltage fault occurred, 0 = no undervoltage fault                         | 0       |
| 0   | OV_FAULT        | Overvoltage fault; 1 = overvoltage fault occurred, 0 = no overvoltage fault                            | 0       |

### Table 9. ADC\_ALARM\_LOG Registers (0x05-0x09) - Read/Write

| BIT   | NAME                  | OPERATION   | DEFAULT |
|-------|-----------------------|---|---------|
| ADC_A | LARM_LOG_1 (0x05) – F | Read/Write  |         |
| 7     | EN#_CHANGED           | EN# pin changed state; 1 = EN# changed state, 0 = EN# unchanged   | 0       |
| 6     | EEPROM_WRITTEN        | EEPROM was written through I <sup>2</sup> C; 1 = EEPROM was written, 0 = EEPROM write has not been written  | 0       |
| 5     | SENSE_HIGH_ALARM      | SENSE <sup>+</sup> - SENSE <sup>-</sup> was above SENSE_MAX_TH; 1 = SENSE <sup>+</sup> - SENSE <sup>-</sup> was high, 0 = SENSE <sup>+</sup> - SENSE <sup>-</sup> has not been high | 0       |
| 4     | SENSE_LOW_ALARM       | SENSE <sup>+</sup> – SENSE <sup>-</sup> was below SENSE_MIN_TH; 1 = SENSE <sup>+</sup> – SENSE <sup>-</sup> was low, 0 = SENSE <sup>+</sup> – SENSE <sup>-</sup> has not been low   | 0       |
| 3     | VPWR_HIGH_ALARM       | VPWR was above VPWR_MAX_TH; 1 = VPWR was high, 0 = VPWR has not been high   | 0       |
| 2     | VPWR_LOW_ALARM        | VPWR was below VPWR_MIN_TH; 1 = VPWR was low, 0 = VPWR has not been low   | 0       |
| 1     | POWER_HIGH_ALARM      | POWER was above POWER_MAX_TH; 1 = POWER was high, 0 = POWER has not been high   | 0       |
| 0     | POWER_LOW_ALARM       | POWER was below POWER_MIN_TH; 1 = POWER was low, 0 = POWER has not been low   | 0       |
| ADC_A | LARM_LOG_2 (0x06) – F | Read/Write  |         |
| 7     | ADIN1_HIGH_ALARM      | ADIN1 was above ADIN1_MAX_TH; 1 = ADIN1 was high, 0 = ADIN1 has not been high   | 0       |
| 6     | ADIN1_LOW_ALARM       | ADIN1 was below ADIN1_MIN_TH; 1 = ADIN1 was low, 0 = ADIN1 has not been low   | 0       |
| 5     | ADIN2_HIGH_ALARM      | ADIN2 was above ADIN2_MAX_TH; 1 = ADIN2 was high, 0 = ADIN2 has not been high   | 0       |
| 4     | ADIN2_LOW_ALARM       | ADIN2 was below ADIN2_MIN_TH; 1 = ADIN2 was low, 0 = ADIN2 has not been low   | 0       |
| 3     | ADIN3_HIGH_ALARM      | ADIN3 was above ADIN3_MAX_TH; 1 = ADIN3 was high, 0 = ADIN3 has not been high   | 0       |
| 2     | ADIN3_LOW_ALARM       | ADIN3 was below ADIN3_MIN_TH; 1 = ADIN3 was low, 0 = ADIN3 has not been low   | 0       |
| 1     | ADIN4_HIGH_ALARM      | ADIN4 was above ADIN4_MAX_TH; 1 = ADIN4 was high, 0 = ADIN4 has not been high   | 0       |
| 0     | ADIN4_LOW_ALARM       | ADIN4 was below ADIN4_MIN_TH; 1 = ADIN4 was low, 0 = ADIN4 has not been low   | 0       |
| ADC_A | LARM_LOG_3 (0x07) – F | Read/Write  |         |
| 7     | ADIO1_HIGH_ALARM      | ADIO1 was above ADIO1_MAX_TH; 1 = ADIO1 was high, 0 = ADIO1 has not been high   | 0       |
| 6     | ADIO1_LOW_ALARM       | ADIO1 was below ADIO1_MIN_TH; 1 = ADIO1 was low, 0 = ADIO1 has not been low   | 0       |
| 5     | ADIO2_HIGH_ALARM      | ADIO2 was above ADIO2_MAX_TH; 1 = ADIO2 was high, 0 = ADIO2 has not been high   | 0       |
| 4     | ADI02_LOW_ALARM       | ADIO2 was below ADIO2_MIN_TH; 1 = ADIO2 was low, 0 = ADIO2 has not been low   | 0       |
| 3     | ADIO3_HIGH_ALARM      | ADIO3 was above ADIO3_MAX_TH; 1 = ADIO3 was high, 0 = ADIO3 has not been high   | 0       |
| 2     | ADI03_LOW_ALARM       | ADIO3 was below ADIO3_MIN_TH; 1 = ADIO3 was low, 0 = ADIO3 has not been low   | 0       |
| 1     | ADIO4_HIGH_ALARM      | ADIO4 was above ADIO4_MAX_TH; 1 = ADIO4 was high, 0 = ADIO4 has not been high   | 0       |
| 0     | ADIO4_LOW_ALARM       | ADIO4 was below ADIO4_MIN_TH; 1 = ADIO4 was low, 0 = ADIO4 has not been low   | 0       |

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| BIT   | NAME                      | OPERATION  | DEFAULT |
|-------|---------------------------|--|---------|
| ADC_A | <br>LARM_LOG_4 (0x08) – F | Read/Write   |         |
| 7     | DRNS_HIGH_ALARM           | DRNS was above DRNS_MAX_TH; 1 = DRNS was high, 0 = DRNS has not been high                              | 0       |
| 6     | DRNS_LOW_ALARM            | DRNS was below DRNS_MIN_TH; 1 = DRNS was low, 0 = DRNS has not been low                                | 0       |
| 5     | DRAIN_HIGH_ALARM          | DRAIN was above DRAIN_MAX_TH; 1 = DRAIN was high, 0 = DRAIN has not been high                          | 0       |
| 4     | DRAIN_LOW_ALARM           | DRAIN was below DRAIN_MIN_TH; 1 = DRAIN was low, 0 = DRAIN has not been low                            | 0       |
| 3     | Reserved                  | Undefined  | 0       |
| 2     | Reserved                  | Undefined  | 0       |
| 1     | Reserved                  | Undefined  | 0       |
| 0     | Reserved                  | Undefined  | 0       |
| ADC_A | LARM_LOG_5 (0x09) – F     | Read/Write   |         |
| 7     | ADIN12_HIGH_ALARM         | ADIN2 - ADIN1 was above ADIN12_MAX_TH; 1 = ADIN2 - ADIN1 was high, 0 = ADIN2 - ADIN1 has not been high | 0       |
| 6     | ADIN12_LOW_ALARM          | ADIN2 – ADIN1 was below ADIN12_MIN_TH; 1 = ADIN2 – ADIN1 was low, 0 = ADIN2 – ADIN1 has not been low   | 0       |
| 5     | ADIN34_HIGH_ALARM         | ADIN4 – ADIN3 was above ADIN34_MAX_TH; 1 = ADIN4 – ADIN3 was high, 0 = ADIN4 – ADIN3 has not been high | 0       |
| 4     | ADIN34_LOW_ALARM          | ADIN4 – ADIN3 was below ADIN34_MIN_TH; 1 = ADIN4 – ADIN3 was low, 0 = ADIN4 – ADIN3 has not been low   | 0       |
| 3     | ADIO12_HIGH_ALARM         | ADIO2 – ADIO1 was above ADIO12_MAX_TH; 1 = ADIO2 – ADIO1 was high, 0 = ADIO2 – ADIO1 has not been high | 0       |
| 2     | ADI012_LOW_ALARM          | ADIO2 – ADIO1 was below ADIO12_MIN_TH; 1 = ADIO2 – ADIO1 was low, 0 = ADIO2 – ADIO1 has not been low   | 0       |
| 1     | ADIO34_HIGH_ALARM         | ADIO4 – ADIO3 was above ADIO34_MAX_TH; 1 = ADIO4 – ADIO3 was high, 0 = ADIO4 – ADIO3 has not been high | 0       |
| 0     | ADIO34_LOW_ALARM          | ADIO4 – ADIO3 was below ADIO34_MIN_TH; 1 = ADIO4 – ADIO3 was low, 0 = ADIO4 – ADIO3 has not been low   | 0       |

### Table 10. CONTROL Registers (0x0A-0x0B) - Read/Write

| BIT   | NAME                      | OPERATION   | DEFAULT |
|-------|---------------------------|---|---------|
| CONTR | ROL_1 (0x0A) – Read/Write |   |         |
| 7     | ON                        | Turns MOSFET on and off; 1 = turn MOSFET on, 0 = turn MOSFET off  | 1       |
| 6     | DVDT                      | Enables dV/dt inrush control during startup; 1 = enabled, 0 = disabled  | 1       |
| 5     | THERM_TMR                 | Turns 2µa TMR pull-down off; 1 = TMR pull-down turned off, 0 = TMR pull-down turned on  | 0       |
| 4     | FET_BAD_TURN_OFF          | Turns MOSFET off following a FET_BAD_FAULT; 1 = turn MOSFET off, 0 = keep MOSFET on   | 1       |
| 3     | PWRGD_RESET_ CNTRL        | Configures power good reset; $1 = reset$ by $V_{OUT}$ low, $0 = reset$ by MOSFET off  | 1       |
| 2     | PGI02_ACLB                | Configures PGI02; 1 = PGI02 as inverted output for active current limit engagement after startup; 0 = normal PGI02 function configured by 0x10 bit[3:2] | 0       |
| 1     | MASS_WRITE_ ENABLE        | Enables mass write to all LTC4283S on the $I^2C$ bus; 1 = enabled, 0 = disabled   | 1       |
| 0     | PAGE_READ_WRITE_ ENABLE   | Enables I <sup>2</sup> C page read/write protocols; $1 = enabled$ , $0 = disabled$  | 1       |
| CONTR | ROL_2 (0x0B) – Read/Write |   |         |
| 7     | EXT_FAULT_RETRY           | Enables auto-retry following an EXT_FAULT; 1 = unlimited retries, 0 = no retry (latch-off)  | 0       |
|       |                           |   |         |

| PGI_RETRY     | Enables auto-retry following a PGI_FAULT; 1 = unlimited retries, 0 = no retry (latch-off) |  |  |  |  |
|---------------|---|--|--|--|--|
| FET_BAD_RETRY | Configures auto-retry following   | ng a FET_BAD_FAULT and N   | NOSFET turn off  | 00   |  |
|               | FET_BAD_RETRY [5:4]   | FET_BAD_RETRY [5:4] Number of Retries  |  |  |  |
|               | 00  | 0 (Latch-Off)  | -  |  |  |
|               | 01  | 1  | -  |  |  |
|               | 10  | 7  | -  |  |  |
|               | 11  | Unlimited  | -  |  |  |
| OC_RETRY      | Configures auto-retry followi   |  | 00   |  |  |
|               | OC_RETRY [3:2]  | Number of Retries  |  |  |  |
|               | 00  | 0 (Latch-Off)  |  |  |  |
|               | 01  | 1  |  |  |  |
|               | 10  | 7  | -  |  |  |
|               | 11  | Unlimited  |  |  |  |
| UV_RETRY      | Enables auto-retry following a UV_FAULT; 1 = unlimited retries, 0 = no retry (latch-off)  |  |  |  |  |
| OV_RETRY      | Enables auto-retry following an OV_FAULT; 1 = unlimited retries, 0 = no retry (latch-off) |  |  |  |  |
|               | PGI_RETRY<br>FET_BAD_RETRY<br>OC_RETRY<br>UV_RETRY<br>OV_RETRY                            | PGI_RETRYEnables auto-retry followingFET_BAD_RETRYConfigures auto-retry followingFET_BAD_RETRY [5:4]00011010110C_RETRYConfigures auto-retry following0C_RETRYConfigures auto-retry following000110110C_RETRY0001101011UV_RETRYEnables auto-retry following0V_RETRYEnables auto-retry following | PGI_RETRY       Enables auto-retry following a PGI_FAULT; 1 = unlimited         FET_BAD_RETRY       Configures auto-retry following a FET_BAD_FAULT and N         FET_BAD_RETRY       FET_BAD_RETRY [5:4]       Number of Retries         00       0 (Latch-Off)         01       1         10       7         11       Unlimited         0C_RETRY       Configures auto-retry following an OC_FAULT         0C_RETRY       Configures auto-retry following an OC_FAULT         00       0 (Latch-Off)         01       1         10       7         11       Unlimited         UV_RETRY       Enables auto-retry following a UV_FAULT; 1 = unlimited         0V_RETRY       Enables auto-retry following an OV_FAULT; 1 = unlimited | PGI_RETRY       Enables auto-retry following a PGI_FAULT; 1 = unlimited retries, 0 = no retry (latch-off)         FET_BAD_RETRY       Configures auto-retry following a FET_BAD_FAULT and MOSFET turn off         FET_BAD_RETRY [5:4]       Number of Retries         00       0 (Latch-Off)         01       1         10       7         11       Unlimited         00       0 (Latch-Off)         01       1         10       7         11       Unlimited         00       0 (Latch-Off)         01       1         10       7         11       Unlimited         00       0 (Latch-Off)         01       1         10       7         11       Unlimited         00       0 (Latch-Off)         01       1         10       7         11       Unlimited         UV_RETRY       Enables auto-retry following a UV_FAULT; 1 = unlimited retries, 0 = no retry (latch-off)         0V_RETRY       Enables auto-retry following an OV_FAULT; 1 = unlimited retries, 0 = no retry (latch-off) |  |

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### Table 11. CONFIG Registers (0x0D-0x0F) - Read/Write

| BIT   | NAME                    | OPERATION   |                              |  | DEFAULT |  |
|-------|-------------------------|---|------------------------------|--|---------|--|
| CONFI | G_1 (0x0D) – Read/Write | ·   |                              |  |         |  |
| 7:4   | ILIM                    | Configures V <sub>ILIM</sub> and V <sub>ILIM(FAST)</sub>  |                              |  |         |  |
|       |                         | ILIM [7:4]  | V <sub>ILIM</sub> [mV]       | V <sub>ILIM(FAST)</sub> [mV]                         |         |  |
|       |                         | 0000  | 15                           | 30   |         |  |
|       |                         | 0001  | 16                           | 32   |         |  |
|       |                         | 0010  | 17                           | 34   |         |  |
|       |                         | 0011  | 18                           | 36   |         |  |
|       |                         | 0100  | 19                           | 38   |         |  |
|       |                         | 0101  | 20                           | 40   |         |  |
|       |                         | 0110  | 21                           | 42   |         |  |
|       |                         | 0111  | 22                           | 44   |         |  |
|       |                         | 1000  | 23                           | 46   |         |  |
|       |                         | 1001  | 24                           | 48   |         |  |
|       |                         | 1010  | 25                           | 50   |         |  |
|       |                         | 1011  | 26                           | 52   |         |  |
|       |                         | 0011         18         36           0100         19         38           0101         20         40           0110         21         42           0111         22         44           1000         23         46           1001         24         48           1010         25         50           1011         26         52           1100         27         54           1101         28         56           1110         29         58           1111         30         60           Configures current limit foldback factor for startup and normal operation           FB [3:2]           Foldback Factor, α [% V <sub>ILIM</sub> ]           00         100 (foldback disabled)           01         50           10         20           11         10           Disables foldback after startup; 1 = disabled, 0 = enabled. Foldback during startup is not affected           Enables load power foldback after startup; 1 = enabled, 0 = disabled |                              |  |         |  |
|       |                         | 1101  | 28                           | 56   |         |  |
|       |                         | 1110  | 29                           | 58   |         |  |
|       |                         | 1111  | 30                           | 60   |         |  |
| 3:2   | FB                      | Configures current limit foldback factor for startup and normal operation   |                              |  |         |  |
|       |                         | FB [3:2]  | Foldback Factor, $\alpha$ [% | 6 VILIM]   |         |  |
|       |                         | 00  | 100 (foldback disat          | oled)  |         |  |
|       |                         | 01  | 50                           |  |         |  |
|       |                         | 10  | 20                           |  |         |  |
|       |                         | 11  | 10                           |  |         |  |
| 1     | FB_DIS                  | Disables foldback after st  | tartup; 1 = disabled, 0 = e  | nabled. Foldback during startup is not affected      | 0       |  |
| 0     | LPFB                    | Enables load power foldb  | oack after startup; 1 = ena  | bled, 0 = disabled                                   | 0       |  |
| CONFI | G_2 (0x0E) – Read/Write |   |                              |  | _!      |  |
| 7:6   | VDTH                    | Configures DRAIN voltag   | e threshold for starting Fl  | ET bad fault filtering timer, V <sub>D,FET(TH)</sub> | 11      |  |
|       |                         | VDTH [7:6]  | V <sub>D,FET(TH)</sub> [mV]  |  |         |  |
|       |                         | 00  | 72                           |  |         |  |
|       |                         | 01  | 102                          |  |         |  |
|       |                         | 10  | 143                          |  |         |  |
|       |                         | 11  | 203                          |  |         |  |
|       | 1                       |   |                              |  | 1       |  |

| BIT   | NAME                    | OPERATION  | OPERATION   |                                      |   |         |
|-------|-------------------------|--|---|--------------------------------------|---|---------|
| 5:4   | FTBD_DL                 | Configures FET_Bad fault                                     | t filtering timer delay, t <sub>DL(</sub>               | FETBAD)                              |   | 00      |
|       |                         | FTBD_DL [5:4]  | t <sub>DL(FETBAD)</sub> [s]                             |                                      |   |         |
|       |                         | 00   | 0.256   |                                      |   |         |
|       |                         | 01   | 0.512   |                                      |   |         |
|       |                         | 10   | 1.02  |                                      |   |         |
|       |                         | 11   | 2.05  |                                      |   |         |
| 3:1   | COOLING_DL              | Configures cooling delay<br>EXT_FAULT, t <sub>DL(RTRY)</sub> | preceding each auto-retr                                | y following OC_                      | _FAULT, FET_BAD_FAULT or                    | 000     |
|       |                         | COOLING_DL [3:1]   | t <sub>DL(RTRY)</sub> [s]                               |                                      |   |         |
|       |                         | 000  | 0.512   |                                      |   |         |
|       |                         | 001  | 1.02  |                                      |   |         |
|       |                         | 010  | 2.05  |                                      |   |         |
|       |                         | 011  | 4.10  |                                      |   |         |
|       |                         | 100  | 8.19  |                                      |   |         |
|       |                         | 101  | 16.4  |                                      |   |         |
|       |                         | 110  | 32.8  |                                      |   |         |
|       |                         | 111  | 65.5  |                                      |   |         |
| 0     | PORB                    | Resets to 0 upon power-on reset has not o                    | on reset. Write this bit to<br>ccurred, 0 = power-on re | 1 to use it as po<br>set occurred    | ower-on reset indicator: 1 =                | 0       |
| CONFI | G_3 (0x0F) – Read/Write |  |   |                                      |   |         |
| BIT   | NAME                    | OPERATION  |   |                                      |   | DEFAULT |
| 7     | EXTFLT_TURN_OFF         | Turns MOSFET off follow                                      | ing an external fault; 1 = 1                            | turn MOSFET o                        | ff, 0 = keep MOSFET on                      | 0       |
| 6     | VPWR_SELECT             | Selects voltage for ADC p<br>MOSFET power), 0 = sele         | oower multiplication; 1 =<br>ects RTNS (attenuated inp  | selects DRNS (a<br>out voltage for i | attenuated drain voltage for<br>nput power) | 0       |
| 5     | FAST_I2C_EN             | Enables fast I <sup>2</sup> C mode; 1                        | = fast $I^2C$ enabled, $0 = fa$                         | st I <sup>2</sup> C disabled         |   | 0       |
| 4:3   | BC                      | Configures bit rate of sin                                   | gle-wire broadcast mode                                 | , f <sub>BC</sub>                    |   | 00      |
|       |                         | BC [4:3]   | f <sub>BC</sub> [kbit/s]                                |                                      |   |         |
|       |                         | 00   | 2048  |                                      |   |         |
|       |                         | 01   | 512   |                                      |   |         |
|       |                         | 10   | 128 (Not available for                                  | 8-bit ADC)                           |   |         |
|       |                         | 11   | 32 (Not available for                                   | 8-bit ADC)                           |   |         |
| 2     | TICK_OVERFLOW_ ALERT    | Enables alert when tick c                                    | ounter overflows; 1 = ale                               | rt enabled, 0 = a                    | alert disabled                              | 0       |
| 1     | METER_OVERFLOW_ALERT    | Enables alert when energ                                     | y meter overflows; 1 = al                               | ert enabled, 0 =                     | alert disabled                              | 0       |
| 0     | INTEGRATE_I             | Enables integration of cu                                    | rrent; 1 = integrate currer                             | nt, 0 = integrate                    | power                                       | 0       |

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### Table 12. PGIO\_CONFIG Registers (0x10:0x11) - Read/Write

| 10010 |                               |                      | nouu/ winto  |   |  |         |  |
|-------|-------------------------------|----------------------|--|---|--|---------|--|
| BIT   | NAME                          | OPERATION            |  |   |  | DEFAULT |  |
| PGIO_ | <u>CONFIG_1 (0x10) – Read</u> | I/Write              |  |   |  |         |  |
| 7:6   | PGI04_CONFIG                  | Configures behavio   | or of PGIO4 pin  |   |  | 00      |  |
|       |                               | PGI04_CONFIG         | [7:6]  | PGIO4   |  |         |  |
|       |                               | 00                   | EX   | (T_FAULT#                                     |  |         |  |
|       |                               | 01                   | E>   | (T_FAULT                                      |  |         |  |
|       |                               | 10                   | General  | purpose output                                |  |         |  |
|       |                               | 11                   | Genera   | l purpose input                               |  |         |  |
| 5:4   | PGI03_CONFIG                  | Configures behavio   | or of PGIO3 pin  |   |  | 00      |  |
|       |                               | PGI03_CONFIG         | [5:4]  | PGI03   |  |         |  |
|       |                               | 00                   |  | PGI#  |  |         |  |
|       |                               | 01                   |  | PGI   |  |         |  |
|       |                               | 10                   | General  | purpose output                                |  |         |  |
|       |                               | 11                   | Genera   | l purpose input                               |  |         |  |
| 3:2   | PGIO2 CONFIG                  | Configures behavio   | or of PGIO2 pin  |   |  | 00      |  |
|       |                               | PGIO2 CONFIG         | [3:2]  | PGI02   |  |         |  |
|       |                               | 00                   | Pow  | ver Good 2#                                   |  |         |  |
|       |                               | 01                   | Pov  | wer Good 2                                    |  |         |  |
|       |                               | 10                   | General  | purpose output                                |  |         |  |
|       |                               | 11                   | Genera   | l purpose input                               |  |         |  |
| 1:0   | PGI01 CONFIG                  | Configures behavio   | or of PGIO1 pin  |   |  | 00      |  |
|       | _                             | PGI01_CONFIG         | [1:0]  | PGI01   |  |         |  |
|       |                               | 00                   | Pow  | ver Good 1#                                   |  |         |  |
|       |                               | 01                   | Pov  | wer Good 1                                    |  |         |  |
|       |                               | 10                   | General  | purpose output                                |  |         |  |
|       |                               | 11                   | Genera   | l purpose input                               |  |         |  |
| PGIO  | CONFIG 2 (0x11) – Read        | l/Write              |  |   |  |         |  |
| 7     | PGIO4 OUT                     | Output data bit to I | PGIO4 pin when co  | nfigured as general purpos                    | se output  | 0       |  |
| 6     | PGI03_OUT                     | Output data bit to I | PGIO3 pin when co  | nfigured as general purpos                    | se output  | 0       |  |
| 5     | PGI02_OUT                     | Output data bit to I | Output data bit to PGIO2 pin when configured as general purpose output                   |   |  |         |  |
| 4     | PGI01_0UT                     | Output data bit to I | Output data bit to PGIO1 pin when configured as general purpose output                   |   |  | 0       |  |
| 3     | ADC_CONV_ALERT                | Enables alert when   | Enables alert when ADC finishes making a conversion; 1 = enable alert, 0 = disable alert |   |  |         |  |
| 2:0   | ADC                           | Configures ADC re    | solution and conve   | ersion rate                                   |  | 100     |  |
|       |                               | ADC [2:0]            | ADC Resolution<br>[Bits]   | ADC Conversion Rate<br>f <sub>CONV</sub> [Hz] | Sampling Clock Frequency<br>f <sub>s</sub> [kHz] |         |  |
|       |                               | 000                  | 8  | 996   | 512  |         |  |
|       |                               | 010                  | 10   | 125   | 256  |         |  |
|       |                               | 100                  | 12   | 15.6  | 128  |         |  |

3.91

0.977

128

128

14

16

110

xx1

### Table 13. ADIO\_CONFIG Register (0x12) – Read/Write

| BIT | NAME         | OPERATION   | DEFAULT |
|-----|--------------|---|---------|
| 7   | ADIO4_CONFIG | Configures behavior of ADIO4 pin; 1 = general purpose input, 0 = general purpose output | 1       |
| 6   | ADIO3_CONFIG | Configures behavior of ADIO3 pin; 1 = general purpose input, 0 = general purpose output | 1       |
| 5   | ADIO2_CONFIG | Configures behavior of ADIO2 pin; 1 = general purpose input, 0 = general purpose output | 1       |
| 4   | ADIO1_CONFIG | Configures behavior of ADIO1 pin; 1 = general purpose input, 0 = general purpose output | 1       |
| 3   | ADIO4_OUT    | Output data bit to ADIO4 pin when configured as general purpose output                  | 0       |
| 2   | ADIO3_OUT    | Output data bit to ADIO3 pin when configured as general purpose output                  | 0       |
| 1   | ADIO2_OUT    | Output data bit to ADIO2 pin when configured as general purpose output                  | 0       |
| 0   | ADI01_0UT    | Output data bit to ADIO1 pin when configured as general purpose output                  | 0       |

#### Table 14. ADC\_SELECT Registers (0x13-0x14) - Read/Write

| BIT   | NAME                        | OPERATION  | DEFAULT |
|-------|-----------------------------|--|---------|
| ADC_S | ELECT_1 (0x13) – Read/Write |  |         |
| 7     | ADIO4_SELECT                | Selects ADIO4 as input for ADC measurement; 1 = selected, 0 = not selected         | 1       |
| 6     | ADIO3_SELECT                | Selects ADIO3 as input for ADC measurement; 1 = selected, 0 = not selected         | 1       |
| 5     | ADIO2_SELECT                | Selects ADIO2 as input for ADC measurement; 1 = selected, 0 = not selected         | 1       |
| 4     | ADIO1_SELECT                | Selects ADIO1 as input for ADC measurement; 1 = selected, 0 = not selected         | 1       |
| 3     | ADIN4_SELECT                | Selects ADIN4 as input for ADC measurement; 1 = selected, 0 = not selected         | 1       |
| 2     | ADIN3_SELECT                | Selects ADIN3 as input for ADC measurement; 1 = selected, 0 = not selected         | 1       |
| 1     | ADIN2_SELECT                | Selects ADIN2 as input for ADC measurement; 1 = selected, 0 = not selected         | 1       |
| 0     | ADIN1_SELECT                | Selects ADIN1 as input for ADC measurement; 1 = selected, 0 = not selected         | 1       |
| ADC_S | ELECT_2 (0x14) – Read/Write |  |         |
| 7     | ADIO34_SELECT               | Selects ADIO4 – ADIO3 as input for ADC measurement; 1 = selected, 0 = not selected | 0       |
| 6     | ADI012_SELECT               | Selects ADIO2 – ADIO1 as input for ADC measurement; 1 = selected, 0 = not selected | 0       |
| 5     | ADIN34_SELECT               | Selects ADIN4 – ADIN3 as input for ADC measurement; 1 = selected, 0 = not selected | 0       |
| 4     | ADIN12_SELECT               | Selects ADIN2 – ADIN1 as input for ADC measurement; 1 = selected, 0 = not selected | 0       |
| 3     | Reserved                    | Undefined  | 1       |
| 2     | Reserved                    | Undefined  | 1       |
| 1     | DRAIN_SELECT                | Selects DRAIN as input for ADC measurement; 1 = selected, 0 = not selected         | 1       |
| 0     | DRNS_SELECT                 | Selects DRNS as input for ADC measurement; 1 = selected, 0 = not selected          | 1       |

#### Table 15. FAULT\_ALERT Register (0x15) - Read/Write

| BIT | NAME                | OPERATION  |   |
|-----|---------------------|--|---|
| 7   | EXT_FAULT_ALERT     | Enables alert for external fault; $1 =$ enable alert, $0 =$ disable alert      | 0 |
| 6   | FET_SHORT_ALERT     | Enables alert for FET short fault; 1 = enable alert, 0 = disable alert         | 0 |
| 5   | POWER_FAILED_ ALERT | Enables alert for power failed fault; $1 = enable alert$ , $0 = disable alert$ | 0 |
| 4   | PGI_ALERT           | Enables alert for PGI fault; 1 = enable alert, 0 = disable alert               | 0 |
| 3   | FET_BAD_ALERT       | Enables alert for FET bad fault; 1 = enable alert, 0 = disable alert           | 0 |
| 2   | OC_ALERT            | Enables alert for overcurrent fault; 1 = enable alert, 0 = disable alert       | 0 |
| 1   | UV_ALERT            | Enables alert for undervoltage fault; 1 = enable alert, 0 = disable alert      | 0 |
| 0   | OV_ALERT            | Enables alert for overvoltage fault; 1 = enable alert, 0 = disable alert       | 0 |



### Table 16. ADC\_ALERT Registers (0x16-0x1A) - Read/Write

| BIT   | NAME                       | OPERATION  |   |
|-------|----------------------------|--|---|
| ADC_A | LERT_1 (0x16) – Read/Write |  |   |
| 7     | EN#_CHANGED_ALERT          | Enables alert when EN# pin changed state; $1 = enable alert$ , $0 = disable alert$                                     | 0 |
| 6     | EEPROM_WRITTEN_ALERT       | Enables alert when EEPROM is written through $I^2C$ ; 1 = enable alert, 0 = disable alert                              | 0 |
| 5     | SENSE_HIGH_ALERT           | Enables alert when SENSE <sup>+</sup> – SENSE <sup>-</sup> was above SENSE_MAX_TH; 1 = enable alert, 0 = disable alert | 0 |
| 4     | SENSE_LOW_ALERT            | Enables alert when SENSE <sup>+</sup> – SENSE <sup>-</sup> was below SENSE_MIN_TH; 1 = enable alert, 0 = disable alert | 0 |
| 3     | VPWR_HIGH_ALERT            | Enables alert when VPWR was above VPWR_MAX_TH; 1 = enable alert, 0 = disable alert                                     | 0 |
| 2     | VPWR_LOW_ALERT             | Enables alert when VPWR was below VPWR_MIN_TH; 1 = enable alert, 0 = disable alert                                     | 0 |
| 1     | POWER_HIGH_ALERT           | Enables alert when POWER was above POWER_MAX_TH; 1 = enable alert, 0 = disable alert                                   | 0 |
| 0     | POWER_LOW_ALERT            | Enables alert when POWER was below POWER_MIN_TH; 1 = enable alert, 0 = disable alert                                   | 0 |
| ADC_A | LERT_2 (0x17) – Read/Write |  |   |
| 7     | ADIN1_HIGH_ALERT           | Enables alert when ADIN1 was above ADIN1_MAX_TH; 1 = enable alert, 0 = disable alert                                   | 0 |
| 6     | ADIN1_LOW_ALERT            | Enables alert when ADIN1 was below ADIN1_MIN_TH; 1 = enable alert, 0 = disable alert                                   | 0 |
| 5     | ADIN2_HIGH_ALERT           | Enables alert when ADIN2 was above ADIN2_MAX_TH; 1 = enable alert, 0 = disable alert                                   | 0 |
| 4     | ADIN2_LOW_ALERT            | Enables alert when ADIN2 was below ADIN2_MIN_TH; 1 = enable alert, 0 = disable alert                                   | 0 |
| 3     | ADIN3_HIGH_ALERT           | Enables alert when ADIN3 was above ADIN3_MAX_TH; 1 = enable alert, 0 = disable alert                                   | 0 |
| 2     | ADIN3_LOW_ALERT            | Enables alert when ADIN3 was below ADIN3_MIN_TH; 1 = enable alert, 0 = disable alert                                   | 0 |
| 1     | ADIN4_HIGH_ALERT           | Enables alert when ADIN4 was above ADIN4_MAX_TH; 1 = enable alert, 0 = disable alert                                   | 0 |
| 0     | ADIN4_LOW_ALERT            | Enables alert when ADIN4 was below ADIN4_MIN_TH; 1 = enable alert, 0 = disable alert                                   | 0 |
| ADC_A | LERT_3 (0x18) – Read/Write |  |   |
| 7     | ADIO1_HIGH_ALERT           | Enables alert when ADIO1 was above ADIO1_MAX_TH; 1 = enable alert, 0 = disable alert                                   | 0 |
| 6     | ADIO1_LOW_ALERT            | Enables alert when ADIO1 was below ADIO1_MIN_TH; 1 = enable alert, 0 = disable alert                                   | 0 |
| 5     | ADIO2_HIGH_ALERT           | Enables alert when ADIO2 was above ADIO2_MAX_TH; 1 = enable alert, 0 = disable alert                                   | 0 |
| 4     | ADIO2_LOW_ALERT            | Enables alert when ADIO2 was below ADIO2_MIN_TH; 1 = enable alert, 0 = disable alert                                   | 0 |
| 3     | ADIO3_HIGH_ALERT           | Enables alert when ADIO3 was above ADIO3_MAX_TH; 1 = enable alert, 0 = disable alert                                   | 0 |
| 2     | ADIO3_LOW_ALERT            | Enables alert when ADIO3 was below ADIO3_MIN_TH; 1 = enable alert, 0 = disable alert                                   | 0 |
| 1     | ADIO4_HIGH_ALERT           | Enables alert when ADIO4 was above ADIO4_MAX_TH; 1 = enable alert, 0 = disable alert                                   | 0 |
| 0     | ADIO4_LOW_ALERT            | Enables alert when ADIO4 was below ADIO4_MIN_TH; 1 = enable alert, 0 = disable alert                                   | 0 |

| BIT   | NAME                       | OPERATION   | DEFAULT |
|-------|----------------------------|---|---------|
| ADC_A | LERT_4 (0x19) – Read/Write |   |         |
| 7     | DRNS_HIGH_ALERT            | Enables alert when DRNS was above DRNS_MAX_TH; 1 = enable alert, 0 = disable alert            | 0       |
| 6     | DRNS_LOW_ALERT             | Enables alert when DRNS was below DRNS_MIN_TH; 1 = enable alert, 0 = disable alert            | 0       |
| 5     | DRAIN_HIGH_ALERT           | Enables alert when DRAIN was above DRAIN_MAX_TH; 1 = enable alert, 0 = disable alert          | 0       |
| 4     | DRAIN_LOW_ALERT            | Enables alert when DRAIN was below DRAIN_MIN_TH; 1 = enable alert, 0 = disable alert          | 0       |
| 3     | Reserved                   | Undefined   | 0       |
| 2     | Reserved                   | Undefined   | 0       |
| 1     | Reserved                   | Undefined   | 0       |
| 0     | Reserved                   | Undefined   | 0       |
| ADC_A | LERT_5 (0x1A) – Read/Write |   |         |
| 7     | ADIN12_HIGH_ALERT          | Enables alert when ADIN2 – ADIN1 was above ADIN12_MAX_TH; 1 = enable alert, 0 = disable alert | 0       |
| 6     | ADIN12_LOW_ALERT           | Enables alert when ADIN2 – ADIN1 was below ADIN12_MIN_TH; 1 = enable alert, 0 = disable alert | 0       |
| 5     | ADIN34_HIGH_ALERT          | Enables alert when ADIN4 – ADIN3 was above ADIN34_MAX_TH; 1 = enable alert, 0 = disable alert | 0       |
| 4     | ADIN34_LOW_ALERT           | Enables alert when ADIN4 – ADIN3 was below ADIN34_MIN_TH; 1 = enable alert, 0 = disable alert | 0       |
| 3     | ADI012_HIGH_ALERT          | Enables alert when ADIO2 – ADIO1 was above ADIO12_MAX_TH; 1 = enable alert, 0 = disable alert | 0       |
| 2     | ADI012_LOW_ALERT           | Enables alert when ADIO2 – ADIO1 was below ADIO12_MIN_TH; 1 = enable alert, 0 = disable alert | 0       |
| 1     | ADIO34_HIGH_ALERT          | Enables alert when ADIO4 – ADIO3 was above ADIO34_MAX_TH; 1 = enable alert, 0 = disable alert | 0       |
| 0     | ADIO34_LOW_ALERT           | Enables alert when ADIO4 – ADIO3 was below ADIO34_MIN_TH; 1 = enable alert, 0 = disable alert | 0       |

#### Table 17. ENERGY Registers (0x7A-0x7F) – Read/Write

| BIT  | NAME   | OPERATION              | DEFAULT          |
|------|--------|------------------------|------------------|
| 47:0 | ENERGY | Data of metered energy | 0x0000_0000_0000 |

#### Table 18. TICK\_COUNTER Registers (0x80-0x83) - Read/Write

| BIT  | NAME         | OPERATION  | DEFAULT     |
|------|--------------|--|-------------|
| 31:0 | TICK_COUNTER | Counts number of ADC conversion cycles that power measurements have been accumulated in the energy meter | 0x0000_0000 |

#### Table 19. METER\_CONTROL Register (0x84) - Read/Write

| BIT | NAME            | OPERATION  |    |
|-----|-----------------|--|----|
| 7   | METER_RESET     | Resets energy meter and tick counter until cleared; 1 = reset, 0 = reset cleared   | 0  |
| 6   | METER_HALT      | Halts energy meter and tick counter from accumulating; 1 = halted, 0 = not halted  |    |
| 5   | TICK_OVERFLOW   | Tick counter has overflowed; 1 = overflowed, 0 = not overflowed  | 0  |
| 4   | METER_OVERFLOW  | Energy meter accumulator has overflowed; 1 = overflowed, 0 = not overflowed  | 0  |
| 3   | ALERT_GENERATED | Latched to 1 when an alert is generated and can only be cleared via $I^2C$ ; 1 = alert generated, 0 = alert has not been generated | 0  |
| 2   | EE_LOCK         | EEPROM lock status, read only; 1 = EEPROM is factory locked, 0 = EEPROM is not factory locked                                      | 0  |
| 1:0 | Reserved        | Read only, always returns 0  | 00 |

#### Table 20. ADC\_SNAPSHOT Register (0x85) — Read/Write

| BIT | NAME         | OPERATION                    |                               | DEFAULT        |      |
|-----|--------------|------------------------------|-------------------------------|----------------|------|
| 7:4 | SNAPSHOT_SEL | Selects one of the 16 ADC au | xiliary inputs for snapshot n | neasurement    | 0000 |
|     |              | SNAPSHOT_SEL [7:4]           | Auxiliary ADC Input           | -              |      |
|     |              | 0000                         | ADIN1                         | -              |      |
|     |              | 0001                         | ADIN2                         | -              |      |
|     |              | 0010                         | ADIN3                         | -              |      |
|     |              | 0011                         | ADIN4                         | -              |      |
|     |              | 0100                         | ADI01                         | -              |      |
|     |              | 0101                         | ADI02                         | _              |      |
|     |              | 0110                         | ADI03                         | -              |      |
|     |              | 0111                         | ADIO4                         | _              |      |
|     |              | 1000                         | DRNS                          | _              |      |
|     |              | 1001                         | DRAIN                         | _              |      |
|     |              | 1010                         | Reserved                      | _              |      |
|     |              | 1011                         | Reserved                      | _              |      |
|     |              | 1100                         | ADIN2 – ADIN1                 | _              |      |
|     |              | 1101                         | ADIN4 – ADIN3                 | -              |      |
|     |              | 1110                         | ADI02 – ADI01                 | -              |      |
|     |              | 1111                         | ADI04 – ADI03                 | -              |      |
| 3   | ADC_HALT     | Enables ADC snapshot mode    | ; 1 = snapshot, 0 = continuo  | ous conversion | 0    |
| 2:0 | Reserved     | Read only, always returns 0  |                               |                | 000  |

#### Table 21. FAULT\_LOG\_CONTROL Register (0x90) - Read/Write

| BIT | NAME             | OPERATION  | DEFAULT |
|-----|------------------|--|---------|
| 7   | FAULT_LOG_ENABLE | Enables logging fault registers and ADC data into EEPROM upon a fault; this bit can only be cleared using $I^2C$ ; 1 = fault log enabled, 0 = fault log disabled | 0       |
| 6   | FAULT_LOG_UNLOCK | Allows clearing of FAULT_LOG_START and FAULT_LOG_DONE bits to re-enable fault log following a previous fault log; 1 = clearing allowed, 0 = clearing not allowed | 0       |
| 5   | FAULT_LOG_START  | Indicates a fault log is started; $l^2C$ can not set this bit but can clear it; 1 = fault log started, 0 = fault log has not been started                        | 0       |
| 4   | FAULT_LOG_DONE   | Indicates a fault log is completed; $I^2C$ can not set this bit but can clear it; 1 = fault log completed, 0 = fault log has not been completed                  | 0       |
| 3   | FAULT_LOG_ALERT  | Enables alert when a fault log is completed; 1 = enable alert, 0 = disable alert   | 0       |
| 2:0 | Reserved         | Read only, always returns 0  | 000     |

#### Table 22. Registers Recorded to EEPROM During Fault Log

| REGISTER NAME | REGISTER<br>ADDRESS | EEPROM<br>Address | DATA LENGTH<br>(BYTES) | DESCRIPTION  |
|---------------|---------------------|-------------------|------------------------|--|
| FAULT         | 0x04                | 0xA4              | 1                      | System fault   |
| ADC_ALARM_LOG | 0x05-0x09           | 0xA5-0xA9         | 5                      | ADC measurement alarms   |
| SENSE         | 0x41                | 0xE1              | 1                      | MSB byte of most recent ADC output for SENSE <sup>+</sup> – SENSE <sup>-</sup> |
| SENSE_MIN     | 0x42                | 0xE2              | 1                      | MSB byte of minimum ADC output for SENSE <sup>+</sup> – SENSE <sup>-</sup>     |
| SENSE_MAX     | 0x43                | 0xE3              | 1                      | MSB byte of maximum ADC output for SENSE <sup>+</sup> – SENSE <sup>-</sup>     |
| VPWR          | 0x44                | 0xE4              | 1                      | MSB byte of most recent ADC output for VPWR voltage                            |
| VPWR_MIN      | 0x45                | 0xE5              | 1                      | MSB byte of minimum ADC output for VPWR voltage                                |
| VPWR_MAX      | 0x46                | 0xE6              | 1                      | MSB byte of maximum ADC output for VPWR voltage                                |

#### Table 23. REBOOT Register (0xA2) - Read/Write

| BIT | NAME         | OPERATION  |                          |  | DEFAULT |
|-----|--------------|--|--------------------------|--|---------|
| 7   | RBT_EN       | Controls auto-reboot; 1 = reboot after delay t <sub>DL(RBT)</sub> , 0 = no reboot. When set to 1, this bit remains 1 after reboot is done. Clear it before issuing the next reboot command |                          |  | 0       |
| 6:4 | RBT_DL       | Configures delay for auto-reboot, $t_{DL(RBT)}$ , after the REBOOT bit is set to 1   |                          |  | 000     |
|     |              | RBT_DL [6:4]   | t <sub>DL(RBT)</sub> [s] |  |         |
|     |              | 000  | 0.512                    |  |         |
|     |              | 001  | 1.02                     |  |         |
|     |              | 010  | 2.05                     |  |         |
|     |              | 011  | 4.10                     |  |         |
|     |              | 100  | 8.19                     |  |         |
|     |              | 101  | 16.4                     |  |         |
|     |              | 110  | 32.8                     |  |         |
|     |              | 111  | 65.5                     |  |         |
| 3:2 | Reserved     | Read only, always returns 0  |                          |  | 00      |
| 1   | DELAY_STATUS | Reboot and cooling delay status; 1 = device is going through a reboot or cooling delay or in latch-<br>off, 0 = reboot or cooling delay has expired or has not been initiated              |                          |  | 0       |
| 0   | WP_STATUS    | WP pin status; 1 = WP is high, 0 = WP pin is low   |                          |  | 0       |

#### Table 24. Mapping between Faults/Alarms and Alert Masks

| FAULT/ALARM                | ALERT MASK                 |  |
|----------------------------|----------------------------|--|
| FAULT 0x04 [7:0]           | FAULT_ALERT 0x15 [7:0]     |  |
| ADC_ALARM_LOG_1 0x05 [7:0] | ADC_ALERT_1 0x16 [7:0]     |  |
| ADC_ALARM_LOG_2 0x06 [7:0] | ADC_ALERT_2 0x17 [7:0]     |  |
| ADC_ALARM_LOG_3 0x07 [7:0] | ADC_ALERT_3 0x18 [7:0]     |  |
| ADC_ALARM_LOG_4 0x08 [7:0] | ADC_ALERT_4 0x19 [7:0]     |  |
| ADC_ALARM_LOG_5 0x09 [7:0] | ADC_ALERT_5 0x1A [7:0]     |  |
| METER_CONTROL 0x84[4:3]    | CONFIG_3 0x0F [2:1]        |  |
| ADC Conversion Completed   | PGIO_CONFIG_2 0x11 [3]     |  |
| EEPROM Fault Log Completed | FAULT_LOG_CONTROL 0x90 [3] |  |
### PACKAGE DESCRIPTION



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Rev. 0

# TYPICAL APPLICATION



Figure 29. –48V/600W Hot Swap Controller Monitoring System Status, Faults, Currents, Voltages, Power and Temperature and Transmitting Data at 2MBit/s in Single-Wire Broadcast Mode

## **RELATED PARTS**

| PART NUMBER                                   | DESCRIPTION   | COMMENTS  |
|---|---|---|
| LTC4284                                       | –48V High Power Hot Swap Controller with<br>Energy Monitor                                    | Dual Gate Drives, SOA Timer, 8- to 16-Bit ADC Monitors Current, Voltage,<br>Power and Energy, Internal EEPROM, I <sup>2</sup> C or Single-Wire Broadcast            |
| LTC4261/LT4261-2                              | –48V Hot Swap Controller with ADC and I <sup>2</sup> C  | dV/dt Startup Inrush, 10-Bit ADC Monitors Voltages and Current, I <sup>2</sup> C or Single-<br>Wire Broadcast, Two Sequenced Power Good Outputs, Supplies from –12V |
| ADM1075                                       | –48V Hot Swap Controller with PMBus   | 12-Bit ADC Monitors Current, Voltage, Power and Energy  |
| LTC4282                                       | High Current Positive Voltage Hot Swap Controller with I <sup>2</sup> C Compatible Monitoring | Dual Gates for Two Parallel MOSFETs, 12-/16-Bit ADC Monitors Current,<br>Voltage, Power and Energy, Internal EEPROM, I <sup>2</sup> C, Supplies from 2.9V to 33V    |
| LTC4281                                       | Positive Voltage Hot Swap Controller with I <sup>2</sup> C Compatible Monitoring              | 12-/16-Bit ADC Monitors Current, Voltage, Power and Energy, Internal EEPROM, I <sup>2</sup> C, Supplies from 2.9V to 33V  |
| LT4250L/LT4250H                               | –48V Hot Swap Controller in SO-8  | Active Current Limiting, Supplies from –18V to –80V   |
| LTC4251/LTC4251-1                             | –48V Hot Swap Controller in SOT-23  | Fast Active Current Limiting, supplies from –15V  |
| LTC4252-1/LTC4252-2/<br>LTC4252A-1/LTC4252A-2 | -48V Hot Swap Controller in MS8   | Fast Active Current Limiting, Supplies from –15V, ±1% UV/OV (LTC4252A)  |
| LTC4253                                       | -48V Hot Swap Controller with Sequencer   | Fast Current Limiting with Three Sequenced Power Good Outputs, Supplies from $-15V$   |
| LTC4260                                       | Positive High Voltage Hot Swap Controller   | With I <sup>2</sup> C and 8-Bit ADC, Supplies from 8.5V to 80V  |
| LTC4371                                       | Negative Voltage Diode-OR Controller  | Controls Two N-Channel MOSFETs, 220ns Turn-Off  |
| LTC4151                                       | High Voltage Current and Voltage Monitor  | Operates from 7V to 80V, with I <sup>2</sup> C and 12-Bit ADC   |





#### ООО "ЛайфЭлектроникс"

ИНН 7805602321 КПП 780501001 Р/С 40702810122510004610 ФАКБ "АБСОЛЮТ БАНК" (ЗАО) в г.Санкт-Петербурге К/С 3010181090000000703 БИК 044030703

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